



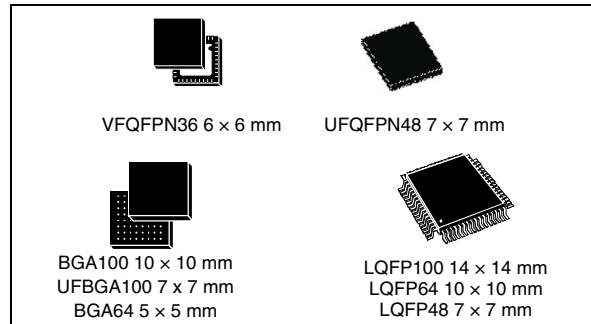
STM32F103x8 STM32F103xB

Medium-density performance line ARM-based 32-bit MCU with 64 or 128 KB Flash, USB, CAN, 7 timers, 2 ADCs, 9 com. interfaces

Datasheet – production data

Features

- ARM 32-bit Cortex™-M3 CPU Core
 - 72 MHz maximum frequency, 1.25 DMIPS/MHz (Dhrystone 2.1) performance at 0 wait state memory access
 - Single-cycle multiplication and hardware division
- Memories
 - 64 or 128 Kbytes of Flash memory
 - 20 Kbytes of SRAM
- Clock, reset and supply management
 - 2.0 to 3.6 V application supply and I/Os
 - POR, PDR, and programmable voltage detector (PVD)
 - 4-to-16 MHz crystal oscillator
 - Internal 8 MHz factory-trimmed RC
 - Internal 40 kHz RC
 - PLL for CPU clock
 - 32 kHz oscillator for RTC with calibration
- Low power
 - Sleep, Stop and Standby modes
 - V_{BAT} supply for RTC and backup registers
- 2 x 12-bit, 1 μ s A/D converters (up to 16 channels)
 - Conversion range: 0 to 3.6 V
 - Dual-sample and hold capability
 - Temperature sensor
- DMA
 - 7-channel DMA controller
 - Peripherals supported: timers, ADC, SPIs, I²Cs and USARTs
- Up to 80 fast I/O ports
 - 26/37/51/80 I/Os, all mappable on 16 external interrupt vectors and almost all 5 V-tolerant



- Debug mode
 - Serial wire debug (SWD) & JTAG interfaces
- 7 timers
 - Three 16-bit timers, each with up to 4 IC/OC/PWM or pulse counter and quadrature (incremental) encoder input
 - 16-bit, motor control PWM timer with dead-time generation and emergency stop
 - 2 watchdog timers (Independent and Window)
 - SysTick timer 24-bit downcounter
- Up to 9 communication interfaces
 - Up to 2 x I²C interfaces (SMBus/PMBus)
 - Up to 3 USARTs (ISO 7816 interface, LIN, IrDA capability, modem control)
 - Up to 2 SPIs (18 Mbit/s)
 - CAN interface (2.0B Active)
 - USB 2.0 full-speed interface
- CRC calculation unit, 96-bit unique ID
- Packages are ECOPACK®

Table 1. Device summary

| Reference | Part number |
|-------------|--|
| STM32F103x8 | STM32F103C8, STM32F103R8 STM32F103V8, STM32F103T8 |
| STM32F103xB | STM32F103RB STM32F103VB, STM32F103CB, STM32F103TB |

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1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F103x8 and STM32F103xB medium-density performance line microcontrollers. For more details on the whole STMicroelectronics STM32F103xx family, please refer to [Section 2.2: Full compatibility throughout the family](#).

The medium-density STM32F103xx datasheet should be read in conjunction with the low-, medium- and high-density STM32F10xxx reference manual.

The reference and Flash programming manuals are both available from the STMicroelectronics website www.st.com.

For information on the Cortex™-M3 core please refer to the Cortex™-M3 Technical Reference Manual, available from the www.arm.com website at the following address: <http://infocenter.arm.com/help/index.jsp?topic=/com.arm.doc.ddi0337e/>.

2 Description

The STM32F103xx medium-density performance line family incorporates the high-performance ARM Cortex™-M3 32-bit RISC core operating at a 72 MHz frequency, high-speed embedded memories (Flash memory up to 128 Kbytes and SRAM up to 20 Kbytes), and an extensive range of enhanced I/Os and peripherals connected to two APB buses. All devices offer two 12-bit ADCs, three general purpose 16-bit timers plus one PWM timer, as well as standard and advanced communication interfaces: up to two I²Cs and SPIs, three USARTs, an USB and a CAN.

The devices operate from a 2.0 to 3.6 V power supply. They are available in both the –40 to +85 °C temperature range and the –40 to +105 °C extended temperature range. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F103xx medium-density performance line family includes devices in six different package types: from 36 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the STM32F103xx medium-density performance line microcontroller family suitable for a wide range of applications such as motor drives, application control, medical and handheld equipment, PC and gaming peripherals, GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms, and HVACs.

2.1 Device overview

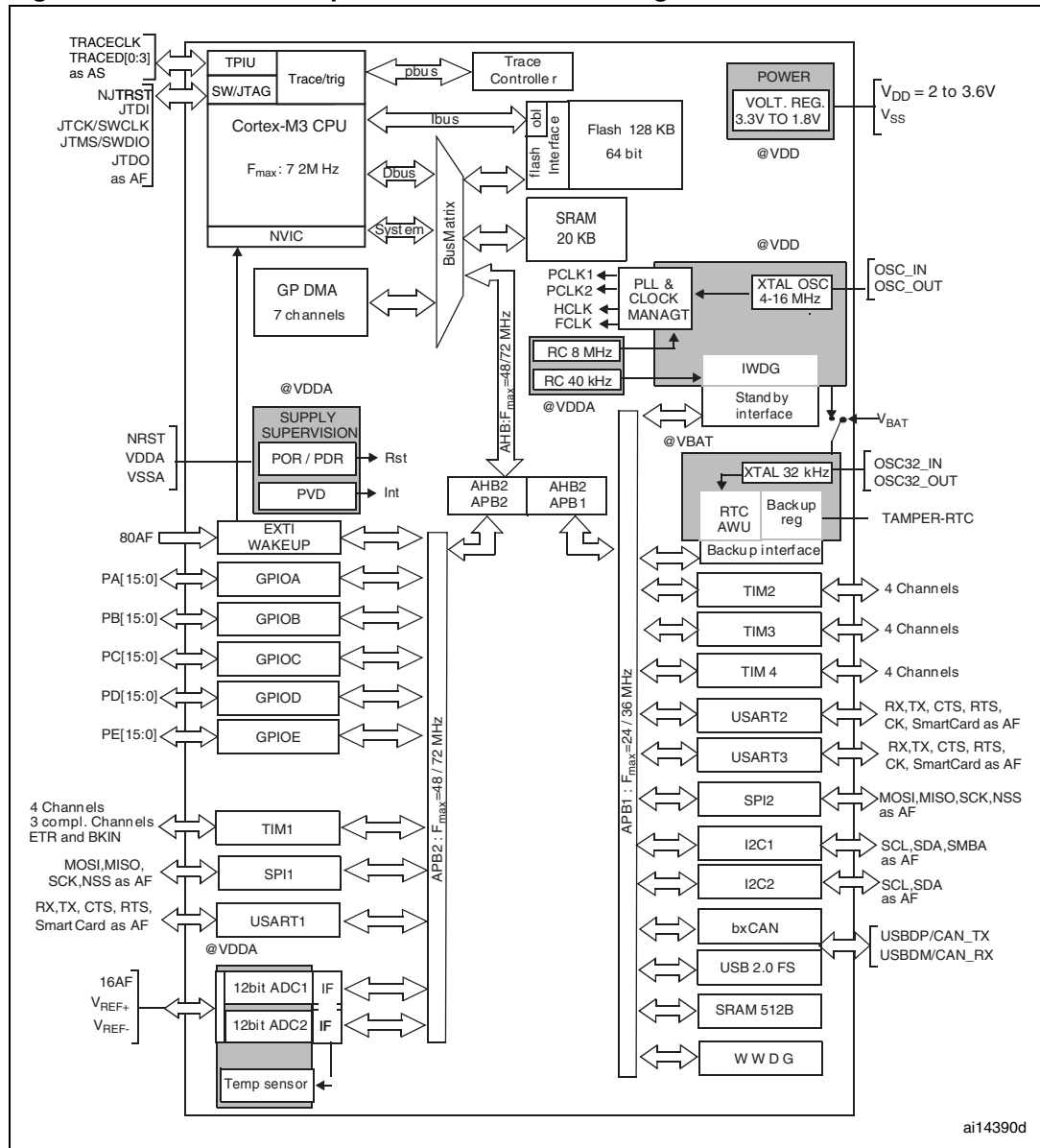
Table 2. STM32F103xx medium-density device features and peripheral counts

| Peripheral | | STM32F103Tx | | STM32F103Cx | | STM32F103Rx | | STM32F103Vx | |
|-------------------------|------------------|---|-----|---------------------|-----|----------------------------|-----|-----------------------------------|-----|
| Flash - Kbytes | | 64 | 128 | 64 | 128 | 64 | 128 | 64 | 128 |
| SRAM - Kbytes | | 20 | | 20 | | 20 | | 20 | |
| Timers | General-purpose | 3 | | 3 | | 3 | | 3 | |
| | Advanced-control | 1 | | 1 | | 1 | | 1 | |
| Communication | SPI | 1 | | 2 | | 2 | | 2 | |
| | I ² C | 1 | | 2 | | 2 | | 2 | |
| | USART | 2 | | 3 | | 3 | | 3 | |
| | USB | 1 | | 1 | | 1 | | 1 | |
| | CAN | 1 | | 1 | | 1 | | 1 | |
| GPIOs | | 26 | | 37 | | 51 | | 80 | |
| 12-bit synchronized ADC | | 2 | | 2 | | 2 | | 2 | |
| Number of channels | | 10 channels | | 10 channels | | 16 channels ⁽¹⁾ | | 16 channels | |
| CPU frequency | | 72 MHz | | | | | | | |
| Operating voltage | | 2.0 to 3.6 V | | | | | | | |
| Operating temperatures | | Ambient temperatures: -40 to +85 °C / -40 to +105 °C (see Table 9) Junction temperature: -40 to + 125 °C (see Table 9) | | | | | | | |
| Packages | | VFQFPN36 | | LQFP48, UFQFPN48 | | LQFP64, TFBGA64 | | LQFP100, LFBGA100, UFBGA100 | |

1. On the TFBGA64 package only 15 channels are available (one analog input pin has been replaced by 'Vref+').

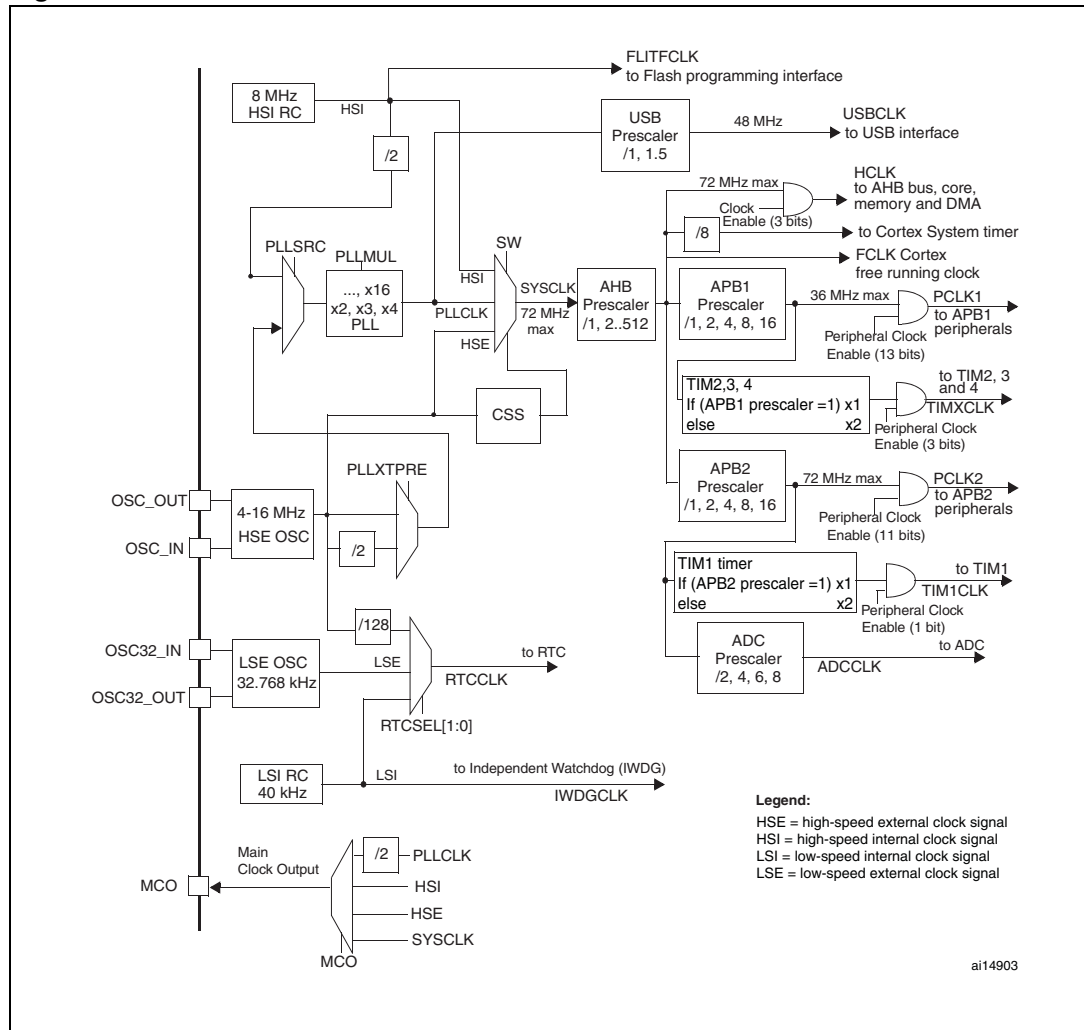


Figure 1. STM32F103xx performance line block diagram



1. T_A = -40 °C to +105 °C (junction temperature up to 125 °C).
2. AF = alternate function on I/O port pin.

Figure 2. Clock tree



1. When the HSI is used as a PLL clock input, the maximum system clock frequency that can be achieved is 64 MHz.
2. For the USB function to be available, both HSE and PLL must be enabled, with USBCLK running at 48 MHz.
3. To have an ADC conversion time of 1 μ s, APB2 must be at 14 MHz, 28 MHz or 56 MHz.

2.2 Full compatibility throughout the family

The STM32F103xx is a complete family whose members are fully pin-to-pin, software and feature compatible. In the reference manual, the STM32F103x4 and STM32F103x6 are identified as low-density devices, the STM32F103x8 and STM32F103xB are referred to as medium-density devices, and the STM32F103xC, STM32F103xD and STM32F103xE are referred to as high-density devices.

Low- and high-density devices are an extension of the STM32F103x8/B devices, they are specified in the STM32F103x4/6 and STM32F103xC/D/E datasheets, respectively. Low-density devices feature lower Flash memory and RAM capacities, less timers and peripherals. High-density devices have higher Flash memory and RAM capacities, and additional peripherals like SDIO, FSMC, I²S and DAC, while remaining fully compatible with the other members of the STM32F103xx family.

The STM32F103x4, STM32F103x6, STM32F103xC, STM32F103xD and STM32F103xE are a drop-in replacement for STM32F103x8/B medium-density devices, allowing the user to try different memory densities and providing a greater degree of freedom during the development cycle.

Moreover, the STM32F103xx performance line family is fully compatible with all existing STM32F101xx access line and STM32F102xx USB access line devices.

Table 3. STM32F103xx family

| Pinout | Low-density devices | | Medium-density devices | | High-density devices | | |
|--------|--|----------------------------|--|--------------|--|--------------|--------------|
| | 16 KB Flash | 32 KB Flash ⁽¹⁾ | 64 KB Flash | 128 KB Flash | 256 KB Flash | 384 KB Flash | 512 KB Flash |
| | 6 KB RAM | 10 KB RAM | 20 KB RAM | 20 KB RAM | 48 KB RAM | 64 KB RAM | 64 KB RAM |
| 144 | | | | | 5 × USARTs 4 × 16-bit timers, 2 × basic timers 3 × SPIs, 2 × I ² Ss, 2 × I ² Cs USB, CAN, 2 × PWM timers 3 × ADCs, 2 × DACs, 1 × SDIO FSMC (100 and 144 pins) | | |
| 100 | | | | | | | |
| 64 | 2 × USARTs 2 × 16-bit timers 1 × SPI, 1 × I ² C, USB, | | 3 × USARTs 3 × 16-bit timers 2 × SPIs, 2 × I ² Cs, USB, | | | | |
| 48 | CAN, 1 × PWM timer | | CAN, 1 × PWM timer | | | | |
| 36 | 2 × ADCs | | 2 × ADCs | | | | |

1. For orderable part numbers that do not show the A internal code after the temperature range code (6 or 7), the reference datasheet for electrical characteristics is that of the STM32F103x8/B medium-density devices.

2.3 Overview

2.3.1 ARM® Cortex™-M3 core with embedded Flash and SRAM

The ARM Cortex™-M3 processor is the latest generation of ARM processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM Cortex™-M3 32-bit RISC processor features exceptional code-efficiency, delivering the high-performance expected from an ARM core in the memory size usually associated with 8- and 16-bit devices.

The STM32F103xx performance line family having an embedded ARM core, is therefore compatible with all ARM tools and software.

Figure 1 shows the general block diagram of the device family.

2.3.2 Embedded Flash memory

64 or 128 Kbytes of embedded Flash is available for storing programs and data.

2.3.3 CRC (cyclic redundancy check) calculation unit

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code from a 32-bit data word and a fixed generator polynomial.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

2.3.4 Embedded SRAM

Twenty Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

2.3.5 Nested vectored interrupt controller (NVIC)

The STM32F103xx performance line embeds a nested vectored interrupt controller able to handle up to 43 maskable interrupt channels (not including the 16 interrupt lines of Cortex™-M3) and 16 priority levels.

- Closely coupled NVIC gives low-latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving* higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.3.6 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 19 edge detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 80 GPIOs can be connected to the 16 external interrupt lines.

2.3.7 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-16 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the high-speed APB domains is 72 MHz. The maximum allowed frequency of the low-speed APB domain is 36 MHz. See [Figure 2](#) for details on the clock tree.

2.3.8 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from User Flash
- Boot from System Memory
- Boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1. For further details please refer to AN2606.

2.3.9 Power supply schemes

- $V_{DD} = 2.0$ to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- $V_{SSA}, V_{DDA} = 2.0$ to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.
- $V_{BAT} = 1.8$ to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

For more details on how to connect power pins, refer to [Figure 14: Power supply scheme](#).

2.3.10 Power supply supervisor

The device has an integrated power-on reset (POR)/power-down reset (PDR) circuitry. It is always active, and ensures proper operation starting from/down to 2 V. The device remains

in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

Refer to [Table 11: Embedded reset and power control block characteristics](#) for the values of $V_{POR/PDR}$ and V_{PVD} .

2.3.11 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in the nominal regulation mode (Run)
- LPR is used in the Stop mode
- Power down is used in Standby mode: the regulator output is in high impedance: the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost)

This regulator is always enabled after reset. It is disabled in Standby mode, providing high impedance output.

2.3.12 Low-power modes

The STM32F103xx performance line supports three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

The Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low power mode.

The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm or the USB wakeup.

- **Standby mode**

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

2.3.13 DMA

The flexible 7-channel general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I²C, USART, general-purpose and advanced-control timers TIMx and ADC.

2.3.14 RTC (real-time clock) and backup registers

The RTC and the backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are ten 16-bit registers used to store 20 bytes of user application data when V_{DD} power is not present.

The real-time clock provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and a periodic interrupt. It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-power RC has a typical frequency of 40 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural crystal deviation. The RTC features a 32-bit programmable counter for long-term measurement using the Compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

2.3.15 Timers and watchdogs

The medium-density STM32F103xx performance line devices include an advanced-control timer, three general-purpose timers, two watchdog timers and a SysTick timer.

Table 4 compares the features of the advanced-control and general-purpose timers.

Table 4. Timer feature comparison

| Timer | Counter resolution | Counter type | Prescaler factor | DMA request generation | Capture/compare channels | Complementary outputs |
|------------------|--------------------|-------------------|---------------------------------|------------------------|--------------------------|-----------------------|
| TIM1 | 16-bit | Up, down, up/down | Any integer between 1 and 65536 | Yes | 4 | Yes |
| TIM2, TIM3, TIM4 | 16-bit | Up, down, up/down | Any integer between 1 and 65536 | Yes | 4 | No |

Advanced-control timer (TIM1)

The advanced-control timer (TIM1) can be seen as a three-phase PWM multiplexed on 6 channels. It has complementary PWM outputs with programmable inserted dead-times. It can also be seen as a complete general-purpose timer. The 4 independent channels can be used for

- Input capture
- Output compare
- PWM generation (edge- or center-aligned modes)
- One-pulse mode output

If configured as a general-purpose 16-bit timer, it has the same features as the TIMx timer. If configured as the 16-bit PWM generator, it has full modulation capability (0-100%).

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switch driven by these outputs.

Many features are shared with those of the general-purpose TIM timers which have the same architecture. The advanced-control timer can therefore work together with the TIM timers via the Timer Link feature for synchronization or event chaining.

General-purpose timers (TIMx)

There are up to three synchronizable general-purpose timers embedded in the STM32F103xx performance line devices. These timers are based on a 16-bit auto-reload up/down counter, a 16-bit prescaler and feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The general-purpose timers can work together with the advanced-control timer via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs. They all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 40 kHz internal RC and as it operates independently of the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes. The counter can be frozen in debug mode.

Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

SysTick timer

This timer is dedicated for OS, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source

2.3.16 I²C bus

Up to two I²C bus interfaces can operate in multimaster and slave modes. They can support standard and fast modes.

They support dual slave addressing (7-bit only) and both 7/10-bit addressing in master mode. A hardware CRC generation/verification is embedded.

They can be served by DMA and they support SM Bus 2.0/PM Bus.

2.3.17 Universal synchronous/asynchronous receiver transmitter (USART)

One of the USART interfaces is able to communicate at speeds of up to 4.5 Mbit/s. The other available interfaces communicate at up to 2.25 Mbit/s. They provide hardware management of the CTS and RTS signals, IrDA SIR ENDEC support, are ISO 7816 compliant and have LIN Master/Slave capability.

All USART interfaces can be served by the DMA controller.

2.3.18 Serial peripheral interface (SPI)

Up to two SPIs are able to communicate up to 18 Mbits/s in slave and master modes in full-duplex and simplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

Both SPIs can be served by the DMA controller.

2.3.19 Controller area network (CAN)

The CAN is compliant with specifications 2.0A and B (active) with a bit rate up to 1 Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. It has three transmit mailboxes, two receive FIFOs with 3 stages and 14 scalable filter banks.

2.3.20 Universal serial bus (USB)

The STM32F103xx performance line embeds a USB device peripheral compatible with the USB full-speed 12 Mbs. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and suspend/resume support. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).

2.3.21 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current-capable.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

I/Os on APB2 with up to 18 MHz toggling speed.

2.3.22 ADC (analog-to-digital converter)

Two 12-bit analog-to-digital converters are embedded into STM32F103xx performance line devices and each ADC shares up to 16 external channels, performing conversions in single-shot or scan modes. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold
- Single shunt

The ADC can be served by the DMA controller.

An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

The events generated by the general-purpose timers (TIMx) and the advanced-control timer (TIM1) can be internally connected to the ADC start trigger, injection trigger, and DMA trigger respectively, to allow the application to synchronize A/D conversion and timers.

2.3.23 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between $2\text{ V} < V_{\text{DDA}} < 3.6\text{ V}$. The temperature sensor is internally connected to the ADC12_IN16 input channel which is used to convert the sensor output voltage into a digital value.

2.3.24 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

3 Pinouts and pin description

Figure 3. STM32F103xx performance line LFBGA100 ballout

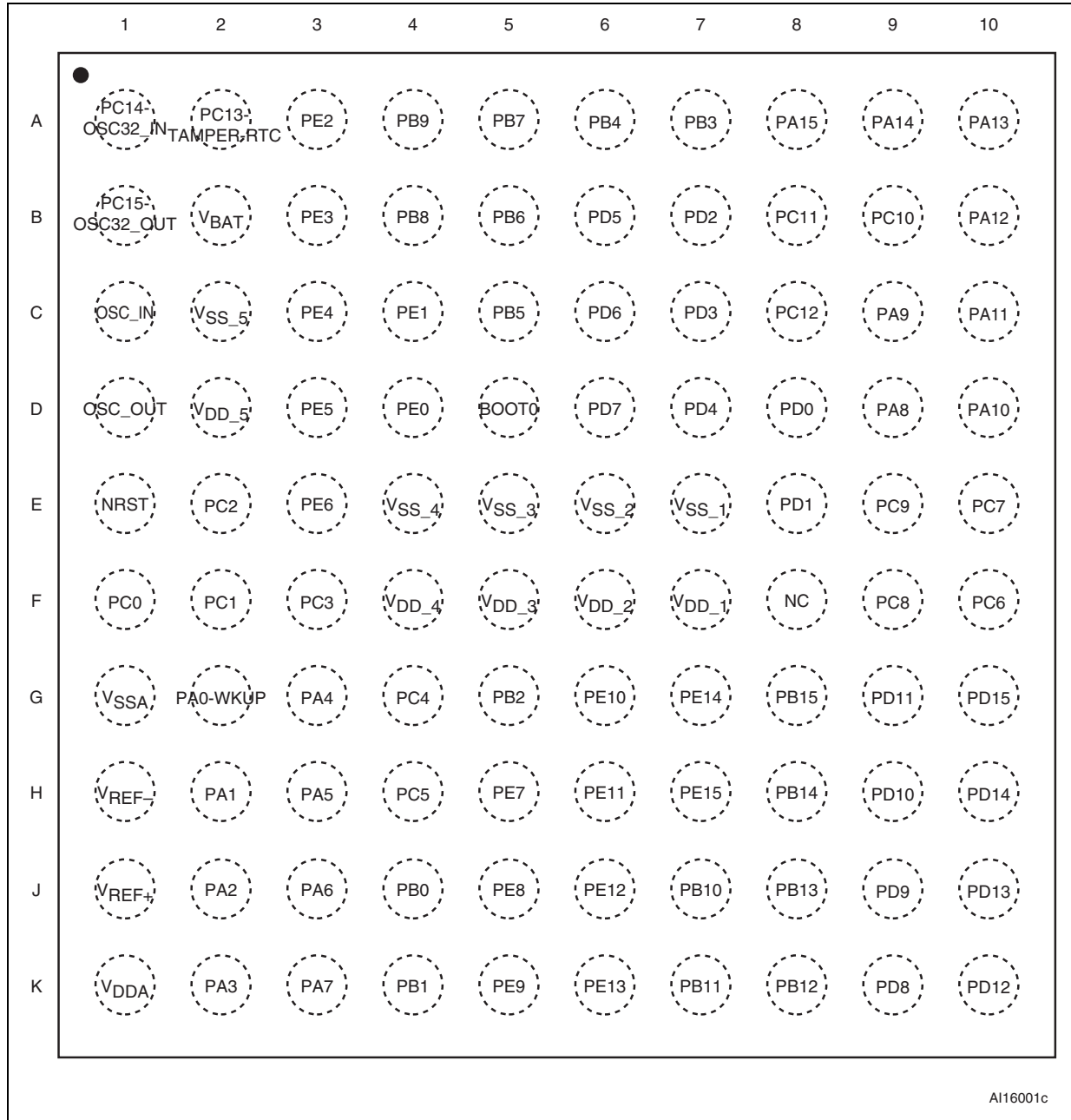


Figure 4. STM32F103xx performance line LQFP100 pinout

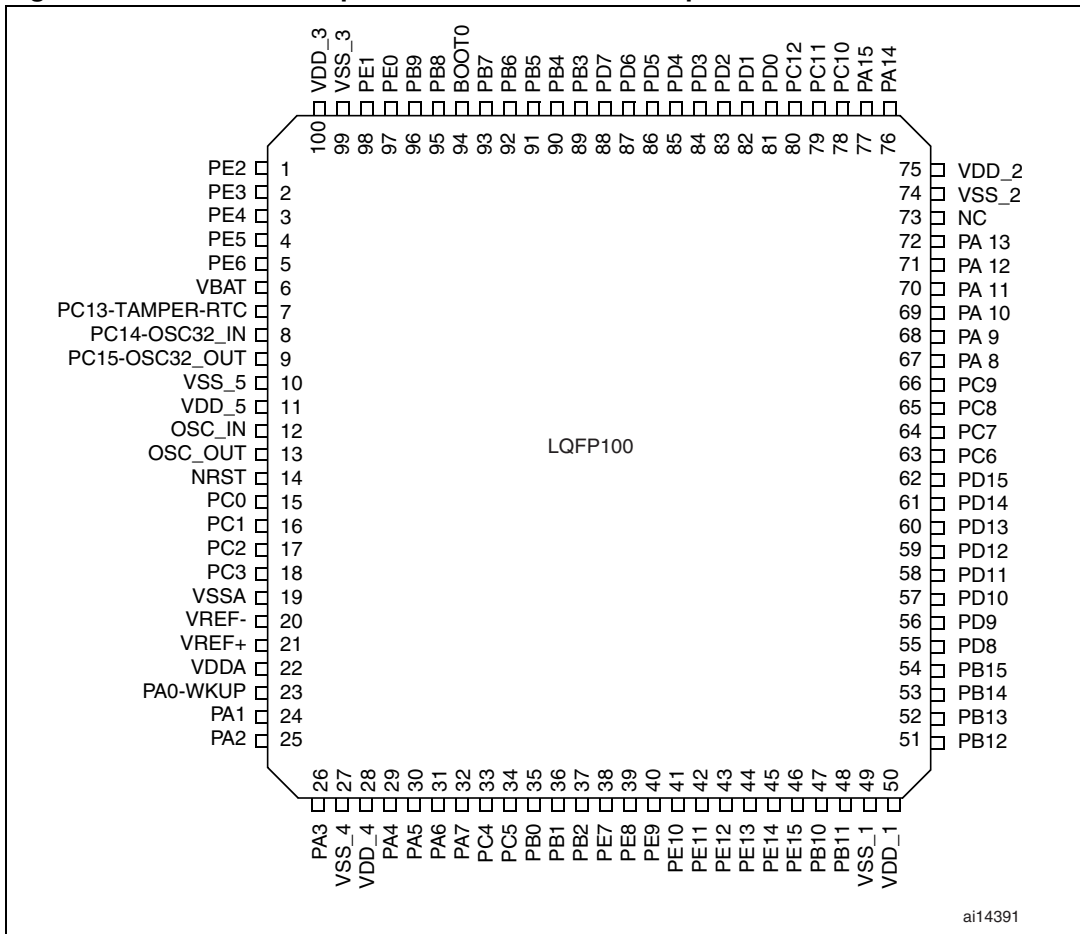
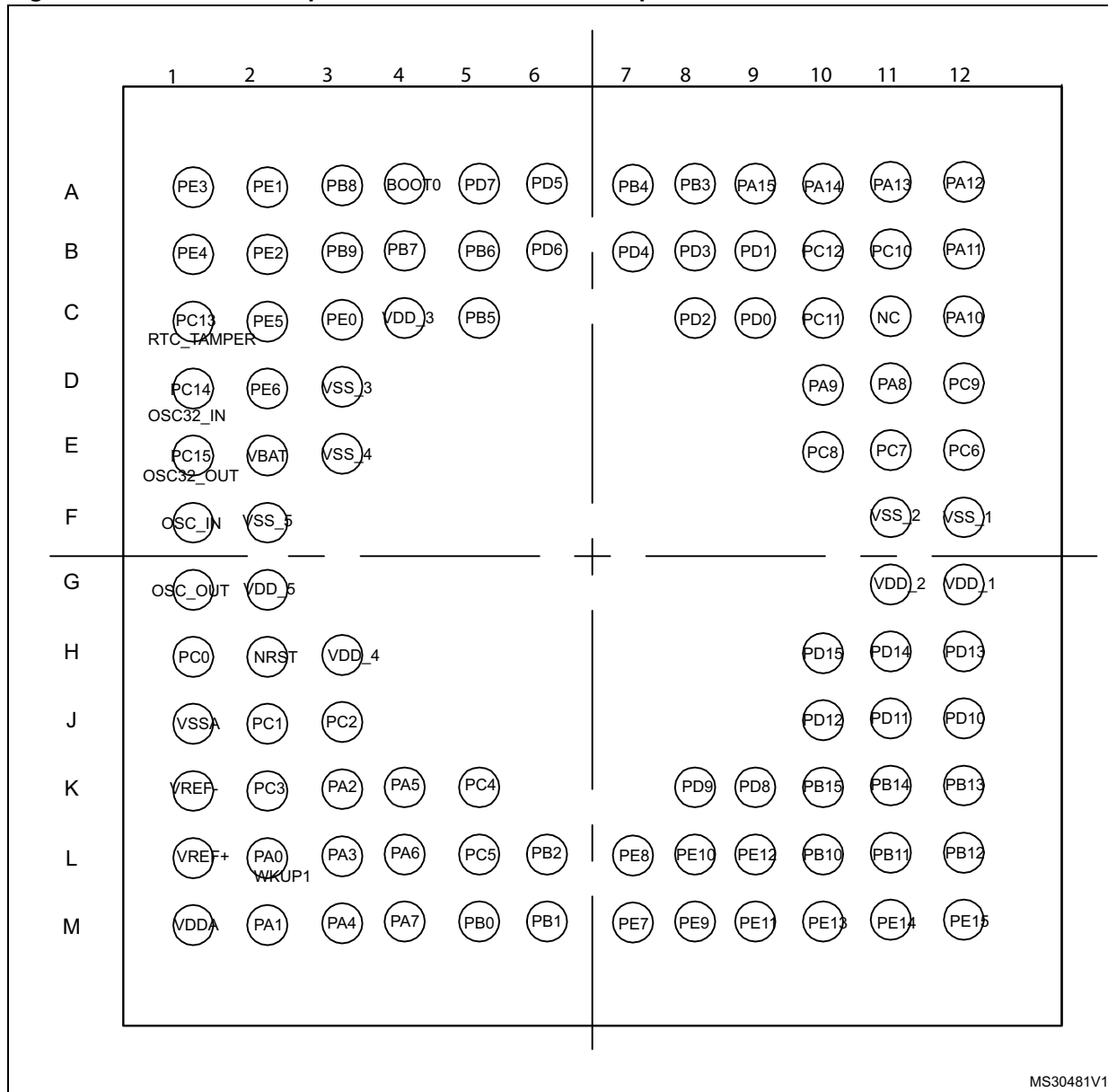


Figure 5. STM32F103xx performance line UFBGA100 pinout



MS30481V1

Figure 6. STM32F103xx performance line LQFP64 pinout

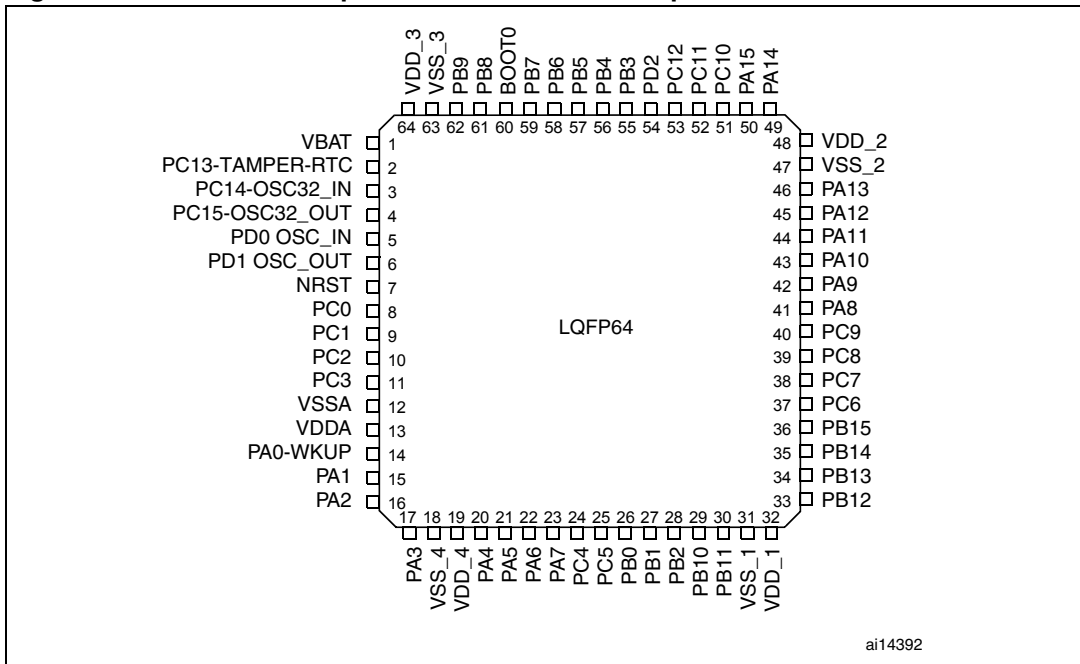


Figure 7. STM32F103xx performance line TFBGA64 ballout

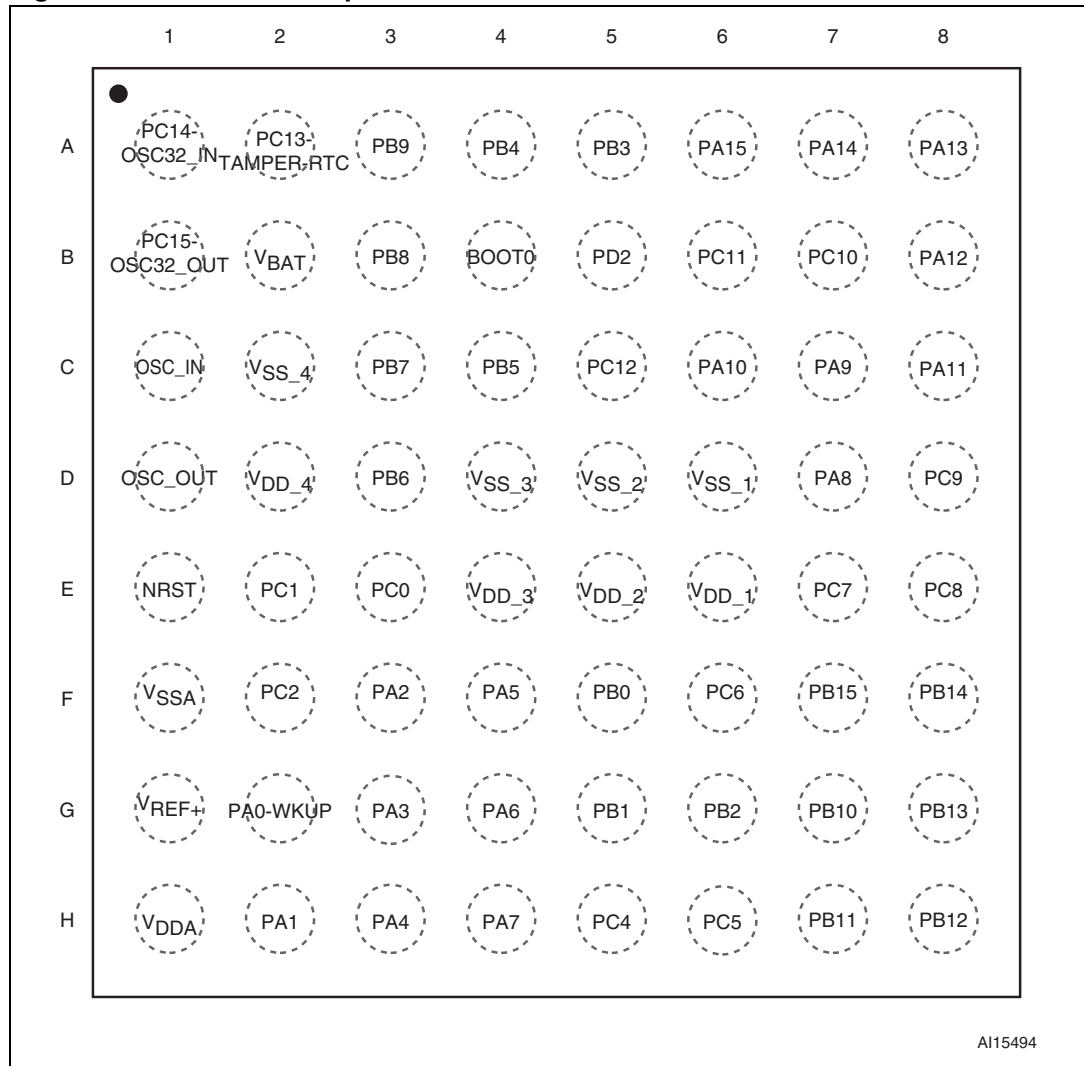


Figure 8. STM32F103xx performance line LQFP48 pinout

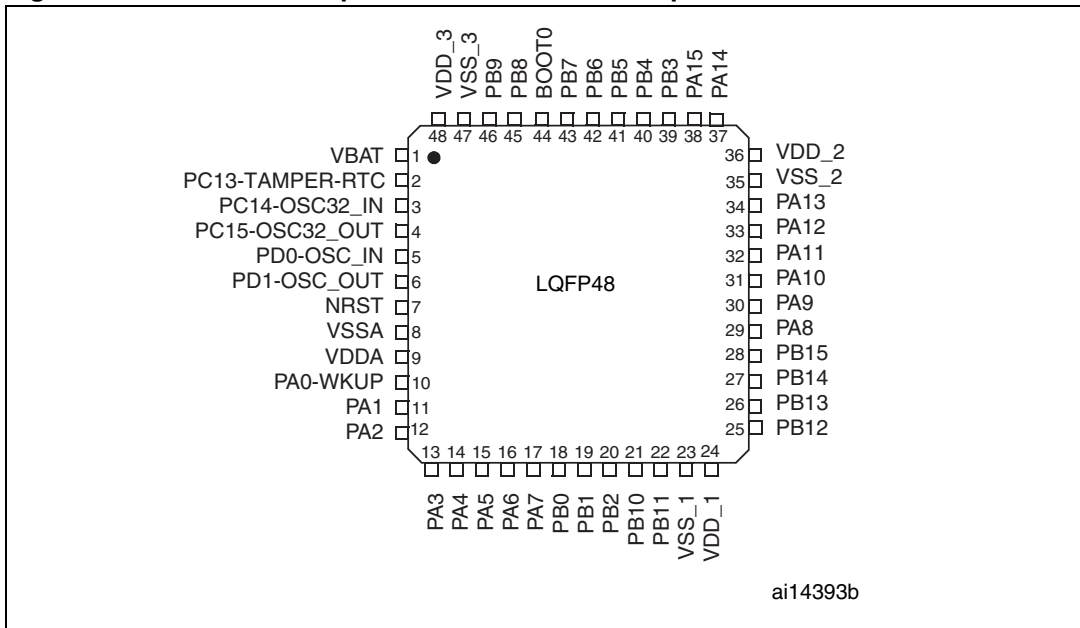


Figure 9. STM32F103xx performance line UFQFPN48 pinout

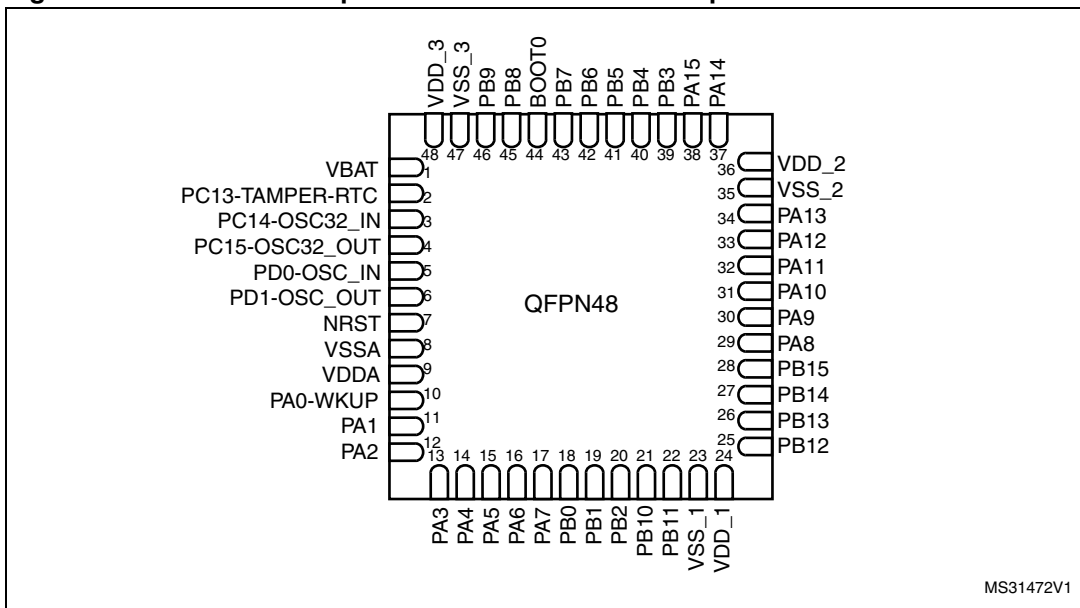


Figure 10. STM32F103xx performance line VFQFPN36 pinout

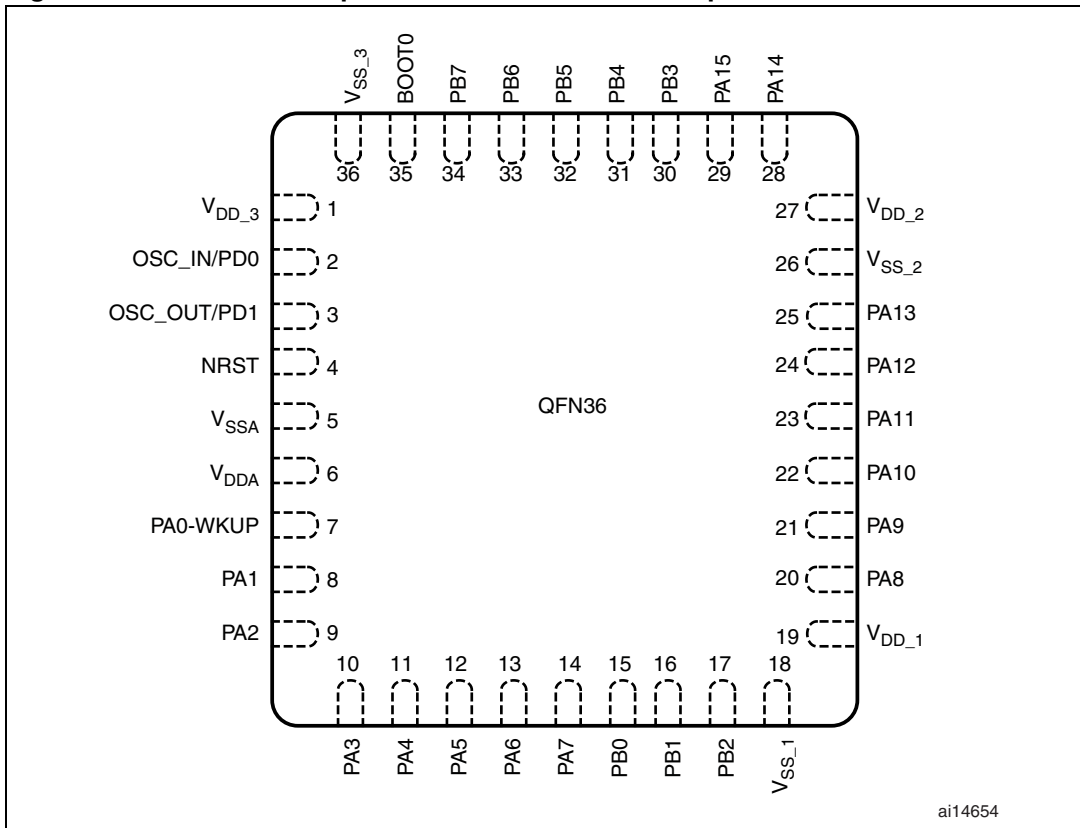


Table 5. Medium-density STM32F103xx pin definitions

| Pins | | | | | | | Pin name | Type ⁽¹⁾ | I / O Level ⁽²⁾ | Main function ⁽³⁾ (after reset) | Alternate functions ⁽⁴⁾ | |
|----------|---------|-----------------|-------------------|--------|---------|----------|--------------------------------|---------------------|----------------------------|---|---|--------------------|
| LFBGA100 | UFBG100 | LQFP48/UFQFPN48 | TFBGA64 | LQFP64 | LQFP100 | VFQFPN36 | | | | | Default | Remap |
| A3 | B2 | - | - | - | 1 | - | PE2 | I/O | FT | PE2 | TRACECK | |
| B3 | A1 | - | - | - | 2 | - | PE3 | I/O | FT | PE3 | TRACED0 | |
| C3 | B1 | - | - | - | 3 | - | PE4 | I/O | FT | PE4 | TRACED1 | |
| D3 | C2 | - | - | - | 4 | - | PE5 | I/O | FT | PE5 | TRACED2 | |
| E3 | D2 | - | - | - | 5 | - | PE6 | I/O | FT | PE6 | TRACED3 | |
| B2 | E2 | 1 | B2 | 1 | 6 | - | V _{BAT} | S | | V _{BAT} | | |
| A2 | C1 | 2 | A2 | 2 | 7 | - | PC13-TAMPER-RTC ⁽⁵⁾ | I/O | | PC13 ⁽⁶⁾ | TAMPER-RTC | |
| A1 | D1 | 3 | A1 | 3 | 8 | - | PC14-OSC32_IN ⁽⁵⁾ | I/O | | PC14 ⁽⁶⁾ | OSC32_IN | |
| B1 | E1 | 4 | B1 | 4 | 9 | - | PC15-OSC32_OUT ⁽⁵⁾ | I/O | | PC15 ⁽⁶⁾ | OSC32_OUT | |
| C2 | F2 | - | - | - | 10 | - | V _{SS_5} | S | | V _{SS_5} | | |
| D2 | G2 | - | - | - | 11 | - | V _{DD_5} | S | | V _{DD_5} | | |
| C1 | F1 | 5 | C1 | 5 | 12 | 2 | OSC_IN | I | | OSC_IN | | PD0 ⁽⁷⁾ |
| D1 | G1 | 6 | D1 | 6 | 13 | 3 | OSC_OUT | O | | OSC_OUT | | PD1 ⁽⁷⁾ |
| E1 | H2 | 7 | E1 | 7 | 14 | 4 | NRST | I/O | | NRST | | |
| F1 | H1 | - | E3 | 8 | 15 | - | PC0 | I/O | | PC0 | ADC12_IN10 | |
| F2 | J2 | - | E2 | 9 | 16 | - | PC1 | I/O | | PC1 | ADC12_IN11 | |
| E2 | J3 | - | F2 | 10 | 17 | - | PC2 | I/O | | PC2 | ADC12_IN12 | |
| F3 | K2 | - | .(⁽⁸⁾ | 11 | 18 | - | PC3 | I/O | | PC3 | ADC12_IN13 | |
| G1 | J1 | 8 | F1 | 12 | 19 | 5 | V _{SSA} | S | | V _{SSA} | | |
| H1 | K1 | - | - | - | 20 | - | V _{REF-} | S | | V _{REF-} | | |
| J1 | L1 | - | G1 ⁽⁸⁾ | - | 21 | - | V _{REF+} | S | | V _{REF+} | | |
| K1 | M1 | 9 | H1 | 13 | 22 | 6 | V _{DDA} | S | | V _{DDA} | | |
| G2 | L2 | 10 | G2 | 14 | 23 | 7 | PA0-WKUP | I/O | | PA0 | WKUP/ USART2_CTS ⁽⁹⁾ / ADC12_IN0/ TIM2_CH1_ ETR ⁽⁹⁾ | |
| H2 | M2 | 11 | H2 | 15 | 24 | 8 | PA1 | I/O | | PA1 | USART2_RTS ⁽⁹⁾ / ADC12_IN1/ TIM2_CH2 ⁽⁹⁾ | |

Table 5. Medium-density STM32F103xx pin definitions (continued)

| Pins | | | | | | | Pin name | Type ⁽¹⁾ | I/O Level ⁽²⁾ | Main function ⁽³⁾ (after reset) | Alternate functions ⁽⁴⁾ | |
|----------|---------|-----------------|---------|--------|---------|---------|-------------------|---------------------|--------------------------|---|--|-----------|
| LFBGA100 | UFBG100 | LQFP48/UFQFPN48 | TFBGA64 | LQFP64 | LQFP100 | VQFPN36 | | | | | Default | Remap |
| J2 | K3 | 12 | F3 | 16 | 25 | 9 | PA2 | I/O | | PA2 | USART2_TX ⁽⁹⁾ / ADC12_IN2/ TIM2_CH3 ⁽⁹⁾ | |
| K2 | L3 | 13 | G3 | 17 | 26 | 10 | PA3 | I/O | | PA3 | USART2_RX ⁽⁹⁾ / ADC12_IN3/ TIM2_CH4 ⁽⁹⁾ | |
| E4 | E3 | - | C2 | 18 | 27 | - | V _{SS_4} | S | | V _{SS_4} | | |
| F4 | H3 | - | D2 | 19 | 28 | - | V _{DD_4} | S | | V _{DD_4} | | |
| G3 | M3 | 14 | H3 | 20 | 29 | 11 | PA4 | I/O | | PA4 | SPI1_NSS ⁽⁹⁾ / USART2_CK ⁽⁹⁾ / ADC12_IN4 | |
| H3 | K4 | 15 | F4 | 21 | 30 | 12 | PA5 | I/O | | PA5 | SPI1_SCK ⁽⁹⁾ / ADC12_IN5 | |
| J3 | L4 | 16 | G4 | 22 | 31 | 13 | PA6 | I/O | | PA6 | SPI1_MISO ⁽⁹⁾ / ADC12_IN6/ TIM3_CH1 ⁽⁹⁾ | TIM1_BKIN |
| K3 | M4 | 17 | H4 | 23 | 32 | 14 | PA7 | I/O | | PA7 | SPI1_MOSI ⁽⁹⁾ / ADC12_IN7/ TIM3_CH2 ⁽⁹⁾ | TIM1_CH1N |
| G4 | K5 | - | H5 | 24 | 33 | | PC4 | I/O | | PC4 | ADC12_IN14 | |
| H4 | L5 | - | H6 | 25 | 34 | | PC5 | I/O | | PC5 | ADC12_IN15 | |
| J4 | M5 | 18 | F5 | 26 | 35 | 15 | PB0 | I/O | | PB0 | ADC12_IN8/ TIM3_CH3 ⁽⁹⁾ | TIM1_CH2N |
| K4 | M6 | 19 | G5 | 27 | 36 | 16 | PB1 | I/O | | PB1 | ADC12_IN9/ TIM3_CH4 ⁽⁹⁾ | TIM1_CH3N |
| G5 | L6 | 20 | G6 | 28 | 37 | 17 | PB2 | I/O | FT | PB2/BOOT1 | | |
| H5 | M7 | - | - | - | 38 | - | PE7 | I/O | FT | PE7 | | TIM1_ETR |
| J5 | L7 | - | - | - | 39 | - | PE8 | I/O | FT | PE8 | | TIM1_CH1N |
| K5 | M8 | - | - | - | 40 | - | PE9 | I/O | FT | PE9 | | TIM1_CH1 |
| G6 | L8 | - | - | - | 41 | - | PE10 | I/O | FT | PE10 | | TIM1_CH2N |
| H6 | M9 | - | - | - | 42 | - | PE11 | I/O | FT | PE11 | | TIM1_CH2 |
| J6 | L9 | - | - | - | 43 | - | PE12 | I/O | FT | PE12 | | TIM1_CH3N |
| K6 | M10 | - | - | - | 44 | - | PE13 | I/O | FT | PE13 | | TIM1_CH3 |
| G7 | M11 | - | - | - | 45 | - | PE14 | I/O | FT | PE14 | | TIM1_CH4 |

Table 5. Medium-density STM32F103xx pin definitions (continued)

| Pins | | | | | | | Pin name | Type ⁽¹⁾ | I/O Level ⁽²⁾ | Main function ⁽³⁾ (after reset) | Alternate functions ⁽⁴⁾ | |
|----------|---------|-----------------|---------|--------|---------|----------|-------------------|---------------------|--------------------------|---|--|--------------------------|
| LFBGA100 | UFBG100 | LQFP48/UFGFPN48 | TFBGA64 | LQFP64 | LQFP100 | VFGFPN36 | | | | | Default | Remap |
| H7 | M12 | - | - | - | 46 | - | PE15 | I/O | FT | PE15 | | TIM1_BKIN |
| J7 | L10 | 21 | G7 | 29 | 47 | - | PB10 | I/O | FT | PB10 | I2C2_SCL/ USART3_TX ⁽⁹⁾ | TIM2_CH3 |
| K7 | L11 | 22 | H7 | 30 | 48 | - | PB11 | I/O | FT | PB11 | I2C2_SDA/ USART3_RX ⁽⁹⁾ | TIM2_CH4 |
| E7 | F12 | 23 | D6 | 31 | 49 | 18 | V _{SS_1} | S | | V _{SS_1} | | |
| F7 | G12 | 24 | E6 | 32 | 50 | 19 | V _{DD_1} | S | | V _{DD_1} | | |
| K8 | L12 | 25 | H8 | 33 | 51 | - | PB12 | I/O | FT | PB12 | SPI2_NSS/ I2C2_SMBAL/ USART3_CK ⁽⁹⁾ / TIM1_BKIN ⁽⁹⁾ | |
| J8 | K12 | 26 | G8 | 34 | 52 | - | PB13 | I/O | FT | PB13 | SPI2_SCK/ USART3_CTS ⁽⁹⁾ / TIM1_CH1N ⁽⁹⁾ | |
| H8 | K11 | 27 | F8 | 35 | 53 | - | PB14 | I/O | FT | PB14 | SPI2_MISO/ USART3_RTS ⁽⁹⁾ / TIM1_CH2N ⁽⁹⁾ | |
| G8 | K10 | 28 | F7 | 36 | 54 | - | PB15 | I/O | FT | PB15 | SPI2_MOSI/ TIM1_CH3N ⁽⁹⁾ | |
| K9 | K9 | - | - | - | 55 | - | PD8 | I/O | FT | PD8 | | USART3_TX |
| J9 | K8 | - | - | - | 56 | - | PD9 | I/O | FT | PD9 | | USART3_RX |
| H9 | J12 | - | - | - | 57 | - | PD10 | I/O | FT | PD10 | | USART3_CK |
| G9 | J11 | - | - | - | 58 | - | PD11 | I/O | FT | PD11 | | USART3_CTS |
| K10 | J10 | - | - | - | 59 | - | PD12 | I/O | FT | PD12 | | TIM4_CH1 / USART3_RTS |
| J10 | H12 | - | - | - | 60 | - | PD13 | I/O | FT | PD13 | | TIM4_CH2 |
| H10 | H11 | - | - | - | 61 | - | PD14 | I/O | FT | PD14 | | TIM4_CH3 |
| G10 | H10 | - | - | - | 62 | - | PD15 | I/O | FT | PD15 | | TIM4_CH4 |
| F10 | E12 | - | F6 | 37 | 63 | - | PC6 | I/O | FT | PC6 | | TIM3_CH1 |
| E10 | E11 | | E7 | 38 | 64 | - | PC7 | I/O | FT | PC7 | | TIM3_CH2 |
| F9 | E10 | | E8 | 39 | 65 | - | PC8 | I/O | FT | PC8 | | TIM3_CH3 |
| E9 | D12 | - | D8 | 40 | 66 | - | PC9 | I/O | FT | PC9 | | TIM3_CH4 |

Table 5. Medium-density STM32F103xx pin definitions (continued)

| Pins | | | | | | | Pin name | Type ⁽¹⁾ | I/O Level ⁽²⁾ | Main function ⁽³⁾ (after reset) | Alternate functions ⁽⁴⁾ | |
|----------|---------|-----------------|---------|--------|---------|---------|-------------------|---------------------|--------------------------|---|--|-------------------------------------|
| LFBGA100 | UFBG100 | LQFP48/UFQFPN48 | TFBGA64 | LQFP64 | LQFP100 | VQFPN36 | | | | | Default | Remap |
| D9 | D11 | 29 | D7 | 41 | 67 | 20 | PA8 | I/O | FT | PA8 | USART1_CK/ TIM1_CH1 ⁽⁹⁾ / MCO | |
| C9 | D10 | 30 | C7 | 42 | 68 | 21 | PA9 | I/O | FT | PA9 | USART1_TX ⁽⁹⁾ / TIM1_CH2 ⁽⁹⁾ | |
| D10 | C12 | 31 | C6 | 43 | 69 | 22 | PA10 | I/O | FT | PA10 | USART1_RX ⁽⁹⁾ / TIM1_CH3 ⁽⁹⁾ | |
| C10 | B12 | 32 | C8 | 44 | 70 | 23 | PA11 | I/O | FT | PA11 | USART1_CTS/ CANRX ⁽⁹⁾ / USBDM/ TIM1_CH4 ⁽⁹⁾ | |
| B10 | A12 | 33 | B8 | 45 | 71 | 24 | PA12 | I/O | FT | PA12 | USART1_RTS/ CANTX ⁽⁹⁾ / /USBDP TIM1_ETR ⁽⁹⁾ | |
| A10 | A11 | 34 | A8 | 46 | 72 | 25 | PA13 | I/O | FT | JTMS/SWDIO | | PA13 |
| F8 | C11 | - | - | - | 73 | - | Not connected | | | | | |
| E6 | F11 | 35 | D5 | 47 | 74 | 26 | V _{SS_2} | S | | V _{SS_2} | | |
| F6 | G11 | 36 | E5 | 48 | 75 | 27 | V _{DD_2} | S | | V _{DD_2} | | |
| A9 | A10 | 37 | A7 | 49 | 76 | 28 | PA14 | I/O | FT | JTCK/SWCLK | | PA14 |
| A8 | A9 | 38 | A6 | 50 | 77 | 29 | PA15 | I/O | FT | JTDI | | TIM2_CH1_ ETR/ PA15 /SPI1_NSS |
| B9 | B11 | - | B7 | 51 | 78 | | PC10 | I/O | FT | PC10 | | USART3_TX |
| B8 | C10 | - | B6 | 52 | 79 | | PC11 | I/O | FT | PC11 | | USART3_RX |
| C8 | B10 | - | C5 | 53 | 80 | | PC12 | I/O | FT | PC12 | | USART3_CK |
| - | C9 | - | C1 | - | 81 | 2 | PD0 | I/O | FT | PD0 | | CANRX |
| - | B9 | - | D1 | - | 82 | 3 | PD1 | I/O | FT | PD1 | | CANTX |
| B7 | C8 | | B5 | 54 | 83 | - | PD2 | I/O | FT | PD2 | TIM3_ETR | |
| C7 | B8 | - | - | - | 84 | - | PD3 | I/O | FT | PD3 | | USART2_CTS |
| D7 | B7 | - | - | - | 85 | - | PD4 | I/O | FT | PD4 | | USART2_RTS |
| B6 | A6 | - | - | - | 86 | - | PD5 | I/O | FT | PD5 | | USART2_TX |
| C6 | B6 | - | - | - | 87 | - | PD6 | I/O | FT | PD6 | | USART2_RX |
| D6 | A5 | - | - | - | 88 | - | PD7 | I/O | FT | PD7 | | USART2_CK |

Table 5. Medium-density STM32F103xx pin definitions (continued)

| Pins | | | | | | | Pin name | Type ⁽¹⁾ | I/O Level ⁽²⁾ | Main function ⁽³⁾ (after reset) | Alternate functions ⁽⁴⁾ | |
|----------|---------|-----------------|---------|--------|---------|----------|-------------------|---------------------|--------------------------|---|--|---|
| LFPGA100 | UFBG100 | LQFP48/UFQFPN48 | TFBGA64 | LQFP64 | LQFP100 | VFGFPN36 | | | | | Default | Remap |
| A7 | A8 | 39 | A5 | 55 | 89 | 30 | PB3 | I/O | FT | JTDO | | TIM2_CH2 / PB3 TRACESWO SPI1_SCK |
| A6 | A7 | 40 | A4 | 56 | 90 | 31 | PB4 | I/O | FT | JNTRST | | TIM3_CH1/ PB4/ SPI1_MISO |
| C5 | C5 | 41 | C4 | 57 | 91 | 32 | PB5 | I/O | | PB5 | I2C1_SMBAI | TIM3_CH2 / SPI1_MOSI |
| B5 | B5 | 42 | D3 | 58 | 92 | 33 | PB6 | I/O | FT | PB6 | I2C1_SCL ⁽⁹⁾ / TIM4_CH1 ⁽⁹⁾ | USART1_TX |
| A5 | B4 | 43 | C3 | 59 | 93 | 34 | PB7 | I/O | FT | PB7 | I2C1_SDA ⁽⁹⁾ / TIM4_CH2 ⁽⁹⁾ | USART1_RX |
| D5 | A4 | 44 | B4 | 60 | 94 | 35 | BOOT0 | I | | BOOT0 | | |
| B4 | A3 | 45 | B3 | 61 | 95 | - | PB8 | I/O | FT | PB8 | TIM4_CH3 ⁽⁹⁾ | I2C1_SCL / CANRX |
| A4 | B3 | 46 | A3 | 62 | 96 | - | PB9 | I/O | FT | PB9 | TIM4_CH4 ⁽⁹⁾ | I2C1_SDA/ CANTX |
| D4 | C3 | - | - | - | 97 | - | PE0 | I/O | FT | PE0 | TIM4_ETR | |
| C4 | A2 | - | - | - | 98 | - | PE1 | I/O | FT | PE1 | | |
| E5 | D3 | 47 | D4 | 63 | 99 | 36 | V _{SS_3} | S | | V _{SS_3} | | |
| F5 | C4 | 48 | E4 | 64 | 100 | 1 | V _{DD_3} | S | | V _{DD_3} | | |

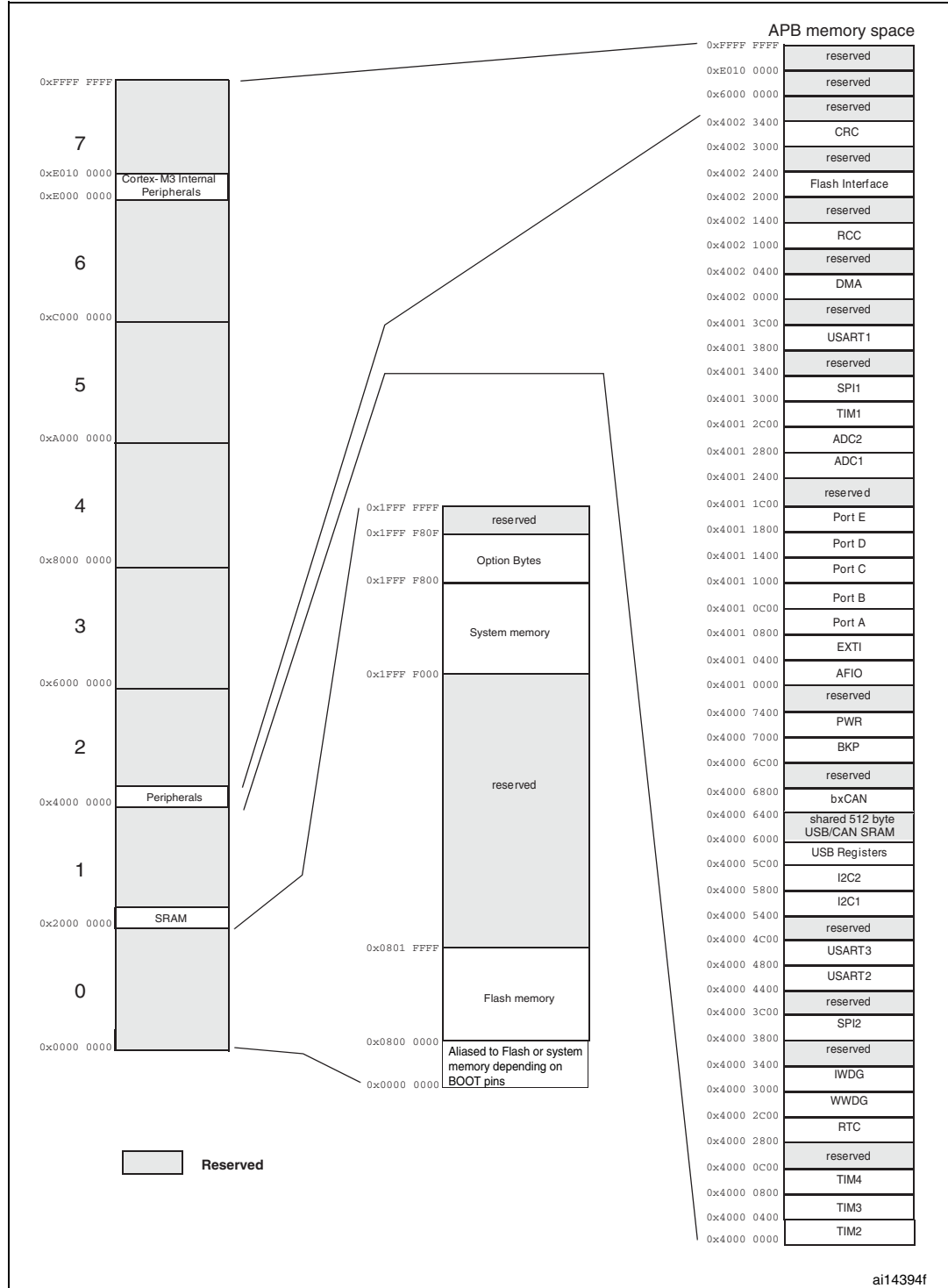
1. I = input, O = output, S = supply.
2. FT = 5 V tolerant.
3. Function availability depends on the chosen device. For devices having reduced peripheral counts, it is always the lower number of peripheral that is included. For example, if a device has only one SPI and two USARTs, they will be called SPI1 and USART1 & USART2, respectively. Refer to [Table 2 on page 10](#).
4. If several peripherals share the same I/O pin, to avoid conflict between these alternate functions only one peripheral should be enabled at a time through the peripheral clock enable bit (in the corresponding RCC peripheral clock enable register).
5. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited: the speed should not exceed 2 MHz with a maximum load of 30 pF and these IOs must not be used as a current source (e.g. to drive an LED).
6. Main function after the first backup domain power-up. Later on, it depends on the contents of the Backup registers even after reset (because these registers are not reset by the main reset). For details on how to manage these IOs, refer to the Battery backup domain and BKP register description sections in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.
7. The pins number 2 and 3 in the VFQFPN36 package, 5 and 6 in the LQFP48, UFQFP48 and LQFP64 packages, and C1 and C2 in the TFBGA64 package are configured as OSC_IN/OSC_OUT after reset, however the functionality of PD0 and PD1 can be remapped by software on these pins. For the LQFP100 package, PD0 and PD1 are available by default, so there is no need for remapping. For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual.
The use of PD0 and PD1 in output mode is limited as they can only be used at 50 MHz in output mode.

8. Unlike in the LQFP64 package, there is no PC3 in the TFBGA64 package. The V_{REF+} functionality is provided instead.
9. This alternate function can be remapped by software to some other port pins (if available on the used package). For more details, refer to the Alternate function I/O and debug configuration section in the STM32F10xxx reference manual, available from the STMicroelectronics website: www.st.com.

4 Memory mapping

The memory map is shown in *Figure 11*.

Figure 11. Memory map



5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ °C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\sigma$).

5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ °C}$, $V_{DD} = 3.3\text{ V}$ (for the $2\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\sigma$).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 12](#).

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 13](#).

Figure 12. Pin loading conditions

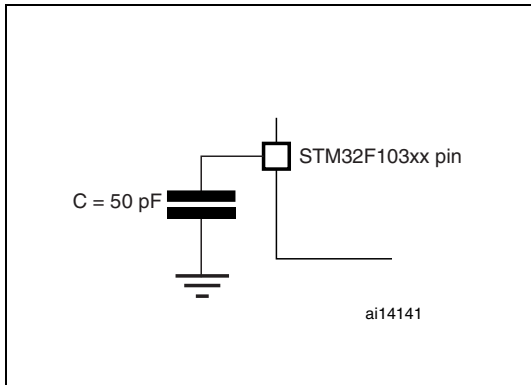
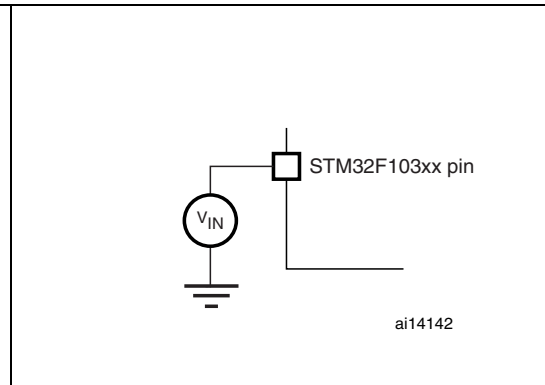
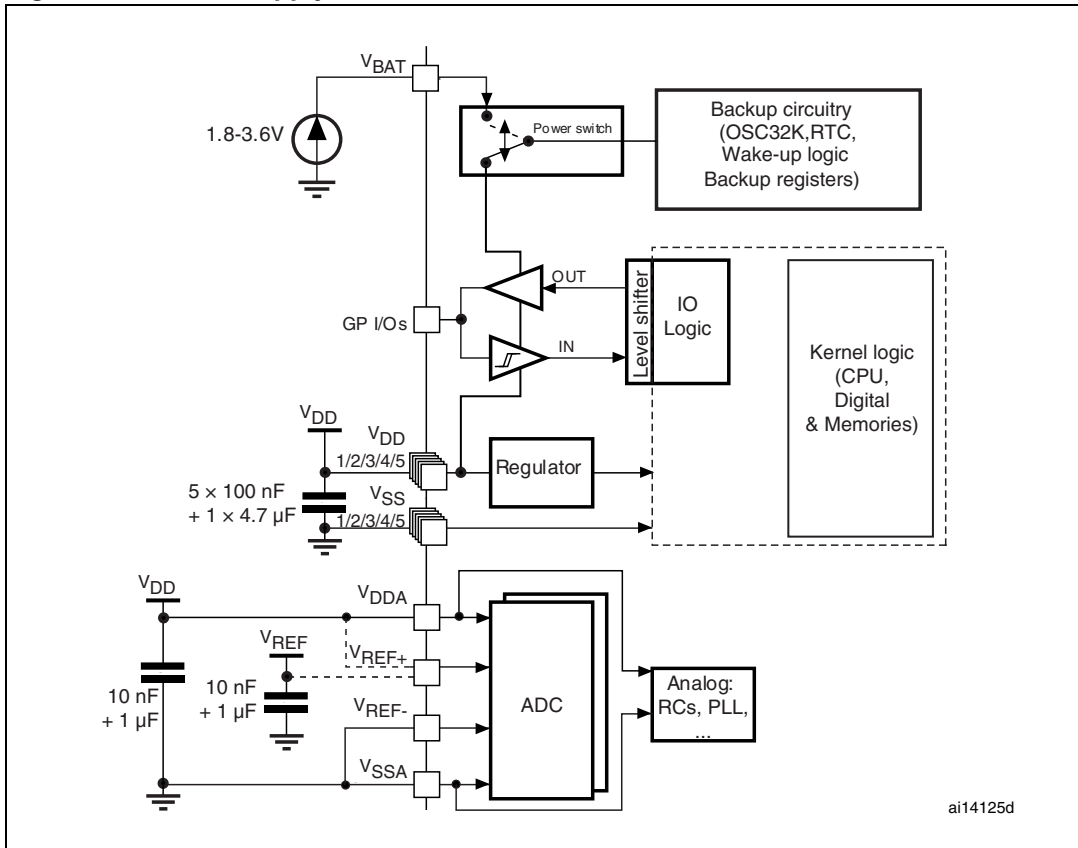


Figure 13. Pin input voltage



5.1.6 Power supply scheme

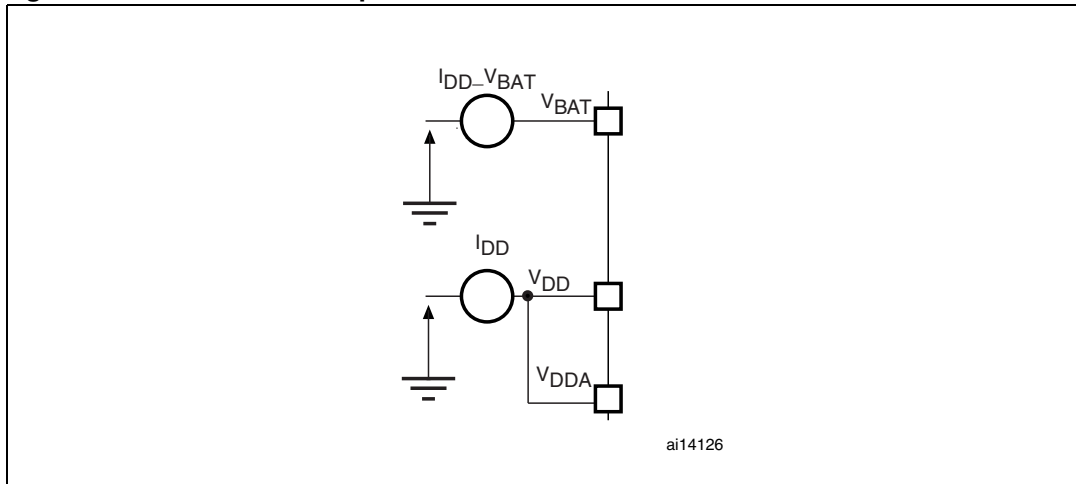
Figure 14. Power supply scheme



Caution: In [Figure 14](#), the 4.7 μ F capacitor must be connected to V_{DD3}.

5.1.7 Current consumption measurement

Figure 15. Current consumption measurement scheme



5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 6: Voltage characteristics](#), [Table 7: Current characteristics](#), and [Table 8: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 6. Voltage characteristics

| Symbol | Ratings | Min | Max | Unit |
|----------------------|---|---|----------------|------|
| $V_{DD} - V_{SS}$ | External main supply voltage (including V_{DDA} and V_{DD}) ⁽¹⁾ | -0.3 | 4.0 | V |
| $V_{IN}^{(2)}$ | Input voltage on five volt tolerant pin | $V_{SS} - 0.3$ | $V_{DD} + 4.0$ | |
| | Input voltage on any other pin | $V_{SS} - 0.3$ | 4.0 | |
| $ \Delta V_{DDx} $ | Variations between different V_{DD} power pins | | 50 | mV |
| $ V_{SSx} - V_{SS} $ | Variations between all the different ground pins | | 50 | |
| $V_{ESD(HBM)}$ | Electrostatic discharge voltage (human body model) | see Section 5.3.11: Absolute maximum ratings (electrical sensitivity) | | |

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to [Table 7: Current characteristics](#) for the maximum allowed injected current values.

Table 7. Current characteristics

| Symbol | Ratings | Max. | Unit |
|-----------------------|---|-------|------|
| I_{VDD} | Total current into V_{DD}/V_{DDA} power lines (source) ⁽¹⁾ | 150 | mA |
| I_{VSS} | Total current out of V_{SS} ground lines (sink) ⁽¹⁾ | 150 | |
| I_{IO} | Output current sunk by any I/O and control pin | 25 | |
| | Output current source by any I/Os and control pin | -25 | |
| $I_{INJ(PIN)}^{(2)}$ | Injected current on five volt tolerant pins ⁽³⁾ | -5/+0 | |
| | Injected current on any other pin ⁽⁴⁾ | ± 5 | |
| $\Sigma I_{INJ(PIN)}$ | Total injected current (sum of all I/O and control pins) ⁽⁵⁾ | ± 25 | |

- All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
- Negative injection disturbs the analog performance of the device. See note 2. on page 77.
- Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 6: Voltage characteristics](#) for the maximum allowed input voltage values.
- A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to [Table 6: Voltage characteristics](#) for the maximum allowed input voltage values.
- When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 8. Thermal characteristics

| Symbol | Ratings | Value | Unit |
|-----------|------------------------------|-------------|------|
| T_{STG} | Storage temperature range | -65 to +150 | °C |
| T_J | Maximum junction temperature | 150 | °C |

5.3 Operating conditions

5.3.1 General operating conditions

Table 9. General operating conditions

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------|---|--|-----|-----|------|
| f_{HCLK} | Internal AHB clock frequency | | 0 | 72 | MHz |
| f_{PCLK1} | Internal APB1 clock frequency | | 0 | 36 | |
| f_{PCLK2} | Internal APB2 clock frequency | | 0 | 72 | |
| V_{DD} | Standard operating voltage | | 2 | 3.6 | V |
| $V_{DDA}^{(1)}$ | Analog operating voltage (ADC not used) | Must be the same potential as $V_{DD}^{(2)}$ | 2 | 3.6 | |
| | Analog operating voltage (ADC used) | | 2.4 | 3.6 | |
| V_{BAT} | Backup operating voltage | | 1.8 | 3.6 | |

Table 9. General operating conditions (continued)

| Symbol | Parameter | Conditions | Min | Max | Unit | |
|-----------------|---|--------------------------------------|-------------------------------|----------------------|------|-----|
| V _{IN} | I/O input voltage | Standard IO | -0.3 | V _{DD} +0.3 | V | |
| | | FT IO ⁽³⁾ | 2 V < V _{DD} ≤ 3.6 V | -0.3 | | 5.5 |
| | | | V _{DD} = 2 V | -0.3 | | 5.2 |
| | | BOOT0 | 0 | 5.5 | | |
| P _D | Power dissipation at T _A = 85 °C for suffix 6 or T _A = 105 °C for suffix 7 ⁽⁴⁾ | LFBGA100 | | 454 | mW | |
| | | LQFP100 | | 434 | | |
| | | UFBGA100 | | 339 | | |
| | | TFBGA64 | | 308 | | |
| | | LQFP64 | | 444 | | |
| | | LQFP48 | | 363 | | |
| | | UFQFPN48 | | 624 | | |
| | | VFQFPN36 | | 1000 | | |
| T _A | Ambient temperature for 6 suffix version | Maximum power dissipation | -40 | 85 | °C | |
| | | Low power dissipation ⁽⁵⁾ | -40 | 105 | | |
| | Ambient temperature for 7 suffix version | Maximum power dissipation | -40 | 105 | | |
| | | Low power dissipation ⁽⁵⁾ | -40 | 125 | | |
| T _J | Junction temperature range | 6 suffix version | -40 | 105 | | |
| | | 7 suffix version | -40 | 125 | | |

1. When the ADC is used, refer to [Table 46: ADC characteristics](#).
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and operation.
3. To sustain a voltage higher than V_{DD}+0.3 V, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see [Table 6.2: Thermal characteristics on page 93](#)).
5. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see [Table 6.2: Thermal characteristics on page 93](#)).

5.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A.

Table 10. Operating conditions at power-up / power-down

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|--------------------------------|------------|-----|-----|------|
| t _{VDD} | V _{DD} rise time rate | | 0 | ∞ | μs/V |
| | V _{DD} fall time rate | | 20 | ∞ | |

5.3.3 Embedded reset and power control block characteristics

The parameters given in [Table 11](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 11. Embedded reset and power control block characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------------|---|-----------------------------|--------------------|------|------|------|
| V _{PVD} | Programmable voltage detector level selection | PLS[2:0]=000 (rising edge) | 2.1 | 2.18 | 2.26 | V |
| | | PLS[2:0]=000 (falling edge) | 2 | 2.08 | 2.16 | V |
| | | PLS[2:0]=001 (rising edge) | 2.19 | 2.28 | 2.37 | V |
| | | PLS[2:0]=001 (falling edge) | 2.09 | 2.18 | 2.27 | V |
| | | PLS[2:0]=010 (rising edge) | 2.28 | 2.38 | 2.48 | V |
| | | PLS[2:0]=010 (falling edge) | 2.18 | 2.28 | 2.38 | V |
| | | PLS[2:0]=011 (rising edge) | 2.38 | 2.48 | 2.58 | V |
| | | PLS[2:0]=011 (falling edge) | 2.28 | 2.38 | 2.48 | V |
| | | PLS[2:0]=100 (rising edge) | 2.47 | 2.58 | 2.69 | V |
| | | PLS[2:0]=100 (falling edge) | 2.37 | 2.48 | 2.59 | V |
| | | PLS[2:0]=101 (rising edge) | 2.57 | 2.68 | 2.79 | V |
| | | PLS[2:0]=101 (falling edge) | 2.47 | 2.58 | 2.69 | V |
| | | PLS[2:0]=110 (rising edge) | 2.66 | 2.78 | 2.9 | V |
| | | PLS[2:0]=110 (falling edge) | 2.56 | 2.68 | 2.8 | V |
| | | PLS[2:0]=111 (rising edge) | 2.76 | 2.88 | 3 | V |
| PLS[2:0]=111 (falling edge) | 2.66 | 2.78 | 2.9 | V | | |
| V _{PVDhyst} ⁽²⁾ | PVD hysteresis | | | 100 | | mV |
| V _{POR/PDR} | Power on/power down reset threshold | Falling edge | 1.8 ⁽¹⁾ | 1.88 | 1.96 | V |
| | | Rising edge | 1.84 | 1.92 | 2.0 | V |
| V _{PDRhyst} ⁽²⁾ | PDR hysteresis | | | 40 | | mV |
| T _{RSTTEMPO} ⁽²⁾ | Reset temporization | | 1 | 2.5 | 4.5 | ms |

1. The product behavior is guaranteed by design down to the minimum V_{POR/PDR} value.

2. Guaranteed by design, not tested in production.

5.3.4 Embedded reference voltage

The parameters given in [Table 12](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 12. Embedded internal reference voltage

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------------|---|--|------|------|---------------------|--------|
| V_{REFINT} | Internal reference voltage | $-40\text{ °C} < T_A < +105\text{ °C}$ | 1.16 | 1.20 | 1.26 | V |
| | | $-40\text{ °C} < T_A < +85\text{ °C}$ | 1.16 | 1.20 | 1.24 | V |
| $T_{S_vrefint}^{(1)}$ | ADC sampling time when reading the internal reference voltage | | | 5.1 | 17.1 ⁽²⁾ | μs |
| $V_{RERINT}^{(2)}$ | Internal reference voltage spread over the temperature range | $V_{DD} = 3\text{ V} \pm 10\text{ mV}$ | | | 10 | mV |
| $T_{Coeff}^{(2)}$ | Temperature coefficient | | | | 100 | ppm/°C |

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production.

5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 15: Current consumption measurement scheme](#).

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above)
- Prefetch in ON (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/2$, $f_{PCLK2} = f_{HCLK}$

The parameters given in [Table 13](#), [Table 14](#) and [Table 15](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 13. Maximum current consumption in Run mode, code with data processing running from Flash

| Symbol | Parameter | Conditions | f _{HCLK} | Max ⁽¹⁾ | | Unit |
|-----------------|----------------------------|--|-------------------|------------------------|-------------------------|------|
| | | | | T _A = 85 °C | T _A = 105 °C | |
| I _{DD} | Supply current in Run mode | External clock ⁽²⁾ , all peripherals enabled | 72 MHz | 50 | 50.3 | mA |
| | | | 48 MHz | 36.1 | 36.2 | |
| | | | 36 MHz | 28.6 | 28.7 | |
| | | | 24 MHz | 19.9 | 20.1 | |
| | | | 16 MHz | 14.7 | 14.9 | |
| | | | 8 MHz | 8.6 | 8.9 | |
| | | External clock ⁽²⁾ , all peripherals disabled | 72 MHz | 32.8 | 32.9 | |
| | | | 48 MHz | 24.4 | 24.5 | |
| | | | 36 MHz | 19.8 | 19.9 | |
| | | | 24 MHz | 13.9 | 14.2 | |
| | | | 16 MHz | 10.7 | 11 | |
| | | | 8 MHz | 6.8 | 7.1 | |

1. Based on characterization, not tested in production.
2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 14. Maximum current consumption in Run mode, code with data processing running from RAM

| Symbol | Parameter | Conditions | f _{HCLK} | Max ⁽¹⁾ | | Unit |
|-----------------|----------------------------|--|-------------------|------------------------|-------------------------|------|
| | | | | T _A = 85 °C | T _A = 105 °C | |
| I _{DD} | Supply current in Run mode | External clock ⁽²⁾ , all peripherals enabled | 72 MHz | 48 | 50 | mA |
| | | | 48 MHz | 31.5 | 32 | |
| | | | 36 MHz | 24 | 25.5 | |
| | | | 24 MHz | 17.5 | 18 | |
| | | | 16 MHz | 12.5 | 13 | |
| | | | 8 MHz | 7.5 | 8 | |
| | | External clock ⁽²⁾ , all peripherals disabled | 72 MHz | 29 | 29.5 | |
| | | | 48 MHz | 20.5 | 21 | |
| | | | 36 MHz | 16 | 16.5 | |
| | | | 24 MHz | 11.5 | 12 | |
| | | | 16 MHz | 8.5 | 9 | |
| | | | 8 MHz | 5.5 | 6 | |

1. Based on characterization, tested in production at V_{DD} max, f_{HCLK} max.
2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Figure 16. Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled

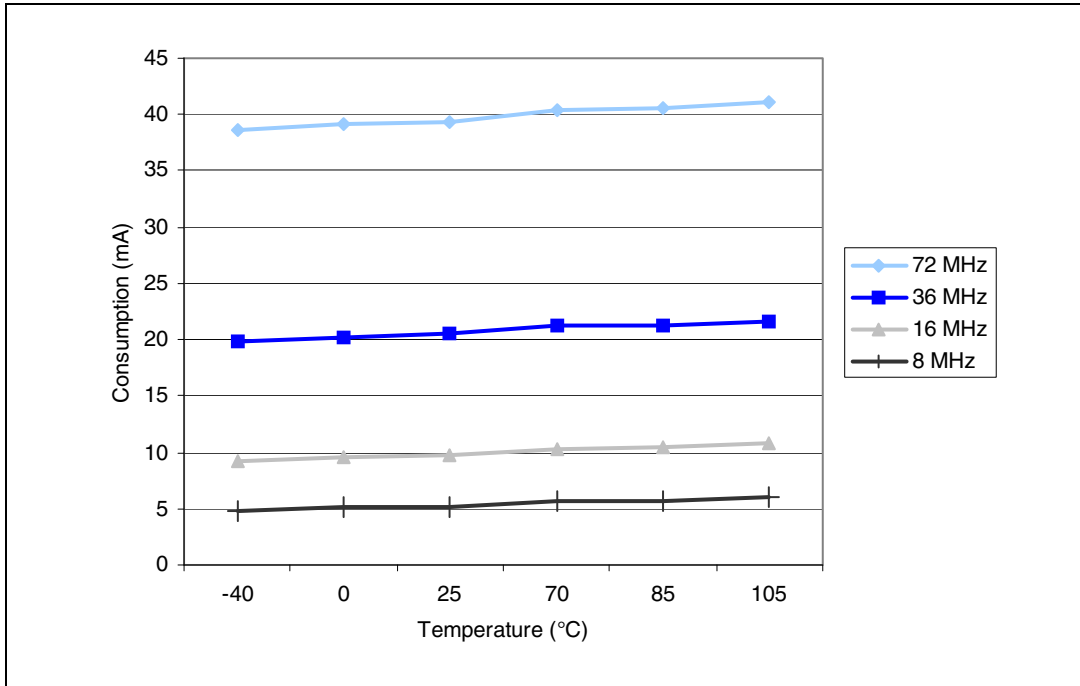


Figure 17. Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals disabled

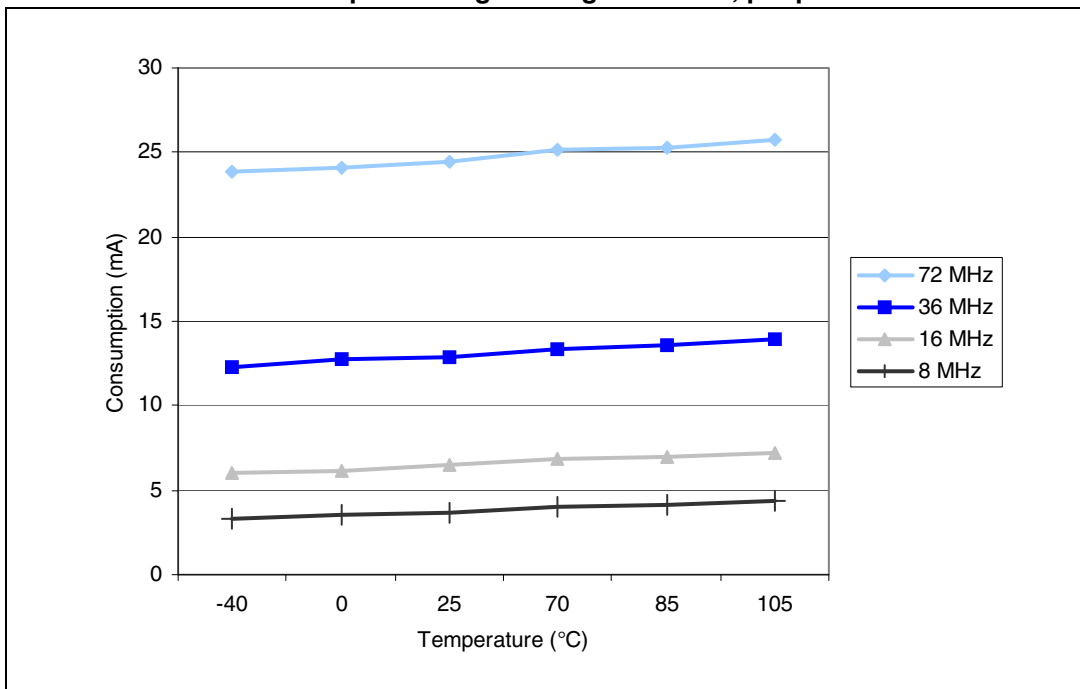


Table 15. Maximum current consumption in Sleep mode, code running from Flash or RAM

| Symbol | Parameter | Conditions | f _{HCLK} | Max ⁽¹⁾ | | Unit |
|-----------------|------------------------------|--|-------------------|------------------------|-------------------------|------|
| | | | | T _A = 85 °C | T _A = 105 °C | |
| I _{DD} | Supply current in Sleep mode | External clock ⁽²⁾ , all peripherals enabled | 72 MHz | 30 | 32 | mA |
| | | | 48 MHz | 20 | 20.5 | |
| | | | 36 MHz | 15.5 | 16 | |
| | | | 24 MHz | 11.5 | 12 | |
| | | | 16 MHz | 8.5 | 9 | |
| | | | 8 MHz | 5.5 | 6 | |
| | | External clock ⁽²⁾ , all peripherals disabled | 72 MHz | 7.5 | 8 | |
| | | | 48 MHz | 6 | 6.5 | |
| | | | 36 MHz | 5 | 5.5 | |
| | | | 24 MHz | 4.5 | 5 | |
| | | | 16 MHz | 4 | 4.5 | |
| | | | 8 MHz | 3 | 4 | |

1. based on characterization, tested in production at V_{DD max}, f_{HCLK max} with peripherals enabled.

2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 16. Typical and maximum current consumptions in Stop and Standby modes

| Symbol | Parameter | Conditions | Typ ⁽¹⁾ | | | Max | | Unit |
|----------------------|--------------------------------|---|---|---|---|------------------------|-------------------------|------|
| | | | V _{DD} /V _{BAT} = 2.0 V | V _{DD} /V _{BAT} = 2.4 V | V _{DD} /V _{BAT} = 3.3 V | T _A = 85 °C | T _A = 105 °C | |
| I _{DD} | Supply current in Stop mode | Regulator in Run mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog) | - | 23.5 | 24 | 200 | 370 | μA |
| | | Regulator in Low Power mode, low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog) | - | 13.5 | 14 | 180 | 340 | |
| | Supply current in Standby mode | Low-speed internal RC oscillator and independent watchdog ON | - | 2.6 | 3.4 | - | - | |
| | | Low-speed internal RC oscillator ON, independent watchdog OFF | - | 2.4 | 3.2 | - | - | |
| | | Low-speed internal RC oscillator and independent watchdog OFF, low-speed oscillator and RTC OFF | - | 1.7 | 2 | 4 | 5 | |
| I _{DD_VBAT} | Backup domain supply current | Low-speed oscillator and RTC ON | 0.9 | 1.1 | 1.4 | 1.9 ⁽²⁾ | 2.2 | |

1. Typical values are measured at T_A = 25 °C.
2. Based on characterization, not tested in production.

Figure 18. Typical current consumption on V_{BAT} with RTC on versus temperature at different V_{BAT} values

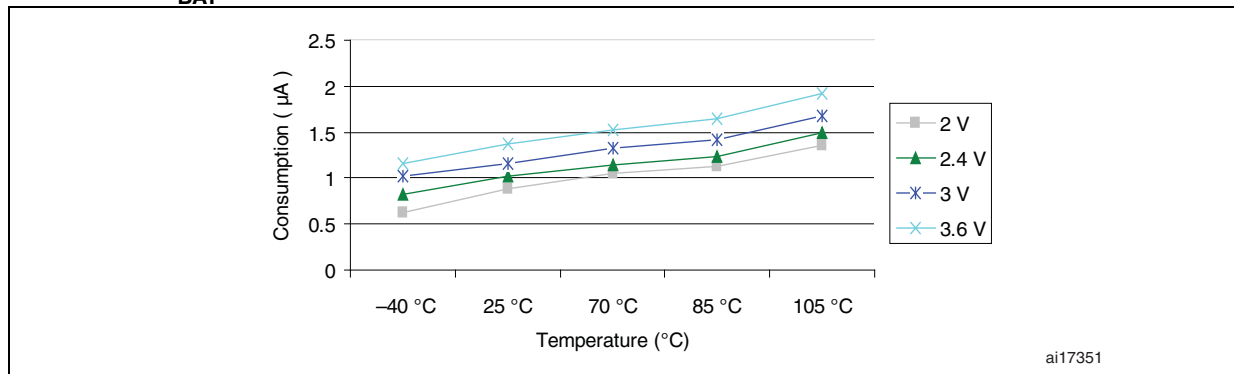


Figure 19. Typical current consumption in Stop mode with regulator in Run mode versus temperature at $V_{DD} = 3.3\text{ V}$ and 3.6 V

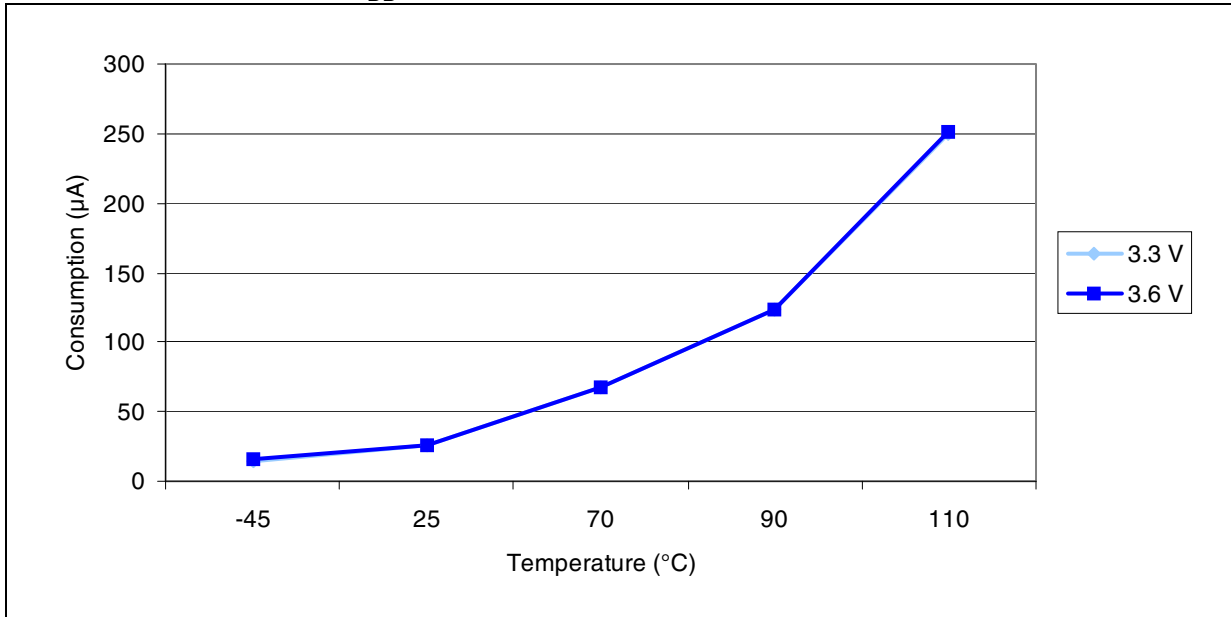


Figure 20. Typical current consumption in Stop mode with regulator in Low-power mode versus temperature at $V_{DD} = 3.3\text{ V}$ and 3.6 V

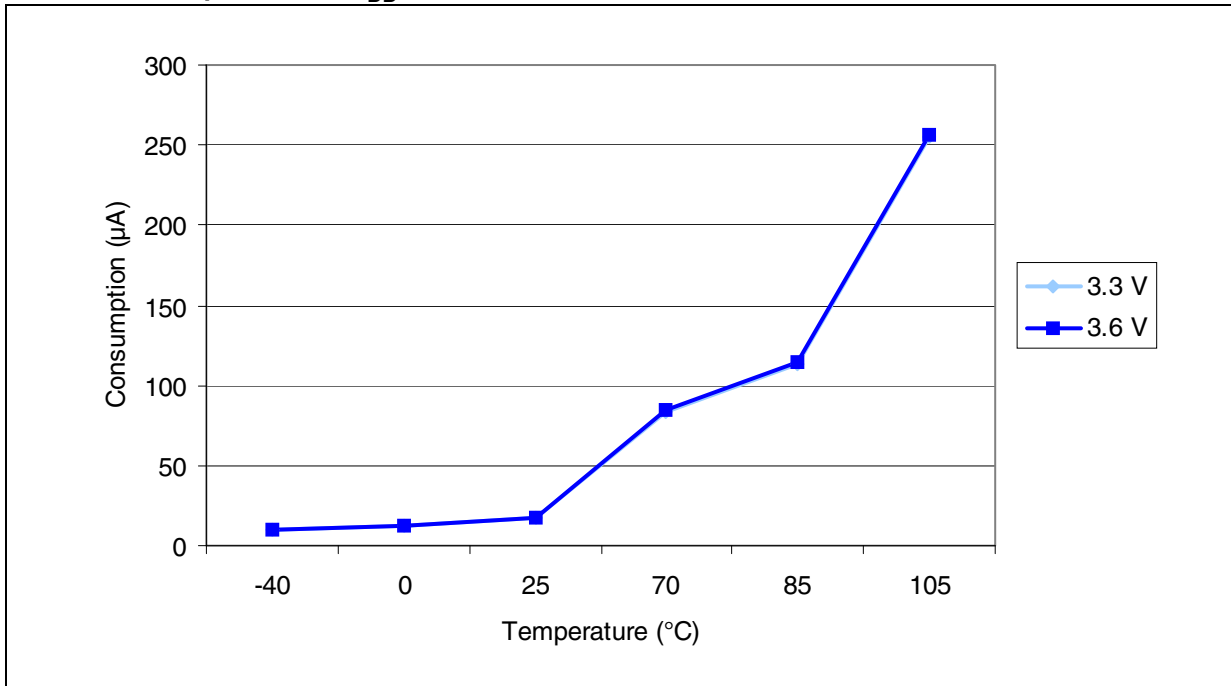
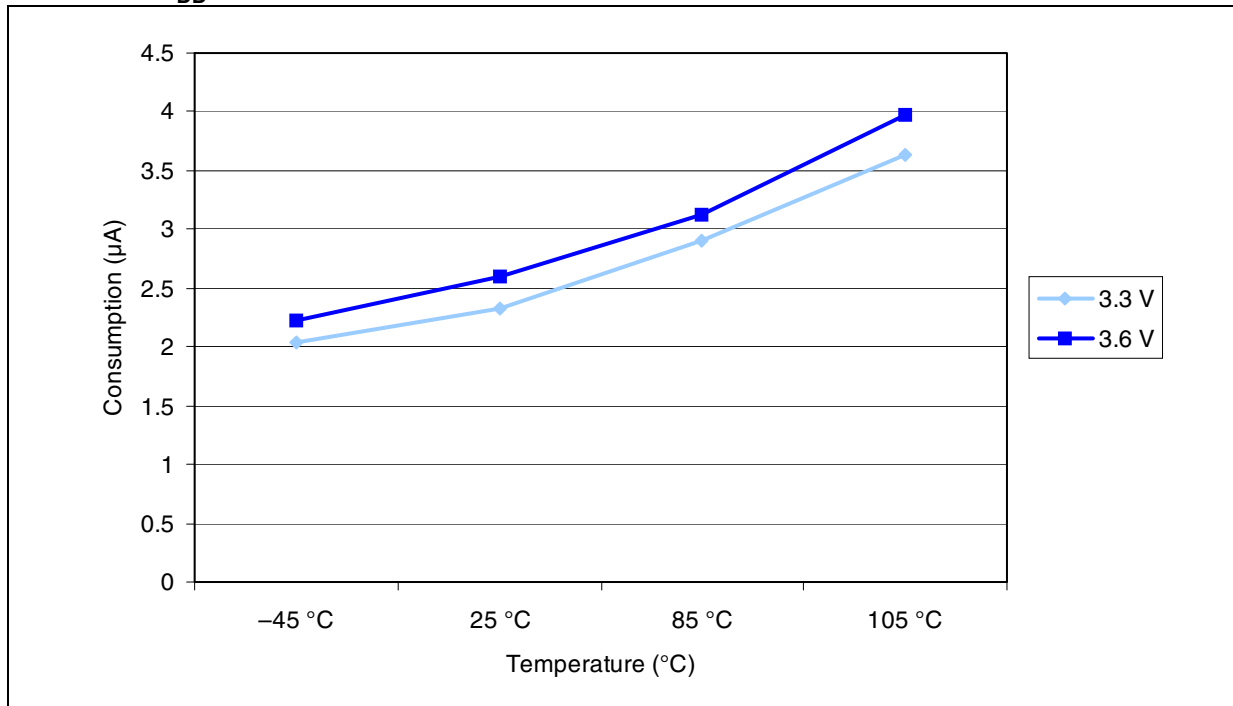


Figure 21. Typical current consumption in Standby mode versus temperature at $V_{DD} = 3.3\text{ V}$ and 3.6 V



Typical current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash access time is adjusted to f_{HCLK} frequency (0 wait state from 0 to 24 MHz, 1 wait state from 24 to 48 MHz and 2 wait states above).
- Ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).
- Prefetch is ON (Reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/4$, $f_{PCLK2} = f_{HCLK}/2$, $f_{ADCCLK} = f_{PCLK2}/4$

Table 17. Typical current consumption in Run mode, code with data processing running from Flash

| Symbol | Parameter | Conditions | f _{HCLK} | Typ ⁽¹⁾ | | Unit |
|-----------------|----------------------------|---|-------------------|--|--------------------------|------|
| | | | | All peripherals enabled ⁽²⁾ | All peripherals disabled | |
| I _{DD} | Supply current in Run mode | External clock ⁽³⁾ | 72 MHz | 36 | 27 | mA |
| | | | 48 MHz | 24.2 | 18.6 | |
| | | | 36 MHz | 19 | 14.8 | |
| | | | 24 MHz | 12.9 | 10.1 | |
| | | | 16 MHz | 9.3 | 7.4 | |
| | | | 8 MHz | 5.5 | 4.6 | |
| | | | 4 MHz | 3.3 | 2.8 | |
| | | | 2 MHz | 2.2 | 1.9 | |
| | | | 1 MHz | 1.6 | 1.45 | |
| | | | 500 kHz | 1.3 | 1.25 | |
| | | 125 kHz | 1.08 | 1.06 | | |
| | | Running on high speed internal RC (HSI), AHB prescaler used to reduce the frequency | 64 MHz | 31.4 | 23.9 | mA |
| | | | 48 MHz | 23.5 | 17.9 | |
| | | | 36 MHz | 18.3 | 14.1 | |
| | | | 24 MHz | 12.2 | 9.5 | |
| | | | 16 MHz | 8.5 | 6.8 | |
| | | | 8 MHz | 4.9 | 4 | |
| | | | 4 MHz | 2.7 | 2.2 | |
| | | | 2 MHz | 1.6 | 1.4 | |
| | | | 1 MHz | 1.02 | 0.9 | |
| 500 kHz | 0.73 | | 0.67 | | | |
| 125 kHz | 0.5 | 0.48 | | | | |

1. Typical values are measures at T_A = 25 °C, V_{DD} = 3.3 V.
2. Add an additional power consumption of 0.8 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).
3. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 18. Typical current consumption in Sleep mode, code running from Flash or RAM

| Symbol | Parameter | Conditions | f _{HCLK} | Typ ⁽¹⁾ | | Unit |
|-----------------|------------------------------|---|-------------------|--|--------------------------|------|
| | | | | All peripherals enabled ⁽²⁾ | All peripherals disabled | |
| I _{DD} | Supply current in Sleep mode | External clock ⁽³⁾ | 72 MHz | 14.4 | 5.5 | mA |
| | | | 48 MHz | 9.9 | 3.9 | |
| | | | 36 MHz | 7.6 | 3.1 | |
| | | | 24 MHz | 5.3 | 2.3 | |
| | | | 16 MHz | 3.8 | 1.8 | |
| | | | 8 MHz | 2.1 | 1.2 | |
| | | | 4 MHz | 1.6 | 1.1 | |
| | | | 2 MHz | 1.3 | 1 | |
| | | | 1 MHz | 1.11 | 0.98 | |
| | | | 500 kHz | 1.04 | 0.96 | |
| | | | 125 kHz | 0.98 | 0.95 | |
| | | Running on high speed internal RC (HSI), AHB prescaler used to reduce the frequency | 64 MHz | 12.3 | 4.4 | |
| | | | 48 MHz | 9.3 | 3.3 | |
| | | | 36 MHz | 7 | 2.5 | |
| | | | 24 MHz | 4.8 | 1.8 | |
| | | | 16 MHz | 3.2 | 1.2 | |
| | | | 8 MHz | 1.6 | 0.6 | |
| | | | 4 MHz | 1 | 0.5 | |
| | | | 2 MHz | 0.72 | 0.47 | |
| | | | 1 MHz | 0.56 | 0.44 | |
| | | | 500 kHz | 0.49 | 0.42 | |
| | | | 125 kHz | 0.43 | 0.41 | |

1. Typical values are measures at T_A = 25 °C, V_{DD} = 3.3 V.
2. Add an additional power consumption of 0.8 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is on (ADON bit is set in the ADC_CR2 register).
3. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in [Table 19](#). The MCU is placed under the following conditions:

- all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked off
 - with only one peripheral clocked on
- ambient operating temperature and V_{DD} supply voltage conditions summarized in [Table 6](#)

Table 19. Peripheral current consumption⁽¹⁾

| Peripheral | | Typical consumption at 25 °C | Unit |
|------------|---------------------|------------------------------|------|
| APB1 | TIM2 | 1.2 | mA |
| | TIM3 | 1.2 | |
| | TIM4 | 0.9 | |
| | SPI2 | 0.2 | |
| | USART2 | 0.35 | |
| | USART3 | 0.35 | |
| | I2C1 | 0.39 | |
| | I2C2 | 0.39 | |
| | USB | 0.65 | |
| | CAN | 0.72 | |
| APB2 | GPIO A | 0.47 | mA |
| | GPIO B | 0.47 | |
| | GPIO C | 0.47 | |
| | GPIO D | 0.47 | |
| | GPIO E | 0.47 | |
| | ADC1 ⁽²⁾ | 1.81 | |
| | ADC2 | 1.78 | |
| | TIM1 | 1.6 | |
| | SPI1 | 0.43 | |
| | USART1 | 0.85 | |

1. $f_{HCLK} = 72$ MHz, $f_{APB1} = f_{HCLK}/2$, $f_{APB2} = f_{HCLK}$, default prescaler value for each peripheral.
 2. Specific conditions for ADC: $f_{HCLK} = 56$ MHz, $f_{APB1} = f_{HCLK}/2$, $f_{APB2} = f_{HCLK}$, $f_{ADCCLK} = f_{APB2}/4$, ADON bit in the ADC_CR2 register is set to 1.

5.3.6 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in [Table 20](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 9](#).

Table 20. High-speed external user clock characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------------------|---|----------------------------------|-------------|-----|-------------|---------|
| f_{HSE_ext} | User external clock source frequency ⁽¹⁾ | | 1 | 8 | 25 | MHz |
| V_{HSEH} | OSC_IN input pin high level voltage | | $0.7V_{DD}$ | | V_{DD} | V |
| V_{HSEL} | OSC_IN input pin low level voltage | | V_{SS} | | $0.3V_{DD}$ | |
| $t_{w(HSE)}$ $t_{w(HSE)}$ | OSC_IN high or low time ⁽¹⁾ | | 5 | | | ns |
| $t_{r(HSE)}$ $t_{f(HSE)}$ | OSC_IN rise or fall time ⁽¹⁾ | | | | 20 | |
| $C_{in(HSE)}$ | OSC_IN input capacitance ⁽¹⁾ | | | 5 | | pF |
| $DuCy_{(HSE)}$ | Duty cycle | | 45 | | 55 | % |
| I_L | OSC_IN Input leakage current | $V_{SS} \leq V_{IN} \leq V_{DD}$ | | | ± 1 | μA |

1. Guaranteed by design, not tested in production.

Low-speed external user clock generated from an external source

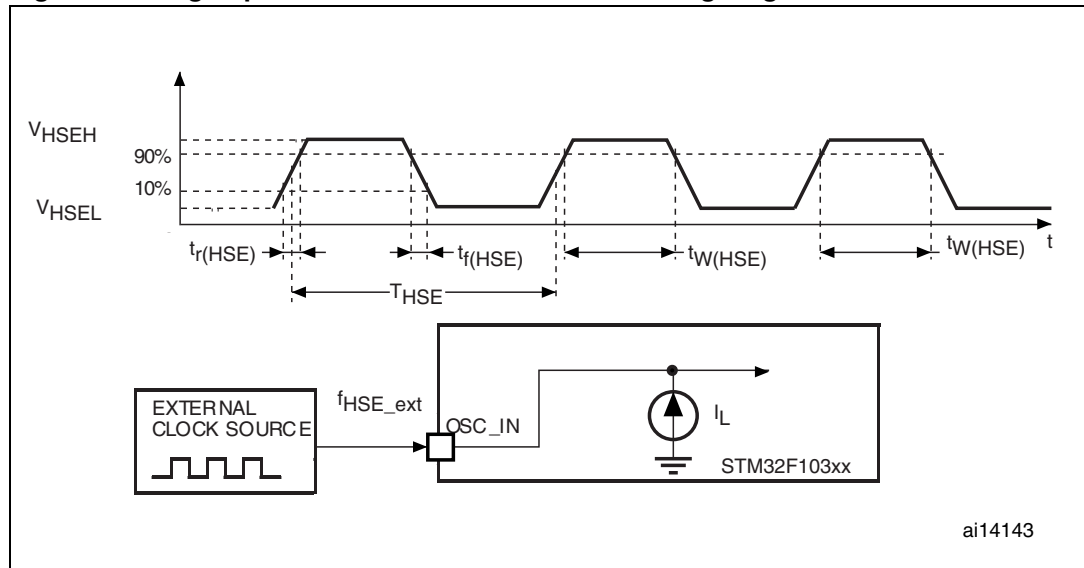
The characteristics given in [Table 21](#) result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 9](#).

Table 21. Low-speed external user clock characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------------------|---|----------------------------------|-------------|--------|-------------|---------|
| f_{LSE_ext} | User External clock source frequency ⁽¹⁾ | | | 32.768 | 1000 | kHz |
| V_{LSEH} | OSC32_IN input pin high level voltage | | $0.7V_{DD}$ | | V_{DD} | V |
| V_{LSEL} | OSC32_IN input pin low level voltage | | V_{SS} | | $0.3V_{DD}$ | |
| $t_{w(LSE)}$ $t_{w(LSE)}$ | OSC32_IN high or low time ⁽¹⁾ | | 450 | | | ns |
| $t_{r(LSE)}$ $t_{f(LSE)}$ | OSC32_IN rise or fall time ⁽¹⁾ | | | | 50 | |
| $C_{in(LSE)}$ | OSC32_IN input capacitance ⁽¹⁾ | | | 5 | | pF |
| $DuCy_{(LSE)}$ | Duty cycle | | 30 | | 70 | % |
| I_L | OSC32_IN Input leakage current | $V_{SS} \leq V_{IN} \leq V_{DD}$ | | | ± 1 | μA |

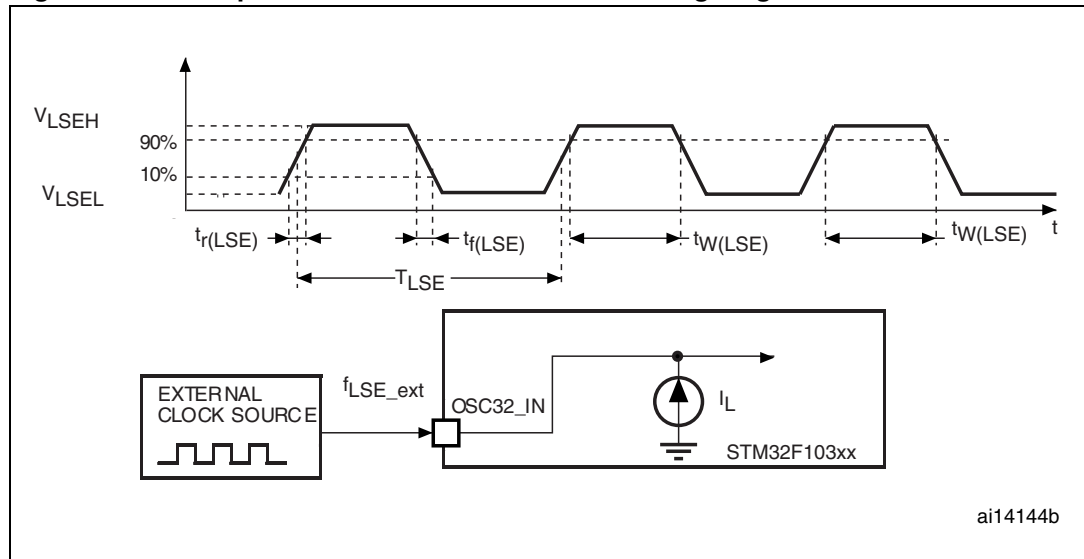
1. Guaranteed by design, not tested in production.

Figure 22. High-speed external clock source AC timing diagram



ai14143

Figure 23. Low-speed external clock source AC timing diagram



ai14144b

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 22](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

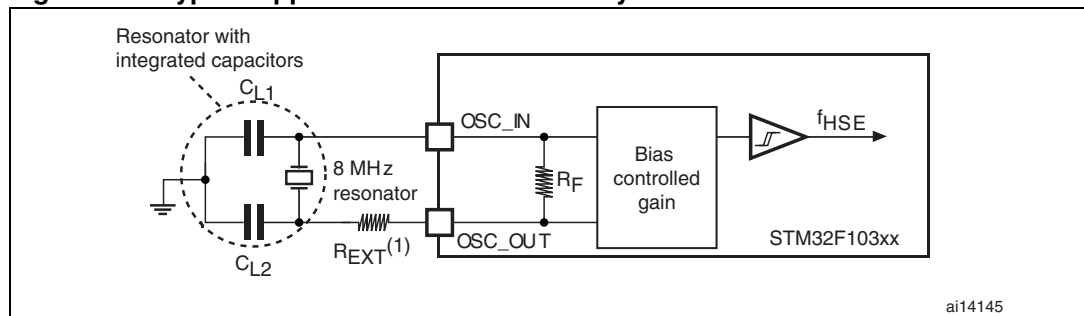
Table 22. HSE 4-16 MHz oscillator characteristics^{(1) (2)}

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------------------|--|---|-----|-----|-----|------------|
| f_{OSC_IN} | Oscillator frequency | | 4 | 8 | 16 | MHz |
| R_F | Feedback resistor | | | 200 | | k Ω |
| C | Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) ⁽³⁾ | $R_S = 30 \Omega$ | | 30 | | pF |
| i_2 | HSE driving current | $V_{DD} = 3.3 V, V_{IN} = V_{SS}$ with 30 pF load | | | 1 | mA |
| g_m | Oscillator transconductance | Startup | 25 | | | mA/V |
| $t_{SU(HSE)}$ ⁽⁴⁾ | startup time | V_{DD} is stabilized | | 2 | | ms |

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization, not tested in production.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see [Figure 24](#)). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} . Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 24. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 23](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 23. LSE oscillator characteristics ($f_{LSE} = 32.768$ kHz)^{(1) (2)}

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------------|---|---------------------------------------|----------------|-----|-----|------------|
| R_F | Feedback resistor | | | 5 | | M Ω |
| C | Recommended load capacitance versus equivalent serial resistance of the crystal (R_S) | $R_S = 30$ K Ω | | | 15 | pF |
| I_2 | LSE driving current | $V_{DD} = 3.3$ V $V_{IN} = V_{SS}$ | | | 1.4 | μ A |
| g_m | Oscillator transconductance | | 5 | | | μ A/V |
| $t_{SU(LSE)}^{(3)}$ | Startup time | V_{DD} is stabilized | $T_A = 50$ °C | 1.5 | | s |
| | | | $T_A = 25$ °C | 2.5 | | |
| | | | $T_A = 10$ °C | 4 | | |
| | | | $T_A = 0$ °C | 6 | | |
| | | | $T_A = -10$ °C | 10 | | |
| | | | $T_A = -20$ °C | 17 | | |
| | | | $T_A = -30$ °C | 32 | | |
| | | | $T_A = -40$ °C | 60 | | |

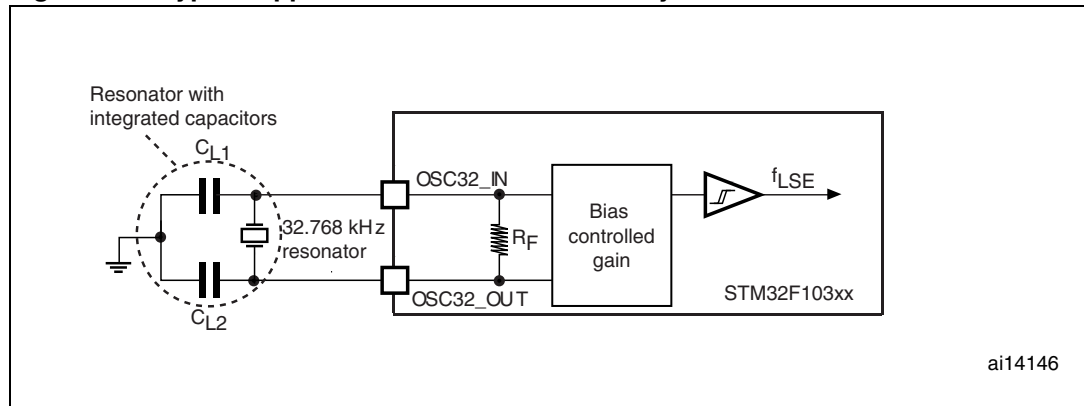
1. Based on characterization, not tested in production.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2} , are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} .
Load capacitance C_L has the following formula: $C_L = C_{L1} \times C_{L2} / (C_{L1} + C_{L2}) + C_{stray}$ where C_{stray} is the pin capacitance and board or trace PCB-related capacitance. Typically, it is between 2 pF and 7 pF.

Caution: To avoid exceeding the maximum value of C_{L1} and C_{L2} (15 pF) it is strongly recommended to use a resonator with a load capacitance $C_L \leq 7$ pF. Never use a resonator with a load capacitance of 12.5 pF.

Example: if you choose a resonator with a load capacitance of $C_L = 6$ pF, and $C_{stray} = 2$ pF, then $C_{L1} = C_{L2} = 8$ pF.

Figure 25. Typical application with a 32.768 kHz crystal



5.3.7 Internal clock source characteristics

The parameters given in [Table 24](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

High-speed internal (HSI) RC oscillator

Table 24. HSI oscillator characteristics⁽¹⁾

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|------------------------------|----------------------------------|--|-------------------------|------|------------------|------|---|
| f_{HSI} | Frequency | | | 8 | | MHz | |
| $DuCy_{(HSI)}$ | Duty cycle | | 45 | | 55 | % | |
| ACC_{HSI} | Accuracy of the HSI oscillator | User-trimmed with the RCC_CR register ⁽²⁾ | | | 1 ⁽³⁾ | % | |
| | | Factory-calibrated ⁽⁴⁾⁽⁵⁾ | $T_A = -40$ to 105 °C | -2 | | 2.5 | % |
| | | | $T_A = -10$ to 85 °C | -1.5 | | 2.2 | % |
| | | | $T_A = 0$ to 70 °C | -1.3 | | 2 | % |
| | $T_A = 25$ °C | -1.1 | | 1.8 | % | | |
| $t_{su(HSI)}$ ⁽⁴⁾ | HSI oscillator startup time | | 1 | | 2 | μs | |
| $I_{DD(HSI)}$ ⁽⁴⁾ | HSI oscillator power consumption | | | 80 | 100 | μA | |

- $V_{DD} = 3.3$ V, $T_A = -40$ to 105 °C unless otherwise specified.
- Refer to application note AN2868 “STM32F10xxx internal RC oscillator (HSI) calibration” available from the ST website www.st.com.
- Guaranteed by design, not tested in production.
- Based on characterization, not tested in production.
- The actual frequency of HSI oscillator may be impacted by a reflow, but does not drift out of the specified range.

Low-speed internal (LSI) RC oscillator

Table 25. LSI oscillator characteristics ⁽¹⁾

| Symbol | Parameter | Min | Typ | Max | Unit |
|---------------------|----------------------------------|-----|------|-----|---------|
| $f_{LSI}^{(2)}$ | Frequency | 30 | 40 | 60 | kHz |
| $t_{su(LSI)}^{(3)}$ | LSI oscillator startup time | | | 85 | μ s |
| $I_{DD(LSI)}^{(3)}$ | LSI oscillator power consumption | | 0.65 | 1.2 | μ A |

1. $V_{DD} = 3$ V, $T_A = -40$ to 105 °C unless otherwise specified.

2. Based on characterization, not tested in production.

3. Guaranteed by design, not tested in production.

Wakeup time from low-power mode

The wakeup times given in [Table 26](#) is measured on a wakeup phase with a 8-MHz HSI RC oscillator. The clock source used to wake up the device depends from the current operating mode:

- Stop or Standby mode: the clock source is the RC oscillator
- Sleep mode: the clock source is the clock that was set before entering Sleep mode.

All timings are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 26. Low-power mode wakeup timings

| Symbol | Parameter | Typ | Unit |
|---------------------|---|-----|---------------|
| $t_{WUSLEEP}^{(1)}$ | Wakeup from Sleep mode | 1.8 | μs |
| $t_{WUSTOP}^{(1)}$ | Wakeup from Stop mode (regulator in run mode) | 3.6 | μs |
| | Wakeup from Stop mode (regulator in low power mode) | 5.4 | |
| $t_{WUSTDBY}^{(1)}$ | Wakeup from Standby mode | 50 | μs |

1. The wakeup times are measured from the wakeup event to the point in which the user application code reads the first instruction.

5.3.8 PLL characteristics

The parameters given in [Table 27](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 27. PLL characteristics

| Symbol | Parameter | Value | | | Unit |
|----------------|--------------------------------|--------------------|-----|--------------------|---------------|
| | | Min ⁽¹⁾ | Typ | Max ⁽¹⁾ | |
| f_{PLL_IN} | PLL input clock ⁽²⁾ | 1 | 8.0 | 25 | MHz |
| | PLL input clock duty cycle | 40 | | 60 | % |
| f_{PLL_OUT} | PLL multiplier output clock | 16 | | 72 | MHz |
| t_{LOCK} | PLL lock time | | | 200 | μs |
| Jitter | Cycle-to-cycle jitter | | | 300 | ps |

1. Based on characterization, not tested in production.
2. Take care of using the appropriate multiplier factors so as to have PLL input clock values compatible with the range defined by f_{PLL_OUT} .

5.3.9 Memory characteristics

Flash memory

The characteristics are given at $T_A = -40$ to 105 °C unless otherwise specified.

Table 28. Flash memory characteristics

| Symbol | Parameter | Conditions | Min ⁽¹⁾ | Typ | Max ⁽¹⁾ | Unit |
|-------------|-------------------------|--------------------------|--------------------|------|--------------------|---------------|
| t_{prog} | 16-bit programming time | $T_A = -40$ to $+105$ °C | 40 | 52.5 | 70 | μs |
| t_{ERASE} | Page (1 KB) erase time | $T_A = -40$ to $+105$ °C | 20 | | 40 | ms |
| t_{ME} | Mass erase time | $T_A = -40$ to $+105$ °C | 20 | | 40 | ms |

Table 28. Flash memory characteristics (continued)

| Symbol | Parameter | Conditions | Min ⁽¹⁾ | Typ | Max ⁽¹⁾ | Unit |
|-------------------|---------------------|---|--------------------|-----|--------------------|------|
| I _{DD} | Supply current | Read mode f _{HCLK} = 72 MHz with 2 wait states, V _{DD} = 3.3 V | | | 20 | mA |
| | | Write / Erase modes f _{HCLK} = 72 MHz, V _{DD} = 3.3 V | | | 5 | mA |
| | | Power-down mode / Halt, V _{DD} = 3.0 to 3.6 V | | | 50 | μA |
| V _{prog} | Programming voltage | | 2 | | 3.6 | V |

1. Guaranteed by design, not tested in production.

Table 29. Flash memory endurance and data retention

| Symbol | Parameter | Conditions | Value | | | Unit |
|------------------|----------------|---|--------------------|-----|-----|---------|
| | | | Min ⁽¹⁾ | Typ | Max | |
| N _{END} | Endurance | T _A = -40 to +85 °C (6 suffix versions) T _A = -40 to +105 °C (7 suffix versions) | 10 | | | kcycles |
| t _{RET} | Data retention | 1 kcycle ⁽²⁾ at T _A = 85 °C | 30 | | | Years |
| | | 1 kcycle ⁽²⁾ at T _A = 105 °C | 10 | | | |
| | | 10 kcycles ⁽²⁾ at T _A = 55 °C | 20 | | | |

1. Based on characterization, not tested in production.

2. Cycling performed over the whole temperature range.

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB:** A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 30](#). They are based on the EMS levels and classes defined in application note AN1709.

Table 30. EMS characteristics

| Symbol | Parameter | Conditions | Level/Class |
|-------------------|---|---|-------------|
| V _{FESD} | Voltage limits to be applied on any I/O pin to induce a functional disturbance | V _{DD} = 3.3 V, T _A = +25 °C, f _{HCLK} = 72 MHz conforms to IEC 61000-4-2 | 2B |
| V _{EFTB} | Fast transient voltage burst limits to be applied through 100 pF on V _{DD} and V _{SS} pins to induce a functional disturbance | V _{DD} = 3.3 V, T _A = +25 °C, f _{HCLK} = 72 MHz conforms to IEC 61000-4-4 | 4A |

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 31. EMI characteristics

| Symbol | Parameter | Conditions | Monitored frequency band | Max vs. [f _{HSE} /f _{HCLK}] | | Unit |
|------------------|------------|---|--------------------------|--|----------|------|
| | | | | 8/48 MHz | 8/72 MHz | |
| S _{EMI} | Peak level | V _{DD} = 3.3 V, T _A = 25 °C, LQFP100 package compliant with IEC 61967-2 | 0.1 to 30 MHz | 12 | 12 | dBμV |
| | | | 30 to 130 MHz | 22 | 19 | |
| | | | 130 MHz to 1GHz | 23 | 29 | |
| | | | SAE EMI Level | 4 | 4 | - |

5.3.11 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 32. ESD absolute maximum ratings

| Symbol | Ratings | Conditions | Class | Maximum value ⁽¹⁾ | Unit |
|-----------------------|---|---|-------|------------------------------|------|
| V _{ESD(HBM)} | Electrostatic discharge voltage (human body model) | T _A = +25 °C conforming to JESD22-A114 | 2 | 2000 | V |
| V _{ESD(CDM)} | Electrostatic discharge voltage (charge device model) | T _A = +25 °C conforming to JESD22-C101 | II | 500 | |

1. Based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 33. Electrical sensitivities

| Symbol | Parameter | Conditions | Class |
|--------|-----------------------|--|------------|
| LU | Static latch-up class | T _A = +105 °C conforming to JESD78A | II level A |

5.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in [Table 34](#)

Table 34. I/O current injection susceptibility

| Symbol | Description | Functional susceptibility | | Unit |
|-----------|---|---------------------------|--------------------|------|
| | | Negative injection | Positive injection | |
| I_{INJ} | Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13 | -0 | +0 | mA |
| | Injected current on all FT pins | -5 | +0 | |
| | Injected current on any other pin | -5 | +5 | |

5.3.13 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in [Table 35](#) are derived from tests performed under the conditions summarized in [Table 9](#). All I/Os are CMOS and TTL compliant.

Table 35. I/O static characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---|--|--|-----|--|------|
| V _{IL} | Low level input voltage | Standard IO input low level voltage | - | - | 0.28*(V _{DD} -2 V)+0.8 V ⁽¹⁾ | V |
| | | IO FT ⁽³⁾ input low level voltage | - | - | 0.32*(V _{DD} -2V)+0.75 V ⁽¹⁾ | |
| | | All I/Os except BOOT0 | - | - | 0.35V _{DD} ⁽²⁾ | |
| V _{IH} | High level input voltage | Standard IO input high level voltage | 0.41*(V _{DD} -2 V)+1.3 V ⁽¹⁾ | - | - | V |
| | | IO FT ⁽³⁾ input high level voltage | 0.42*(V _{DD} -2 V)+1 V ⁽¹⁾ | - | - | |
| | | All I/Os except BOOT0 | 0.65V _{DD} ⁽²⁾ | - | - | |
| V _{hys} | Standard IO Schmitt trigger voltage hysteresis ⁽⁴⁾ | | 200 | - | - | mV |
| | IO FT Schmitt trigger voltage hysteresis ⁽⁴⁾ | | 5% V _{DD} ⁽⁵⁾ | - | - | |
| I _{lkg} | Input leakage current ⁽⁶⁾ | V _{SS} ≤ V _{IN} ≤ V _{DD} Standard I/Os | - | - | ±1 | μA |
| | | V _{IN} = 5 V I/O FT | - | - | 3 | |
| R _{PU} | Weak pull-up equivalent resistor ⁽⁷⁾ | V _{IN} = V _{SS} | 30 | 40 | 50 | kΩ |
| R _{PD} | Weak pull-down equivalent resistor ⁽⁷⁾ | V _{IN} = V _{DD} | 30 | 40 | 50 | |
| C _{IO} | I/O pin capacitance | | - | 5 | - | pF |

1. Data based on design simulation.

2. Tested in production.

3. FT = Five-volt tolerant. In order to sustain a voltage higher than V_{DD}+0.3 the internal pull-up/pull-down resistors must be disabled.

4. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization, not tested in production.

5. With a minimum of 100 mV.

6. Leakage could be higher than max. if negative current is injected on adjacent pins.

7. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimum (~10% order).

All I/Os are CMOS and TTL compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in [Figure 26](#) and [Figure 27](#) for standard I/Os, and in [Figure 28](#) and [Figure 29](#) for 5 V tolerant I/Os.

Figure 26. Standard I/O input characteristics - CMOS port

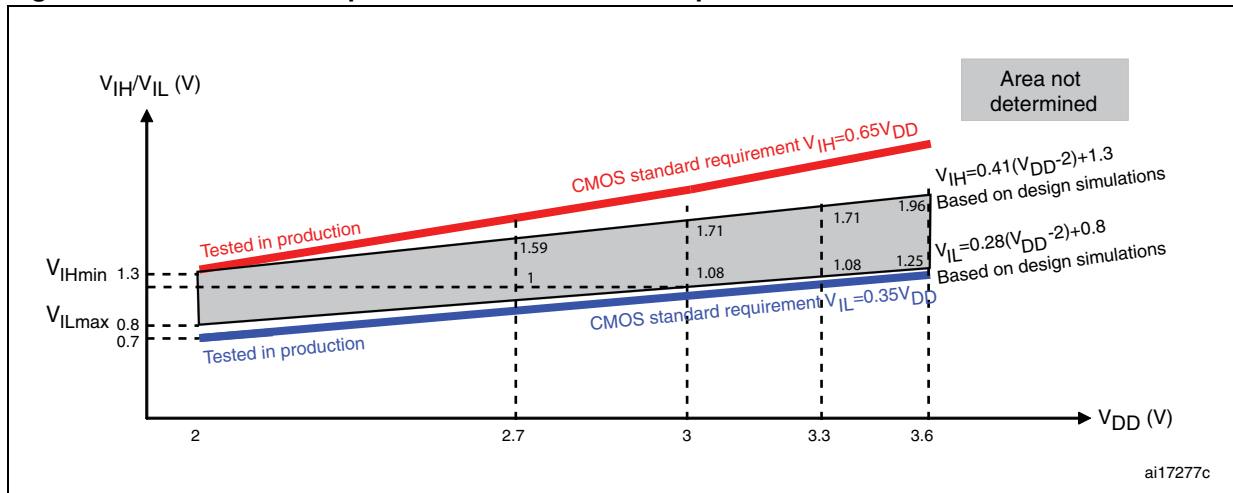


Figure 27. Standard I/O input characteristics - TTL port

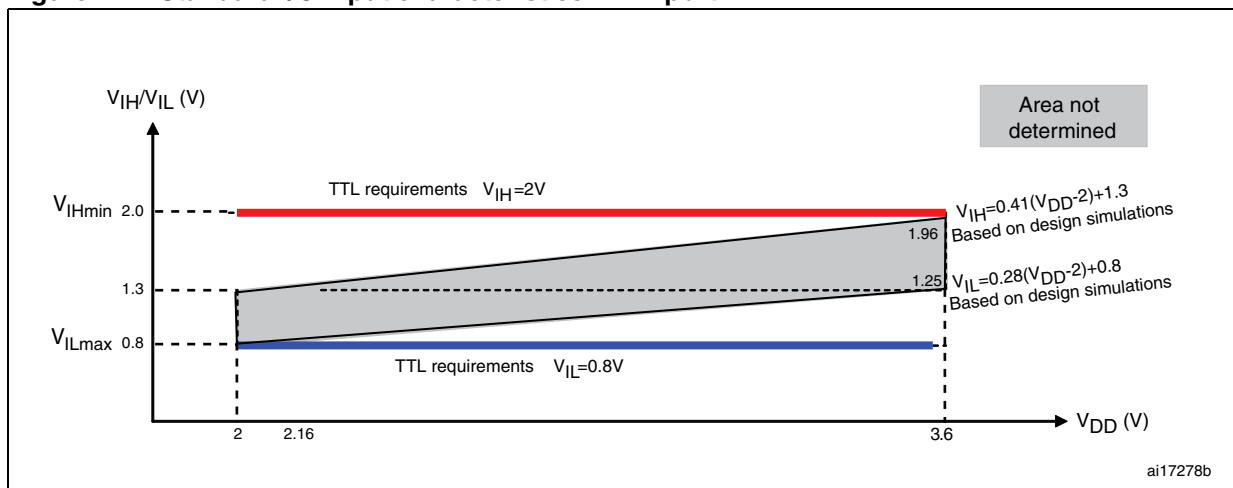


Figure 28. 5 V tolerant I/O input characteristics - CMOS port

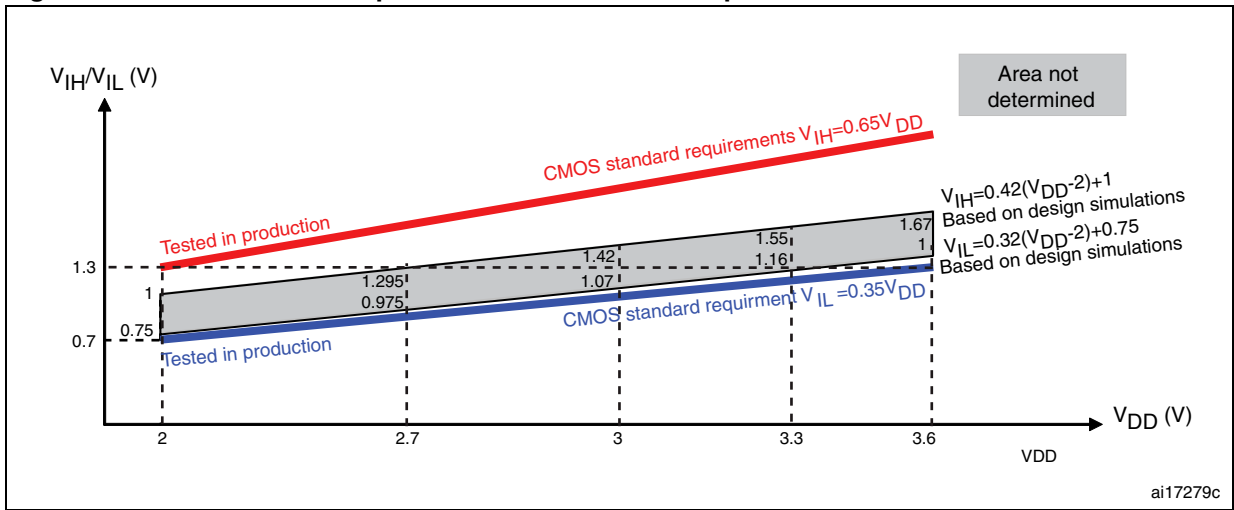
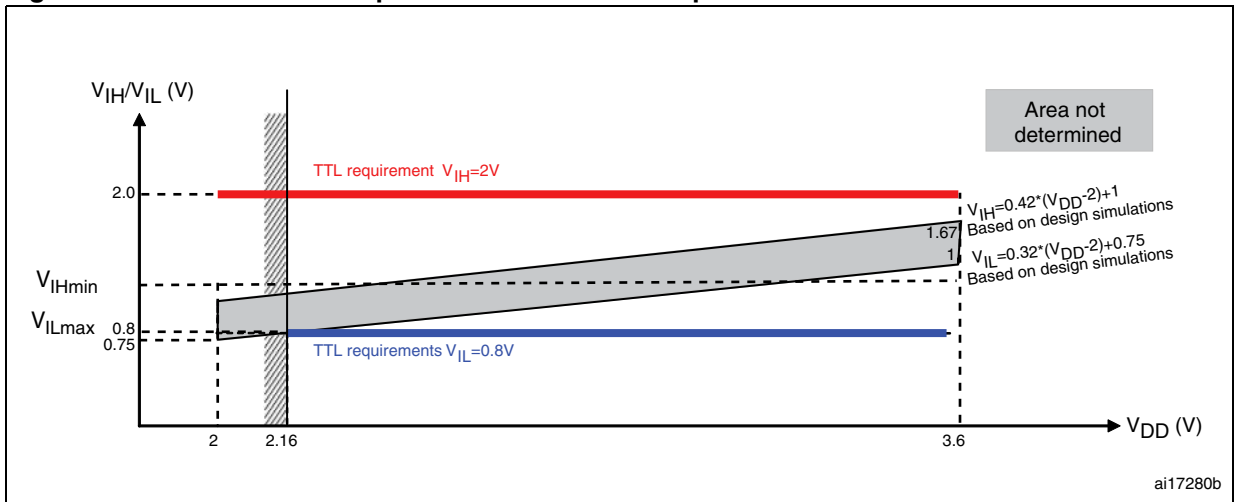


Figure 29. 5 V tolerant I/O input characteristics - TTL port



Output driving current

The GPIOs (general-purpose inputs/outputs) can sink or source up to ± 8 mA, and sink or source up to ± 20 mA (with a relaxed V_{OL}/V_{OH}) except PC13, PC14 and PC15 which can sink or source up to ± 3 mA. When using the GPIOs PC13 to PC15 in output mode, the speed should not exceed 2 MHz with a maximum load of 30 pF.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 5.2](#):

- The sum of the currents sourced by all the I/Os on V_{DD} , plus the maximum Run consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating I_{VDD} (see [Table 7](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating I_{VSS} (see [Table 7](#)).

Output voltage levels

Unless otherwise specified, the parameters given in [Table 36](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#). All I/Os are CMOS and TTL compliant.

Table 36. Output voltage characteristics

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|---|--|--------------|-----|------|
| $V_{OL}^{(1)}$ | Output low level voltage for an I/O pin when 8 pins are sunk at same time | CMOS port ⁽²⁾ , $I_{IO} = +8$ mA 2.7 V < V_{DD} < 3.6 V | | 0.4 | V |
| $V_{OH}^{(3)}$ | Output high level voltage for an I/O pin when 8 pins are sourced at same time | | $V_{DD}-0.4$ | | |
| $V_{OL}^{(1)}$ | Output low level voltage for an I/O pin when 8 pins are sunk at same time | TTL port ⁽²⁾ $I_{IO} = +8$ mA 2.7 V < V_{DD} < 3.6 V | | 0.4 | V |
| $V_{OH}^{(3)}$ | Output high level voltage for an I/O pin when 8 pins are sourced at same time | | 2.4 | | |
| $V_{OL}^{(1)(4)}$ | Output low level voltage for an I/O pin when 8 pins are sunk at same time | $I_{IO} = +20$ mA 2.7 V < V_{DD} < 3.6 V | | 1.3 | V |
| $V_{OH}^{(3)(4)}$ | Output high level voltage for an I/O pin when 8 pins are sourced at same time | | $V_{DD}-1.3$ | | |
| $V_{OL}^{(1)(4)}$ | Output low level voltage for an I/O pin when 8 pins are sunk at same time | $I_{IO} = +6$ mA 2 V < V_{DD} < 2.7 V | | 0.4 | V |
| $V_{OH}^{(3)(4)}$ | Output high level voltage for an I/O pin when 8 pins are sourced at same time | | $V_{DD}-0.4$ | | |

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in [Table 7](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in [Table 7](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} .
4. Based on characterization data, not tested in production.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 30](#) and [Table 37](#), respectively.

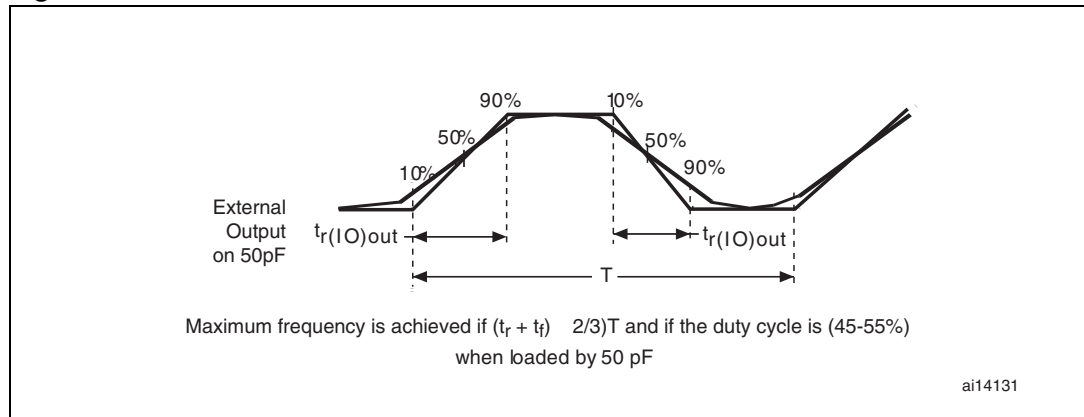
Unless otherwise specified, the parameters given in [Table 37](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 37. I/O AC characteristics⁽¹⁾

| MODEx[1:0] bit value ⁽¹⁾ | Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------------------------|-------------------------|---|--|-----|--------------------|------|
| 10 | f _{max(IO)out} | Maximum frequency ⁽²⁾ | C _L = 50 pF, V _{DD} = 2 V to 3.6 V | | 2 | MHz |
| | t _{f(IO)out} | Output high to low level fall time | C _L = 50 pF, V _{DD} = 2 V to 3.6 V | | 125 ⁽³⁾ | ns |
| | t _{r(IO)out} | Output low to high level rise time | | | 125 ⁽³⁾ | |
| 01 | f _{max(IO)out} | Maximum frequency ⁽²⁾ | C _L = 50 pF, V _{DD} = 2 V to 3.6 V | | 10 | MHz |
| | t _{f(IO)out} | Output high to low level fall time | C _L = 50 pF, V _{DD} = 2 V to 3.6 V | | 25 ⁽³⁾ | ns |
| | t _{r(IO)out} | Output low to high level rise time | | | 25 ⁽³⁾ | |
| 11 | F _{max(IO)out} | Maximum frequency ⁽²⁾ | C _L = 30 pF, V _{DD} = 2.7 V to 3.6 V | | 50 | MHz |
| | | | C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V | | 30 | MHz |
| | | | C _L = 50 pF, V _{DD} = 2 V to 2.7 V | | 20 | MHz |
| | t _{f(IO)out} | Output high to low level fall time | C _L = 30 pF, V _{DD} = 2.7 V to 3.6 V | | 5 ⁽³⁾ | ns |
| | | | C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V | | 8 ⁽³⁾ | |
| | | | C _L = 50 pF, V _{DD} = 2 V to 2.7 V | | 12 ⁽³⁾ | |
| | t _{r(IO)out} | Output low to high level rise time | C _L = 30 pF, V _{DD} = 2.7 V to 3.6 V | | 5 ⁽³⁾ | |
| | | | C _L = 50 pF, V _{DD} = 2.7 V to 3.6 V | | 8 ⁽³⁾ | |
| | | | C _L = 50 pF, V _{DD} = 2 V to 2.7 V | | 12 ⁽³⁾ | |
| - | t _{EXTIpw} | Pulse width of external signals detected by the EXTI controller | | 10 | | ns |

1. The I/O speed is configured using the MODEx[1:0] bits. Refer to the STM32F10xxx reference manual for a description of GPIO Port configuration register.
2. The maximum frequency is defined in [Figure 30](#).
3. Guaranteed by design, not tested in production.

Figure 30. I/O AC characteristics definition



5.3.14 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor, R_{PU} (see [Table 35](#)).

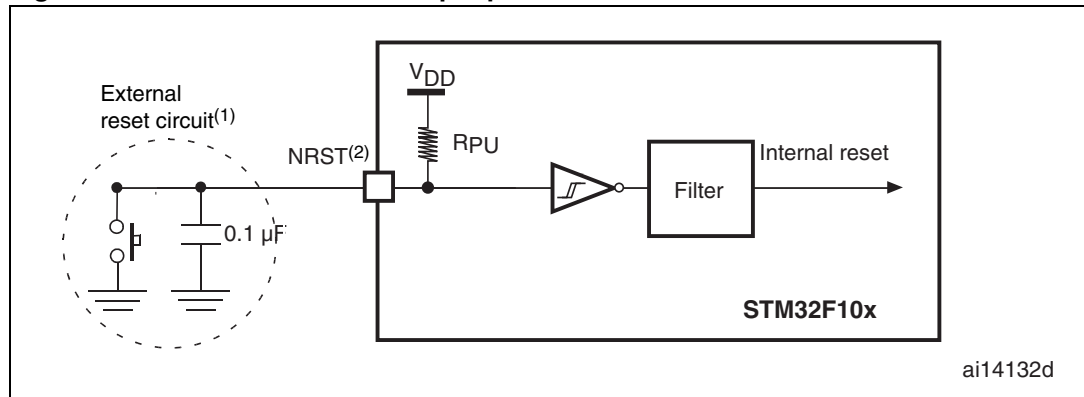
Unless otherwise specified, the parameters given in [Table 38](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 38. NRST pin characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------------|---|-------------------|------|-----|--------------|------------|
| $V_{IL(NRST)}^{(1)}$ | NRST Input low level voltage | | -0.5 | | 0.8 | V |
| $V_{IH(NRST)}^{(1)}$ | NRST Input high level voltage | | 2 | | $V_{DD}+0.5$ | |
| $V_{hys(NRST)}$ | NRST Schmitt trigger voltage hysteresis | | | 200 | | mV |
| R_{PU} | Weak pull-up equivalent resistor ⁽²⁾ | $V_{IN} = V_{SS}$ | 30 | 40 | 50 | k Ω |
| $V_{F(NRST)}^{(1)}$ | NRST Input filtered pulse | | | | 100 | ns |
| $V_{NF(NRST)}^{(1)}$ | NRST Input not filtered pulse | | 300 | | | ns |

1. Guaranteed by design, not tested in production.
2. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance must be minimum (~10% order).

Figure 31. Recommended NRST pin protection



2. The reset network protects the device against parasitic resets.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 38](#). Otherwise the reset will not be taken into account by the device.

5.3.15 TIM timer characteristics

The parameters given in [Table 39](#) are guaranteed by design.

Refer to [Section 5.3.12: I/O current injection characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 39. TIMx⁽¹⁾ characteristics

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---|--------------------------------|--------|----------------------|---------------|
| $t_{res(TIM)}$ | Timer resolution time | | 1 | | $t_{TIMxCLK}$ |
| | | $f_{TIMxCLK} = 72 \text{ MHz}$ | 13.9 | | ns |
| f_{EXT} | Timer external clock frequency on CH1 to CH4 | | 0 | $f_{TIMxCLK}/2$ | MHz |
| | | $f_{TIMxCLK} = 72 \text{ MHz}$ | 0 | 36 | MHz |
| Res_{TIM} | Timer resolution | | | 16 | bit |
| $t_{COUNTER}$ | 16-bit counter clock period when internal clock is selected | | 1 | 65536 | $t_{TIMxCLK}$ |
| | | $f_{TIMxCLK} = 72 \text{ MHz}$ | 0.0139 | 910 | μs |
| t_{MAX_COUNT} | Maximum possible count | | | 65536×65536 | $t_{TIMxCLK}$ |
| | | $f_{TIMxCLK} = 72 \text{ MHz}$ | | 59.6 | s |

1. TIMx is used as a general term to refer to the TIM1, TIM2, TIM3 and TIM4 timers.

5.3.16 Communications interfaces

I²C interface characteristics

The STM32F103xx performance line I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

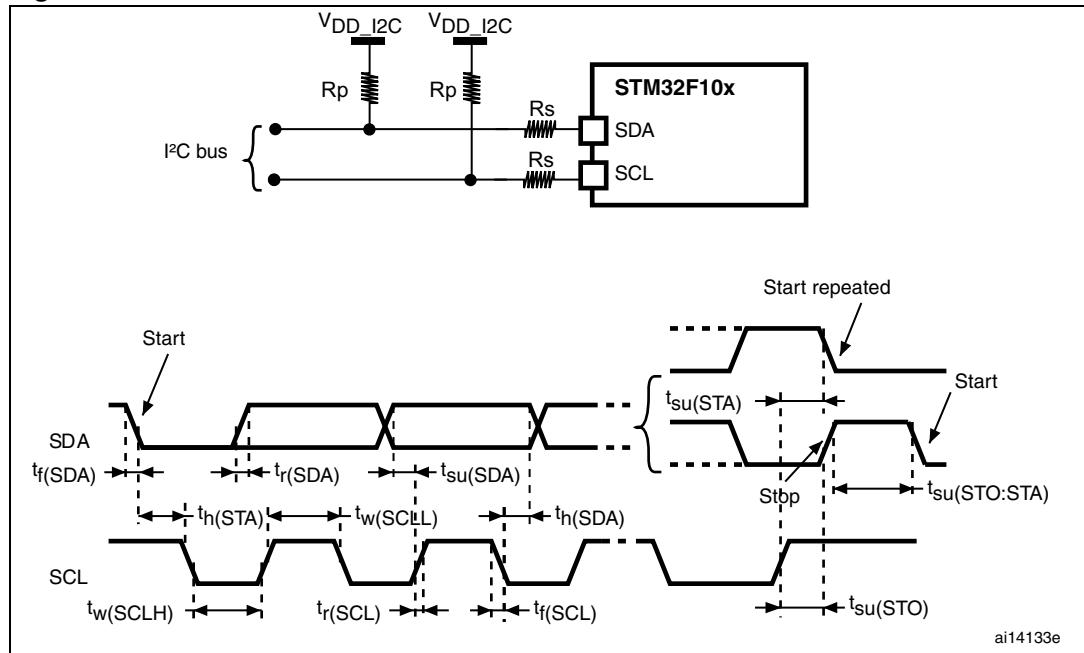
The I²C characteristics are described in [Table 40](#). Refer also to [Section 5.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (SDA and SCL).

Table 40. I²C characteristics

| Symbol | Parameter | Standard mode I ² C ⁽¹⁾ | | Fast mode I ² C ⁽¹⁾⁽²⁾ | | Unit |
|--|---|---|------|--|--------------------|------|
| | | Min | Max | Min | Max | |
| t _{w(SCLL)} | SCL clock low time | 4.7 | | 1.3 | | μs |
| t _{w(SCLH)} | SCL clock high time | 4.0 | | 0.6 | | |
| t _{su(SDA)} | SDA setup time | 250 | | 100 | | ns |
| t _{h(SDA)} | SDA data hold time | 0 | | 0 | 900 ⁽³⁾ | |
| t _{r(SDA)} t _{r(SCL)} | SDA and SCL rise time | | 1000 | 20 + 0.1C _b | 300 | |
| t _{f(SDA)} t _{f(SCL)} | SDA and SCL fall time | | 300 | | 300 | |
| t _{h(STA)} | Start condition hold time | 4.0 | | 0.6 | | μs |
| t _{su(STA)} | Repeated Start condition setup time | 4.7 | | 0.6 | | |
| t _{su(STO)} | Stop condition setup time | 4.0 | | 0.6 | | μs |
| t _{w(STO:STA)} | Stop to Start condition time (bus free) | 4.7 | | 1.3 | | μs |
| C _b | Capacitive load for each bus line | | 400 | | 400 | pF |

1. Guaranteed by design, not tested in production.
2. f_{CLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I²C fast mode clock.
3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

Figure 32. I²C bus AC waveforms and measurement circuit



1. Measurement points are done at CMOS levels: 0.3V_{DD} and 0.7V_{DD}.
2. Rs = Series protection resistors, Rp = Pull-up resistors, V_{DD_I2C} = I2C bus supply.

Table 41. SCL frequency (f_{PCLK1} = 36 MHz, V_{DD_I2C} = 3.3 V)⁽¹⁾⁽²⁾

| f _{SCL} (kHz) | I2C_CCR value |
|------------------------|-------------------------|
| | R _P = 4.7 kΩ |
| 400 | 0x801E |
| 300 | 0x8028 |
| 200 | 0x803C |
| 100 | 0x00B4 |
| 50 | 0x0168 |
| 20 | 0x0384 |

1. R_P = External pull-up resistance, f_{SCL} = I²C speed,
2. For speeds around 200 kHz, the tolerance on the achieved speed is of ±5%. For other speed ranges, the tolerance on the achieved speed is ±2%. These variations depend on the accuracy of the external components used to design the application.

SPI interface characteristics

Unless otherwise specified, the parameters given in [Table 42](#) are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 9](#).

Refer to [Section 5.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 42. SPI characteristics

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--|----------------------------------|--|-------------|-------------|------|
| f_{SCK} $1/t_c(SCK)$ | SPI clock frequency | Master mode | | 18 | MHz |
| | | Slave mode | | 18 | |
| $t_{r(SCK)}$ $t_{f(SCK)}$ | SPI clock rise and fall time | Capacitive load: C = 30 pF | | 8 | ns |
| DuCy(SCK) | SPI slave input clock duty cycle | Slave mode | 30 | 70 | % |
| $t_{su(NSS)}^{(1)}$ | NSS setup time | Slave mode | $4t_{PCLK}$ | | ns |
| $t_{h(NSS)}^{(1)}$ | NSS hold time | Slave mode | $2t_{PCLK}$ | | |
| $t_{w(SCKH)}^{(1)}$ $t_{w(SCKL)}^{(1)}$ | SCK high and low time | Master mode, $f_{PCLK} = 36$ MHz, presc = 4 | 50 | 60 | |
| $t_{su(MI)}^{(1)}$ $t_{su(SI)}^{(1)}$ | Data input setup time | Master mode | 5 | | |
| | | Slave mode | 5 | | |
| $t_{h(MI)}^{(1)}$ $t_{h(SI)}^{(1)}$ | Data input hold time | Master mode | 5 | | |
| | | Slave mode | 4 | | |
| $t_{a(SO)}^{(1)(2)}$ | Data output access time | Slave mode, $f_{PCLK} = 20$ MHz | 0 | $3t_{PCLK}$ | |
| $t_{dis(SO)}^{(1)(3)}$ | Data output disable time | Slave mode | 2 | 10 | |
| $t_{v(SO)}^{(1)}$ | Data output valid time | Slave mode (after enable edge) | | 25 | |
| $t_{v(MO)}^{(1)}$ | Data output valid time | Master mode (after enable edge) | | 5 | |
| $t_{h(SO)}^{(1)}$ $t_{h(MO)}^{(1)}$ | Data output hold time | Slave mode (after enable edge) | 15 | | |
| | | Master mode (after enable edge) | 2 | | |

1. Based on characterization, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 33. SPI timing diagram - slave mode and CPHA = 0

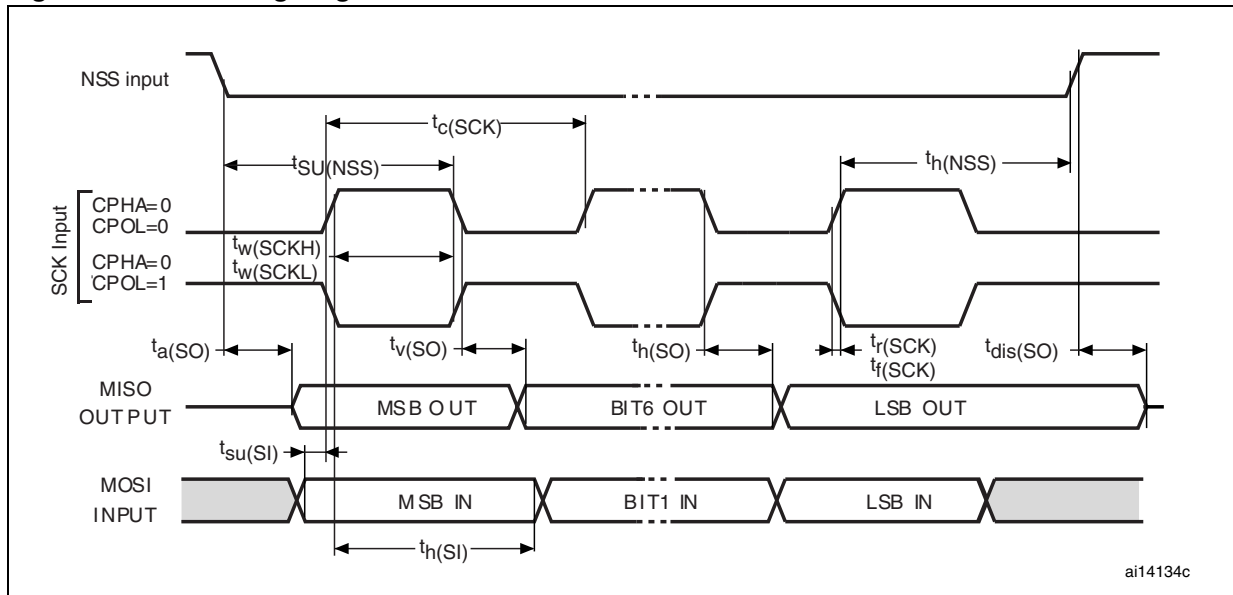
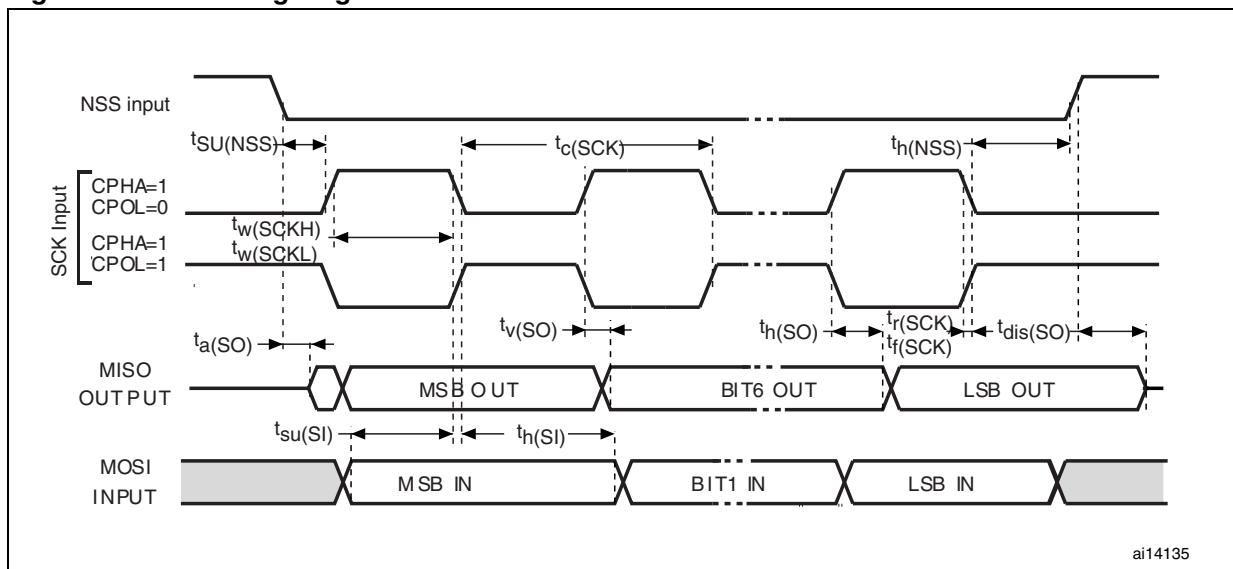
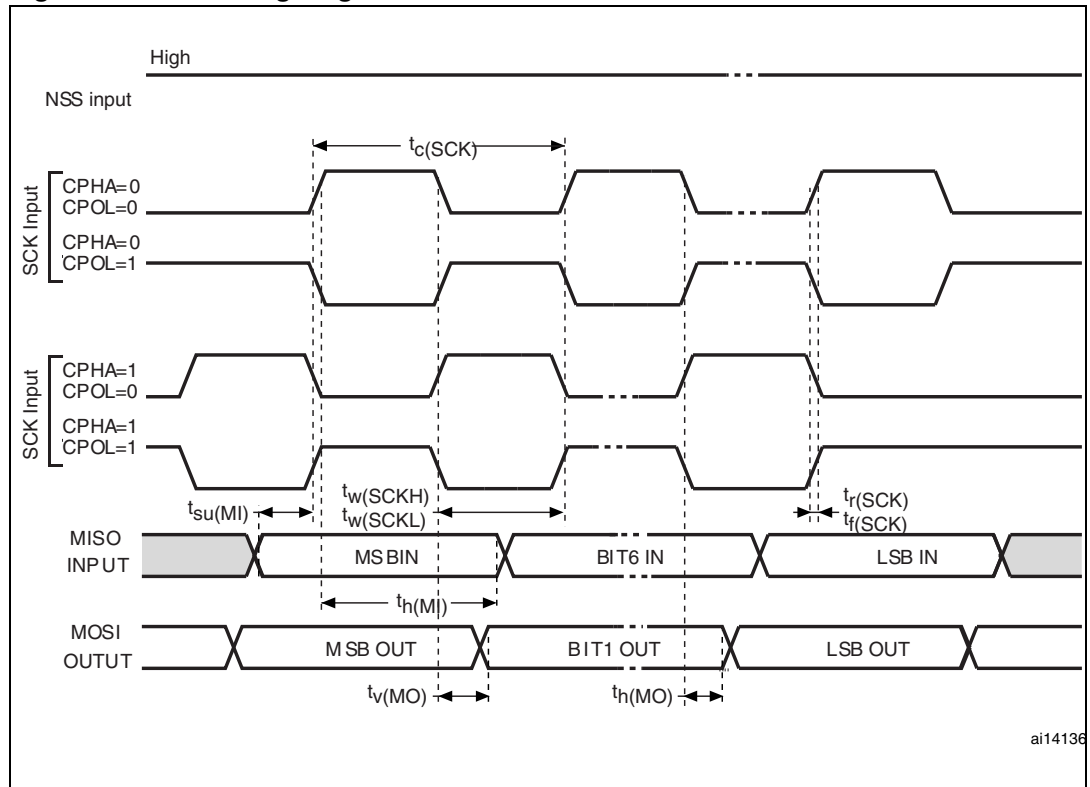


Figure 34. SPI timing diagram - slave mode and CPHA = 1⁽¹⁾



1. Measurement points are done at CMOS levels: 0.3V_{DD} and 0.7V_{DD}.

Figure 35. SPI timing diagram - master mode⁽¹⁾



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

USB characteristics

The USB interface is USB-IF certified (Full Speed).

Table 43. USB startup time

| Symbol | Parameter | Max | Unit |
|---------------------|------------------------------|-----|---------|
| $t_{STARTUP}^{(1)}$ | USB transceiver startup time | 1 | μs |

1. Guaranteed by design, not tested in production.

Table 44. USB DC electrical characteristics

| Symbol | Parameter | Conditions | Min. ⁽¹⁾ | Max. ⁽¹⁾ | Unit |
|--------------------------------|--------------------------------------|---|---------------------|---------------------|------|
| Input levels | | | | | |
| V _{DD} | USB operating voltage ⁽²⁾ | | 3.0 ⁽³⁾ | 3.6 | V |
| V _{DI} ⁽⁴⁾ | Differential input sensitivity | I(USBDP, USBDM) | 0.2 | | V |
| V _{CM} ⁽⁴⁾ | Differential common mode range | Includes V _{DI} range | 0.8 | 2.5 | |
| V _{SE} ⁽⁴⁾ | Single ended receiver threshold | | 1.3 | 2.0 | |
| Output levels | | | | | |
| V _{OL} | Static output level low | R _L of 1.5 kΩ to 3.6 V ⁽⁵⁾ | | 0.3 | V |
| V _{OH} | Static output level high | R _L of 15 kΩ to V _{SS} ⁽⁵⁾ | 2.8 | 3.6 | |

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USBDP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F103xx USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by design, not tested in production.
5. R_L is the load connected on the USB drivers

Figure 36. USB timings: definition of data signal rise and fall time

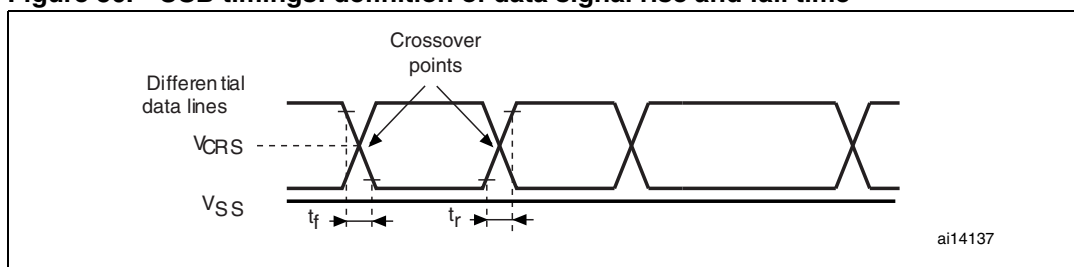


Table 45. USB: Full-speed electrical characteristics⁽¹⁾

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------------------|---------------------------------|--------------------------------|-----|-----|------|
| Driver characteristics | | | | | |
| t _r | Rise time ⁽²⁾ | C _L = 50 pF | 4 | 20 | ns |
| t _f | Fall time ⁽²⁾ | C _L = 50 pF | 4 | 20 | ns |
| t _{rfm} | Rise/ fall time matching | t _r /t _f | 90 | 110 | % |
| V _{CRS} | Output signal crossover voltage | | 1.3 | 2.0 | V |

1. Guaranteed by design, not tested in production.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

5.3.17 CAN (controller area network) interface

Refer to [Section 5.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

5.3.18 12-bit ADC characteristics

Unless otherwise specified, the parameters given in [Table 46](#) are derived from tests performed under the ambient temperature, f_{PCLK2} frequency and V_{DDA} supply voltage conditions summarized in [Table 9](#).

Note: It is recommended to perform a calibration after each power-up.

Table 46. ADC characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------|---|---|--|--------------------|--------------------|-------------|
| V_{DDA} | Power supply | | 2.4 | | 3.6 | V |
| V_{REF+} | Positive reference voltage | | 2.4 | | V_{DDA} | V |
| I_{VREF} | Current on the V_{REF} input pin | | | 160 ⁽¹⁾ | 220 ⁽¹⁾ | μ A |
| f_{ADC} | ADC clock frequency | | 0.6 | | 14 | MHz |
| $f_S^{(2)}$ | Sampling rate | | 0.05 | | 1 | MHz |
| $f_{TRIG}^{(2)}$ | External trigger frequency | $f_{ADC} = 14$ MHz | | | 823 | kHz |
| | | | | | 17 | $1/f_{ADC}$ |
| $V_{AIN}^{(3)}$ | Conversion voltage range | | 0 (V_{SSA} or V_{REF-} tied to ground) | | V_{REF+} | V |
| $R_{AIN}^{(2)}$ | External input impedance | See Equation 1 and Table 47 for details | | | 50 | k Ω |
| $R_{ADC}^{(2)}$ | Sampling switch resistance | | | | 1 | k Ω |
| $C_{ADC}^{(2)}$ | Internal sample and hold capacitor | | | | 8 | pF |
| $t_{CAL}^{(2)}$ | Calibration time | $f_{ADC} = 14$ MHz | 5.9 | | | μ s |
| | | | 83 | | | $1/f_{ADC}$ |
| $t_{lat}^{(2)}$ | Injection trigger conversion latency | $f_{ADC} = 14$ MHz | | | 0.214 | μ s |
| | | | | | 3 ⁽⁴⁾ | $1/f_{ADC}$ |
| $t_{latr}^{(2)}$ | Regular trigger conversion latency | $f_{ADC} = 14$ MHz | | | 0.143 | μ s |
| | | | | | 2 ⁽⁴⁾ | $1/f_{ADC}$ |
| $t_S^{(2)}$ | Sampling time | $f_{ADC} = 14$ MHz | 0.107 | | 17.1 | μ s |
| | | | 1.5 | | 239.5 | $1/f_{ADC}$ |
| $t_{STAB}^{(2)}$ | Power-up time | | 0 | 0 | 1 | μ s |
| $t_{CONV}^{(2)}$ | Total conversion time (including sampling time) | $f_{ADC} = 14$ MHz | 1 | | 18 | μ s |
| | | | 14 to 252 (t_S for sampling +12.5 for successive approximation) | | | $1/f_{ADC}$ |

1. Based on characterization, not tested in production.

2. Guaranteed by design, not tested in production.

3. In devices delivered in VFQFPN and LQFP packages, V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} . Devices that come in the TFBGA64 package have a V_{REF+} pin but no V_{REF-} pin (V_{REF-} is internally connected to V_{SSA}), see [Table 5](#) and [Figure 7](#).

4. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in [Table 46](#).

Equation 1: R_{AIN} max formula:

$$R_{AIN} < \frac{T_s}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here N = 12 (from 12-bit resolution).

Table 47. R_{AIN} max for f_{ADC} = 14 MHz⁽¹⁾

| T _s (cycles) | t _s (μs) | R _{AIN} max (kΩ) |
|-------------------------|---------------------|---------------------------|
| 1.5 | 0.11 | 0.4 |
| 7.5 | 0.54 | 5.9 |
| 13.5 | 0.96 | 11.4 |
| 28.5 | 2.04 | 25.2 |
| 41.5 | 2.96 | 37.2 |
| 55.5 | 3.96 | 50 |
| 71.5 | 5.11 | NA |
| 239.5 | 17.1 | NA |

1. Based on characterization, not tested in production.

Table 48. ADC accuracy - limited test conditions^{(1) (2)}

| Symbol | Parameter | Test conditions | Typ | Max ⁽³⁾ | Unit |
|--------|------------------------------|--|------|--------------------|------|
| ET | Total unadjusted error | f _{PCLK2} = 56 MHz, f _{ADC} = 14 MHz, R _{AIN} < 10 kΩ V _{DDA} = 3 V to 3.6 V T _A = 25 °C Measurements made after ADC calibration | ±1.3 | ±2 | LSB |
| EO | Offset error | | ±1 | ±1.5 | |
| EG | Gain error | | ±0.5 | ±1.5 | |
| ED | Differential linearity error | | ±0.7 | ±1 | |
| EL | Integral linearity error | | ±0.8 | ±1.5 | |

- ADC DC accuracy values are measured after internal calibration.
- ADC Accuracy vs. Negative Injection Current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
Any positive injection current within the limits specified for I_{INJ(PIN)} and ΣI_{INJ(PIN)} in [Section 5.3.12](#) does not affect the ADC accuracy.
- Based on characterization, not tested in production.

Table 49. ADC accuracy^{(1) (2) (3)}

| Symbol | Parameter | Test conditions | Typ | Max ⁽⁴⁾ | Unit |
|--------|------------------------------|--|-----------|--------------------|------|
| ET | Total unadjusted error | $f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 14 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$ $V_{DDA} = 2.4 \text{ V to } 3.6 \text{ V}$ Measurements made after ADC calibration | ± 2 | ± 5 | LSB |
| EO | Offset error | | ± 1.5 | ± 2.5 | |
| EG | Gain error | | ± 1.5 | ± 3 | |
| ED | Differential linearity error | | ± 1 | ± 2 | |
| EL | Integral linearity error | | ± 1.5 | ± 3 | |

1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
3. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 5.3.12](#) does not affect the ADC accuracy.
4. Based on characterization, not tested in production.

Figure 37. ADC accuracy characteristics

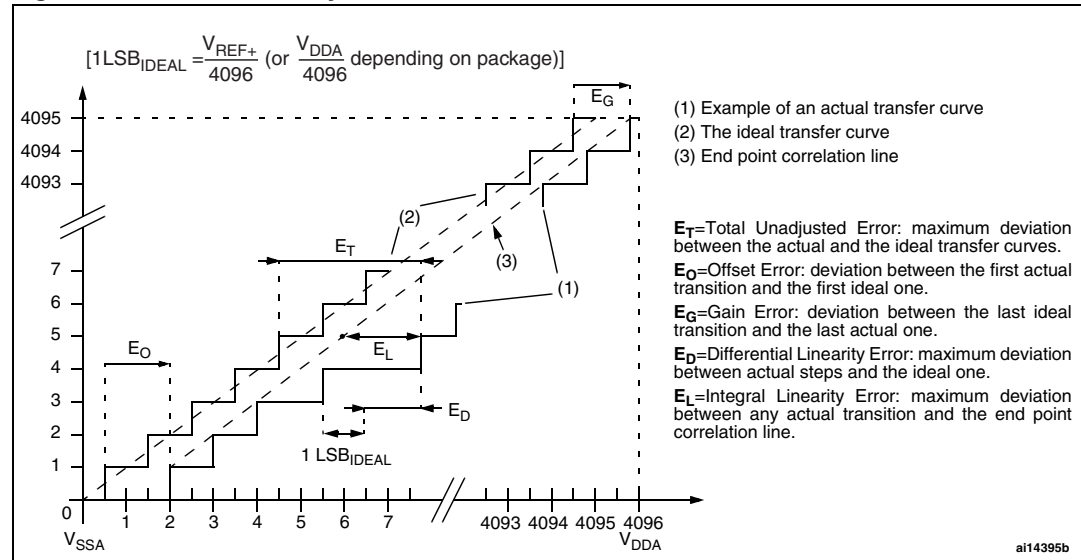
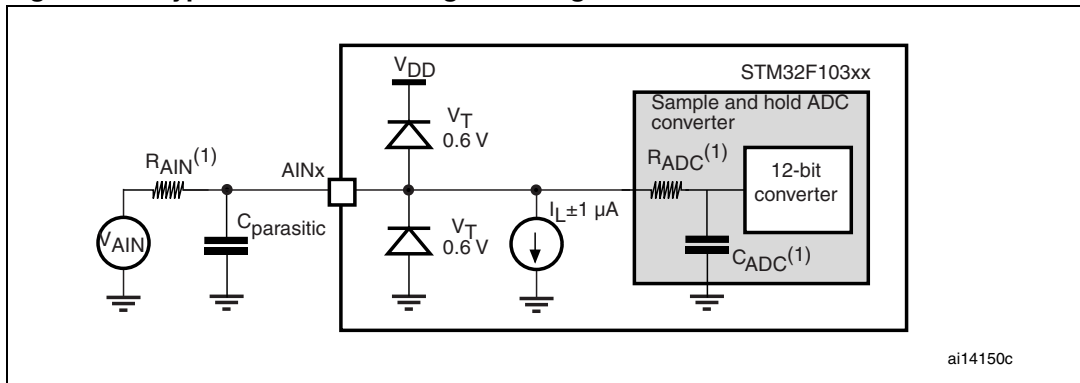


Figure 38. Typical connection diagram using the ADC

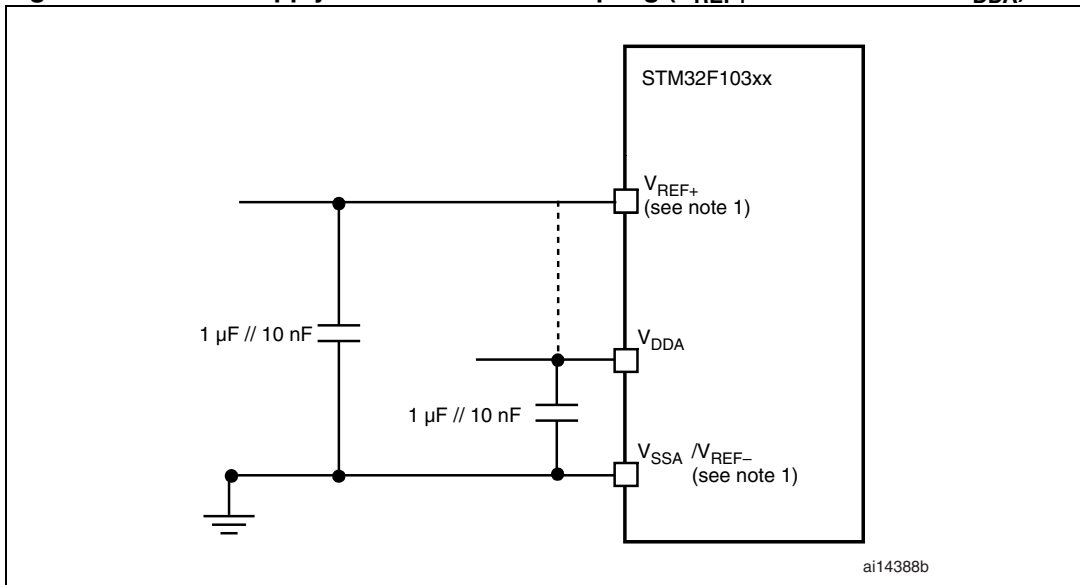


1. Refer to [Table 46](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

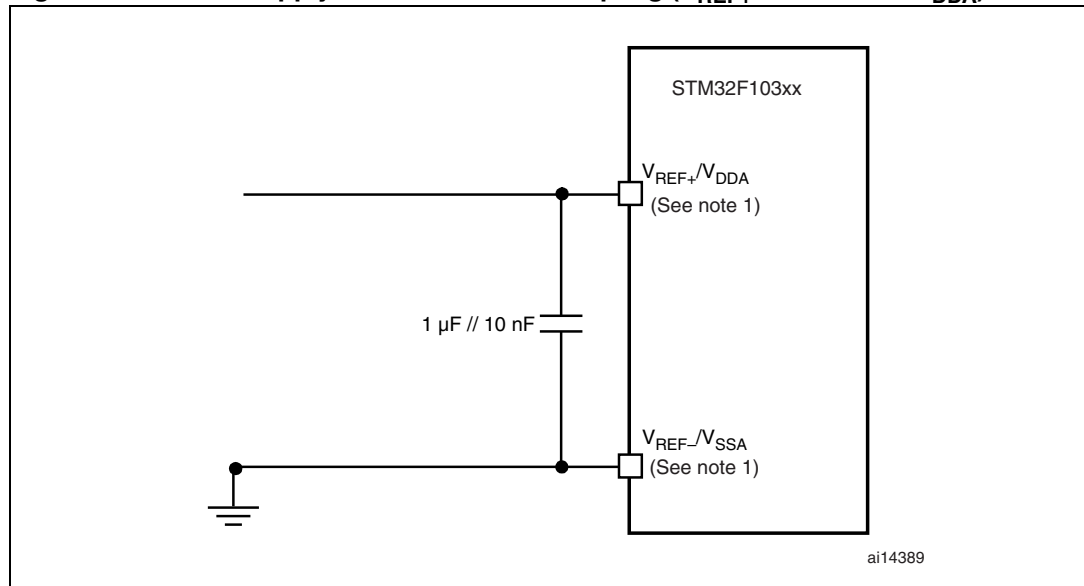
Power supply decoupling should be performed as shown in [Figure 39](#) or [Figure 40](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 39. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

Figure 40. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})



1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

5.3.19 Temperature sensor characteristics

Table 50. TS characteristics

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------------------------|--|------|---------|---------|-----------------|
| $T_L^{(1)}$ | V_{SENSE} linearity with temperature | | ± 1 | ± 2 | $^{\circ}C$ |
| Avg_Slope ⁽¹⁾ | Average slope | 4.0 | 4.3 | 4.6 | mV/ $^{\circ}C$ |
| $V_{25}^{(1)}$ | Voltage at 25 $^{\circ}C$ | 1.34 | 1.43 | 1.52 | V |
| $t_{START}^{(2)}$ | Startup time | 4 | | 10 | μs |
| $T_{S_temp}^{(3)(2)}$ | ADC sampling time when reading the temperature | | | 17.1 | μs |

1. Based on characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

6 Package characteristics

6.1 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 41. VFQFPN36 6 x 6 mm, 0.5 mm pitch, package outline⁽¹⁾

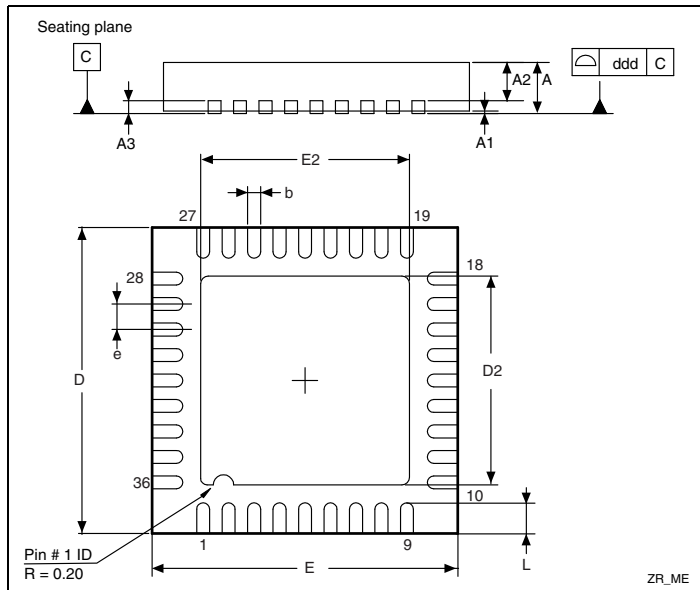
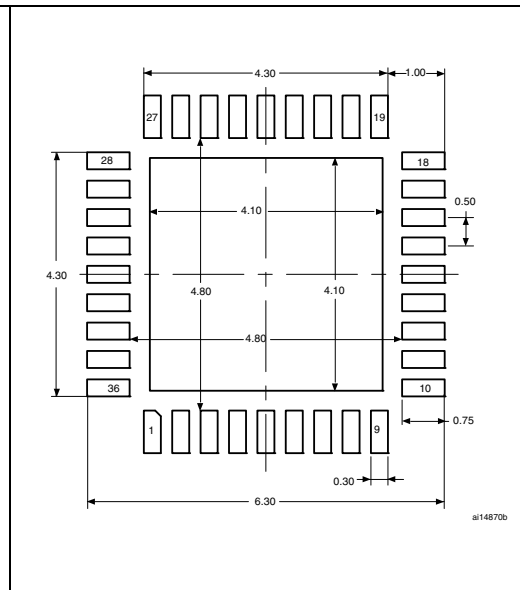


Figure 42. Recommended footprint (dimensions in mm)⁽¹⁾⁽²⁾



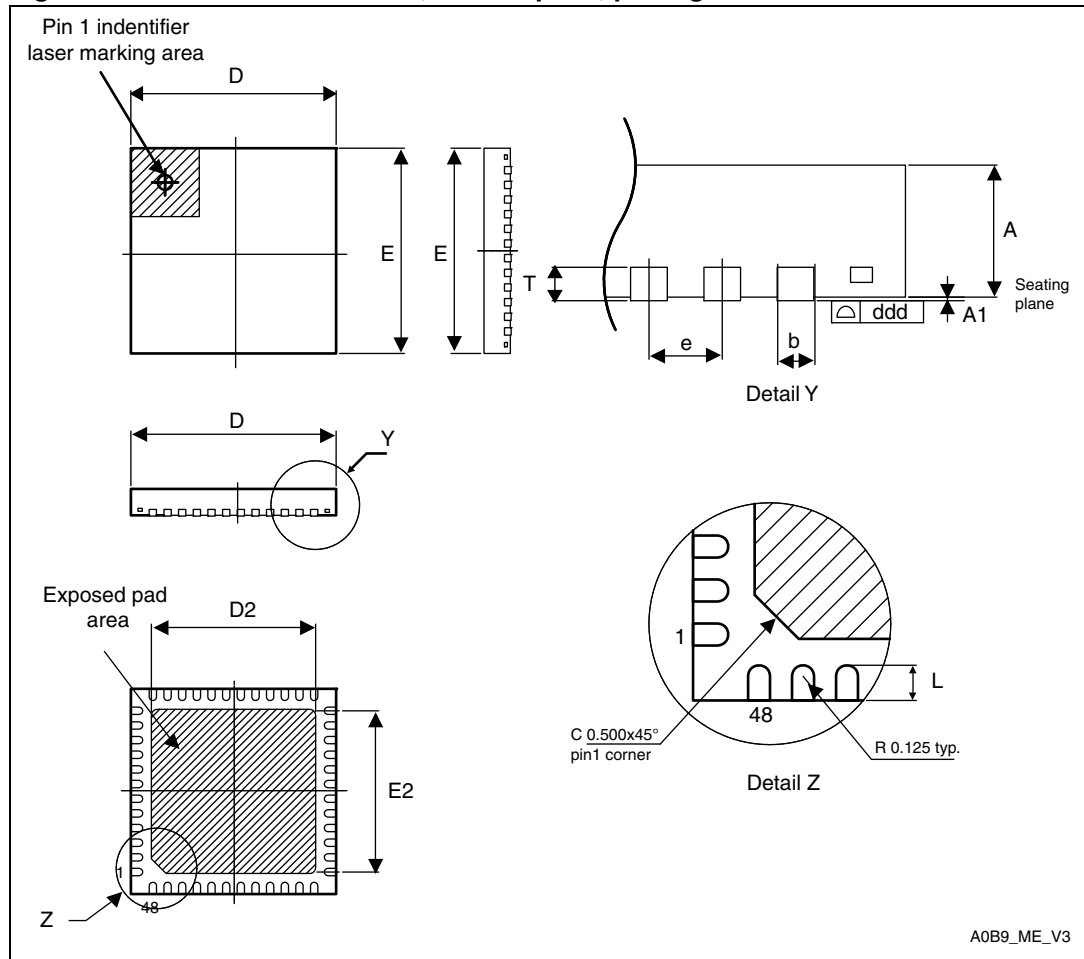
1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead solder joint life.

Table 51. VFQFPN36 6 x 6 mm, 0.5 mm pitch, package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|-------------|-------|-------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 0.800 | 0.900 | 1.000 | 0.0315 | 0.0354 | 0.0394 |
| A1 | | 0.020 | 0.050 | | 0.0008 | 0.0020 |
| A2 | | 0.650 | 1.000 | | 0.0256 | 0.0394 |
| A3 | | 0.250 | | | 0.0098 | |
| b | 0.180 | 0.230 | 0.300 | 0.0071 | 0.0091 | 0.0118 |
| D | 5.875 | 6.000 | 6.125 | 0.2313 | 0.2362 | 0.2411 |
| D2 | 1.750 | 3.700 | 4.250 | 0.0689 | 0.1457 | 0.1673 |
| E | 5.875 | 6.000 | 6.125 | 0.2313 | 0.2362 | 0.2411 |
| E2 | 1.750 | 3.700 | 4.250 | 0.0689 | 0.1457 | 0.1673 |
| e | 0.450 | 0.500 | 0.550 | 0.0177 | 0.0197 | 0.0217 |
| L | 0.350 | 0.550 | 0.750 | 0.0138 | 0.0217 | 0.0295 |
| ddd | 0.080 | | | 0.0031 | | |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 43. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package outline



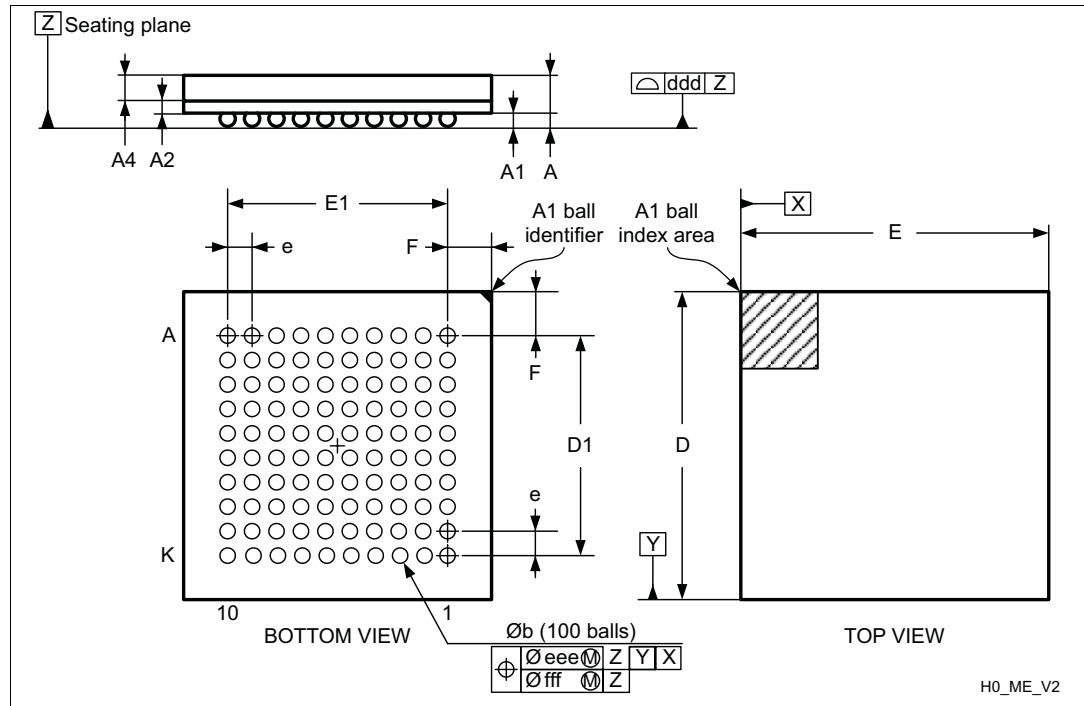
A0B9_ME_V3

1. Drawing is not to scale.
2. There is an exposed die pad on the underside of the QFPN package, this pad is not internally connected to the VSS or VDD power pads. It is recommended to connect it to VSS.
3. All leads/pads should also be soldered to the PCB to improve the lead solder joint life.

Table 52. UFQFPN48 7 x 7 mm, 0.5 mm pitch, package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|-------------|-------|-------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 0.500 | 0.550 | 0.600 | 0.0197 | 0.0217 | 0.0236 |
| A1 | 0.000 | 0.020 | 0.050 | 0.0000 | 0.0008 | 0.0020 |
| D | 6.900 | 7.000 | 7.100 | 0.2717 | 0.2756 | 0.2795 |
| E | 6.900 | 7.000 | 7.100 | 0.2717 | 0.2756 | 0.2795 |
| L | 0.300 | 0.400 | 0.500 | 0.0118 | 0.0157 | 0.0197 |
| T | | 0.152 | | | 0.0060 | |
| b | 0.200 | 0.250 | 0.300 | 0.0079 | 0.0098 | 0.0118 |
| e | | 0.500 | | | 0.0197 | |
| ddd | | 0.080 | | | 0.0031 | |

Figure 45. LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 53. LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|---------------------|-------------|--------|--------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | | | 1.700 | | | 0.0669 |
| A1 | 0.270 | | | 0.0106 | | |
| A2 | | 0.300 | | | 0.0118 | |
| A4 | | | 0.800 | | | 0.0315 |
| b | 0.450 | 0.500 | 0.550 | 0.0177 | 0.0197 | 0.0217 |
| D | 9.850 | 10.000 | 10.150 | 0.3878 | 0.3937 | 0.3996 |
| D1 | | 7.200 | | | 0.2835 | |
| E | 9.850 | 10.000 | 10.150 | 0.3878 | 0.3937 | 0.3996 |
| E1 | | 7.200 | | | 0.2835 | |
| e | | 0.800 | | | 0.0315 | |
| F | | 1.400 | | | 0.0551 | |
| ddd | | | 0.120 | | | 0.0047 |
| eee | | | 0.150 | | | 0.0059 |
| fff | | | 0.080 | | | 0.0031 |
| N (number of balls) | 100 | | | | | |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 46. Recommended PCB design rules (0.80/0.75 mm pitch BGA)

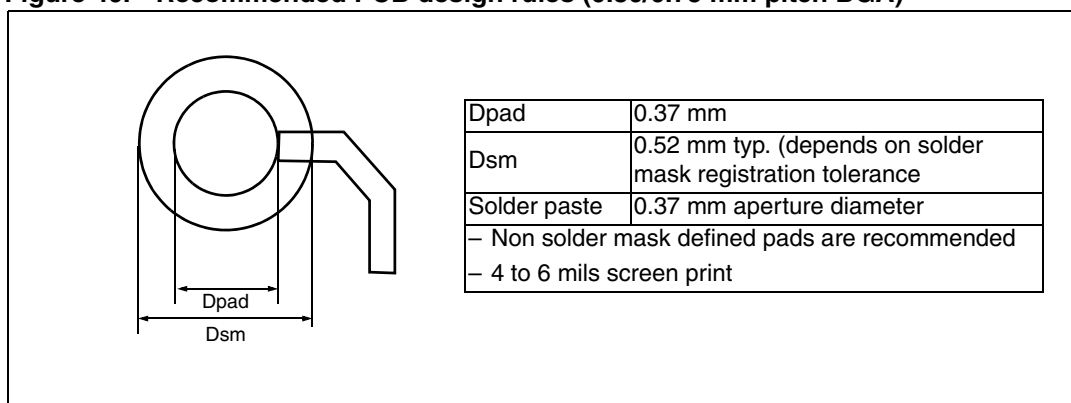
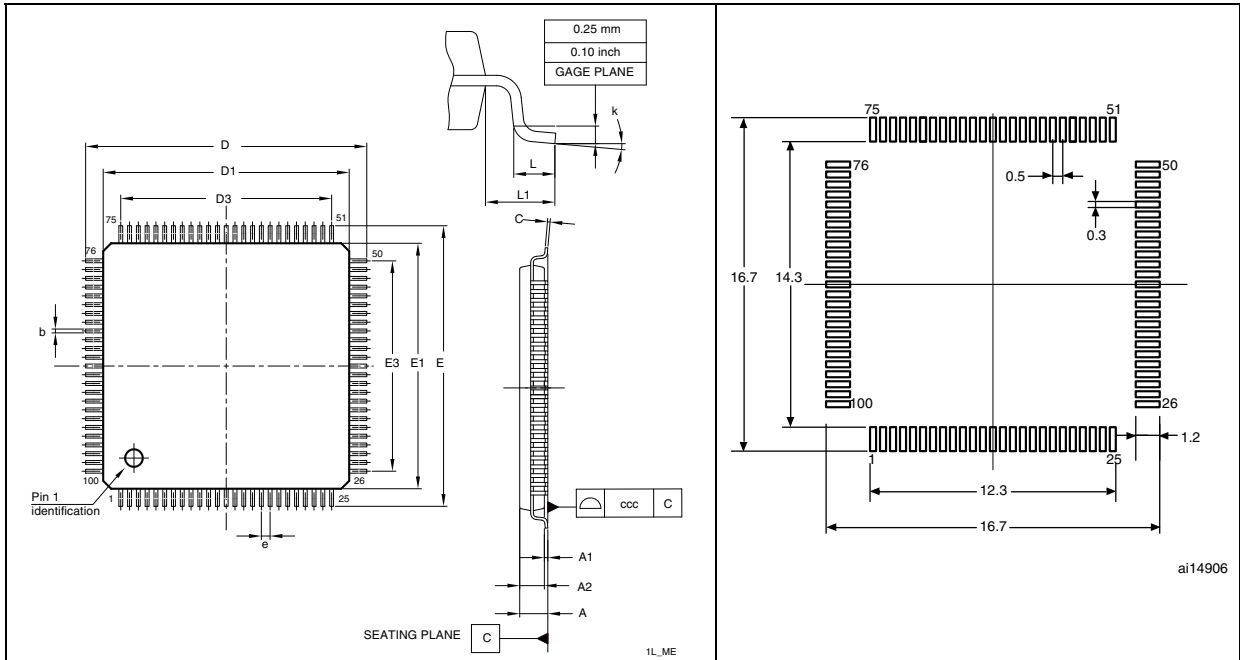


Figure 47. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline⁽¹⁾

Figure 48. Recommended footprint⁽¹⁾⁽²⁾



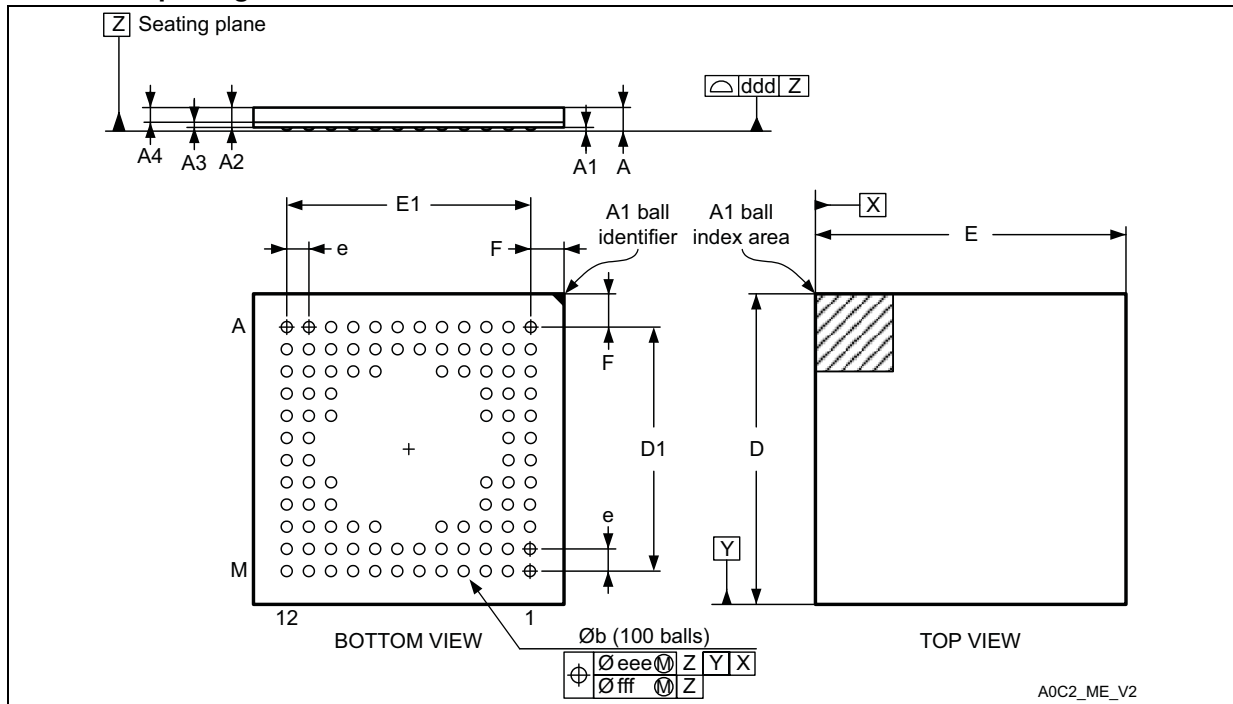
1. Drawing is not to scale.
2. Dimensions are in millimeters.

Table 54. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|-------------|------|------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | | | 1.6 | | | 0.063 |
| A1 | 0.05 | | 0.15 | 0.002 | | 0.0059 |
| A2 | 1.35 | 1.4 | 1.45 | 0.0531 | 0.0551 | 0.0571 |
| b | 0.17 | 0.22 | 0.27 | 0.0067 | 0.0087 | 0.0106 |
| c | 0.09 | | 0.2 | 0.0035 | | 0.0079 |
| D | 15.8 | 16 | 16.2 | 0.622 | 0.6299 | 0.6378 |
| D1 | 13.8 | 14 | 14.2 | 0.5433 | 0.5512 | 0.5591 |
| D3 | | 12 | | | 0.4724 | |
| E | 15.8 | 16 | 16.2 | 0.622 | 0.6299 | 0.6378 |
| E1 | 13.8 | 14 | 14.2 | 0.5433 | 0.5512 | 0.5591 |
| E3 | | 12 | | | 0.4724 | |
| e | | 0.5 | | | 0.0197 | |
| L | 0.45 | 0.6 | 0.75 | 0.0177 | 0.0236 | 0.0295 |
| L1 | | 1 | | | 0.0394 | |
| k | 0.0° | 3.5° | 7.0° | 0.0° | 3.5° | 7.0° |
| ccc | 0.08 | | | 0.0031 | | |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 49. UFBGA100 - ultra fine pitch ball grid array, 7 x 7 mm, 0.50 mm pitch, package outline



1. Drawing is not to scale.

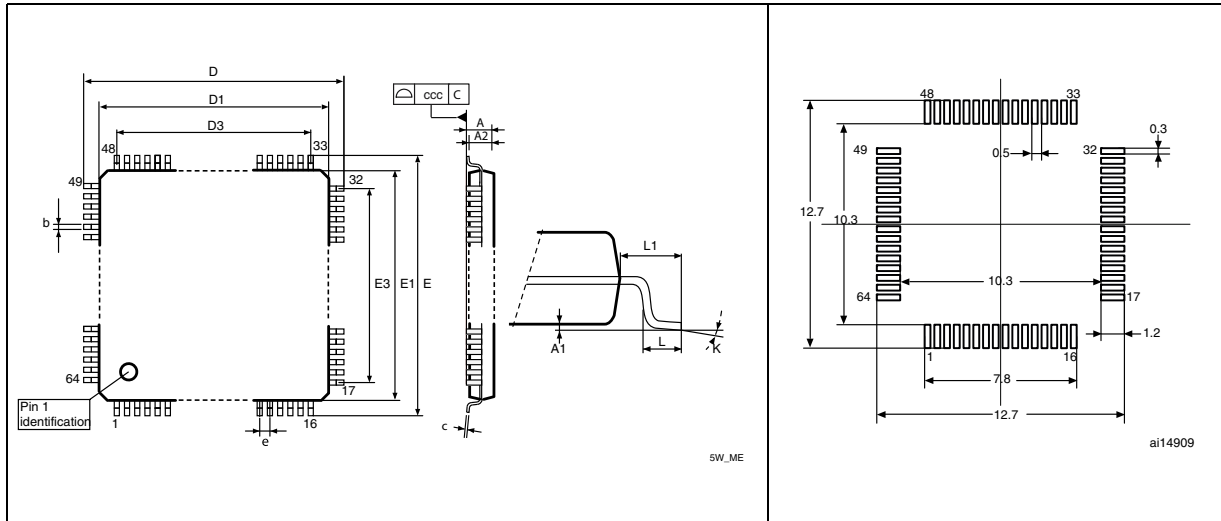
Table 55. UFBGA100 - ultra fine pitch ball grid array, 7 x 7 mm, 0.50 mm pitch, package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|-------------|-------|-------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | 0.460 | 0.530 | 0.600 | 0.0181 | 0.0209 | 0.0236 |
| A1 | 0.050 | 0.080 | 0.110 | 0.0020 | 0.0031 | 0.0043 |
| A2 | 0.400 | 0.450 | 0.500 | 0.0157 | 0.0177 | 0.0197 |
| A3 | 0.080 | 0.130 | 0.180 | 0.0031 | 0.0051 | 0.0071 |
| A4 | 0.270 | 0.320 | 0.370 | 0.0106 | 0.0126 | 0.0146 |
| b | 0.200 | 0.250 | 0.300 | 0.0079 | 0.0098 | 0.0118 |
| D | 6.950 | 7.000 | 7.050 | 0.2736 | 0.2756 | 0.2776 |
| D1 | 5.450 | 5.500 | 5.550 | 0.2146 | 0.2165 | 0.2185 |
| E | 6.950 | 7.000 | 7.050 | 0.2736 | 0.2756 | 0.2776 |
| E1 | 5.450 | 5.500 | 5.550 | 0.2146 | 0.2165 | 0.2185 |
| e | | 0.500 | | | 0.0197 | |
| F | 0.700 | 0.750 | 0.800 | 0.0276 | 0.0295 | 0.0315 |
| ddd | | | 0.100 | | | 0.0039 |
| eee | | | 0.150 | | | 0.0059 |
| fff | | | 0.050 | | | 0.0020 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 50. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline⁽¹⁾

Figure 51. Recommended footprint⁽¹⁾⁽²⁾



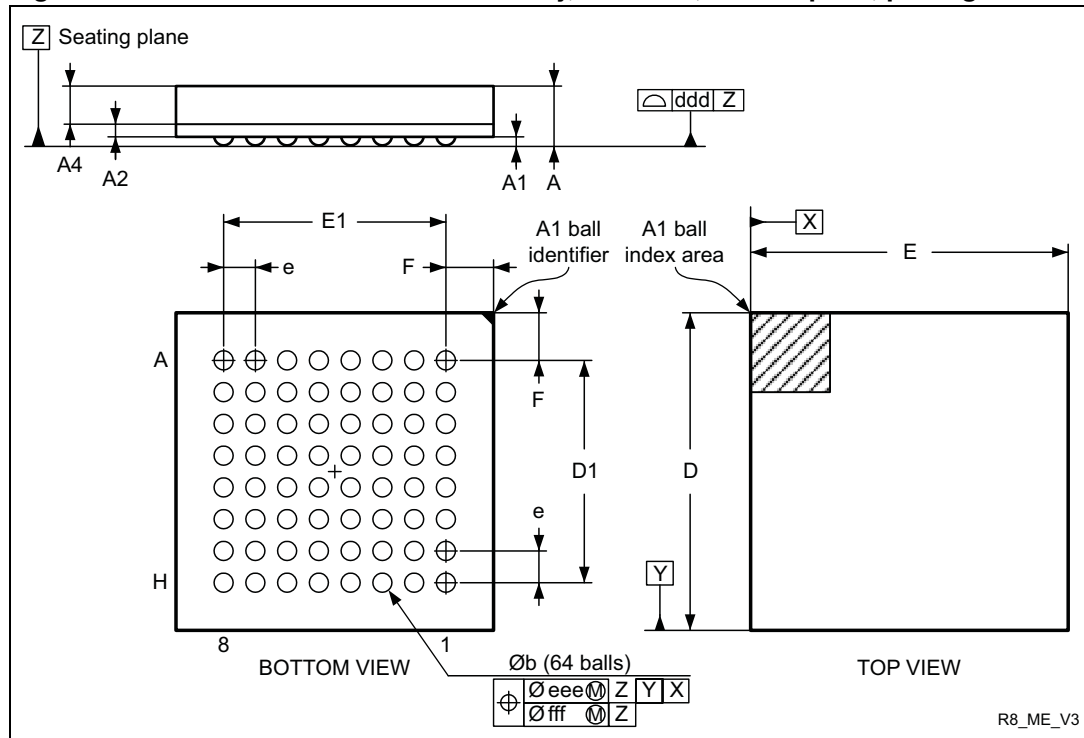
1. Drawing is not to scale.
2. Dimensions are in millimeters.

Table 56. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|----------------|-------|------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | | | 1.60 | | | 0.0630 |
| A1 | 0.05 | | 0.15 | 0.0020 | | 0.0059 |
| A2 | 1.35 | 1.40 | 1.45 | 0.0531 | 0.0551 | 0.0571 |
| b | 0.17 | 0.22 | 0.27 | 0.0067 | 0.0087 | 0.0106 |
| c | 0.09 | | 0.20 | 0.0035 | | 0.0079 |
| D | | 12.00 | | | 0.4724 | |
| D1 | | 10.00 | | | 0.3937 | |
| E | | 12.00 | | | 0.4724 | |
| E1 | | 10.00 | | | 0.3937 | |
| e | | 0.50 | | | 0.0197 | |
| θ | 0° | 3.5° | 7° | 0° | 3.5° | 7° |
| L | 0.45 | 0.60 | 0.75 | 0.0177 | 0.0236 | 0.0295 |
| L1 | | 1.00 | | | 0.0394 | |
| N | Number of pins | | | | | |
| | 64 | | | | | |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 52. TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package outline



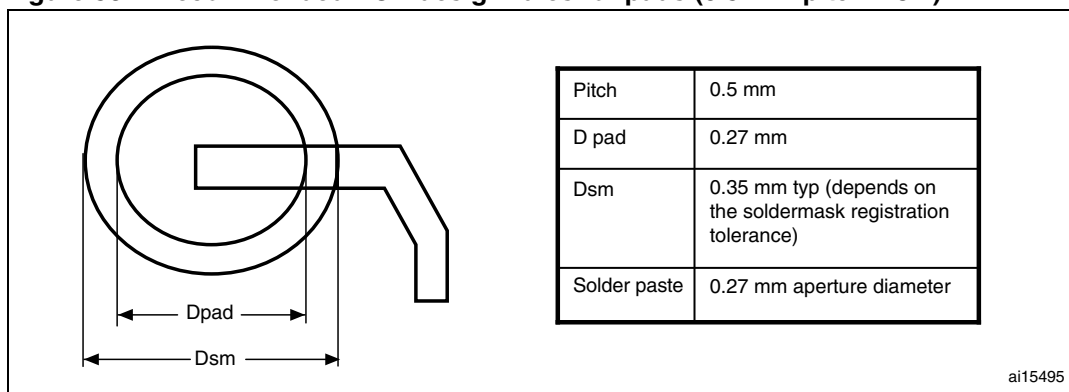
1. Drawing is not to scale.

Table 57. TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|-------------|-------|-------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | | | 1.200 | | | 0.0472 |
| A1 | 0.150 | | | 0.0059 | | |
| A2 | | 0.200 | | | 0.0079 | |
| A4 | | | 0.600 | | | 0.0236 |
| b | 0.250 | 0.300 | 0.350 | 0.0098 | 0.0118 | 0.0138 |
| D | 4.850 | 5.000 | 5.150 | 0.1909 | 0.1969 | 0.2028 |
| D1 | | 3.500 | | | 0.1378 | |
| E | 4.850 | 5.000 | 5.150 | 0.1909 | 0.1969 | 0.2028 |
| E1 | | 3.500 | | | 0.1378 | |
| e | | 0.500 | | | 0.0197 | |
| F | | 0.750 | | | 0.0295 | |
| ddd | | | 0.080 | | | 0.0031 |
| eee | | | 0.150 | | | 0.0059 |
| fff | | | 0.050 | | | 0.0020 |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

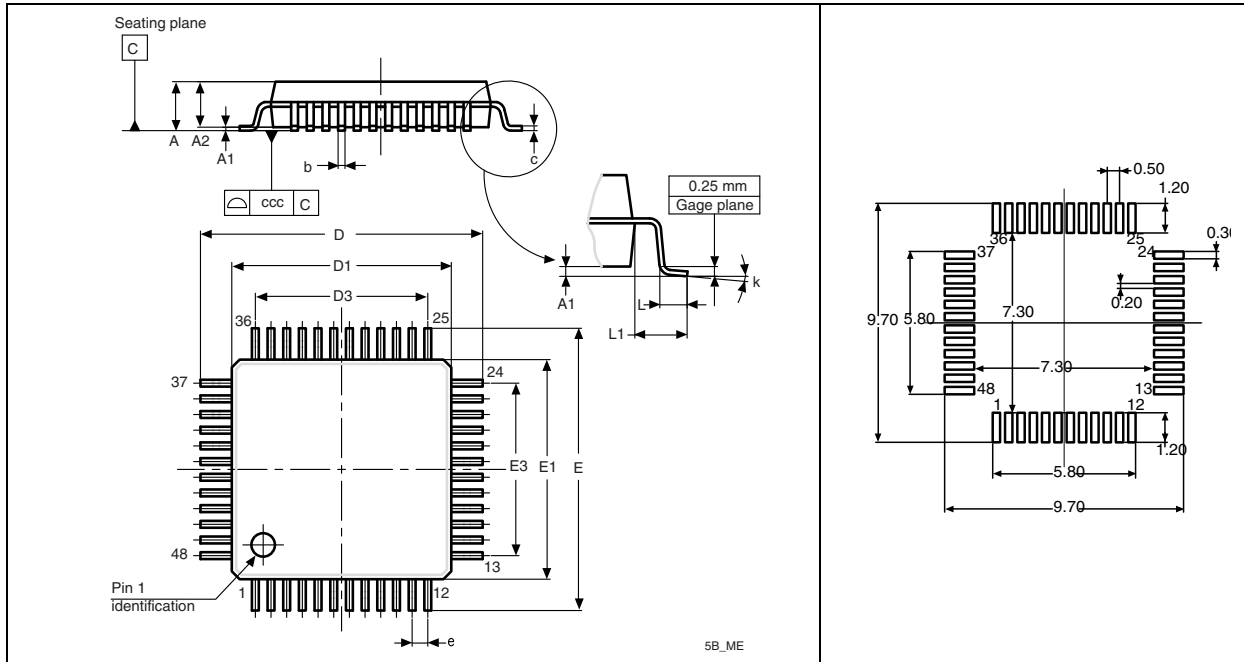
Figure 53. Recommended PCB design rules for pads (0.5 mm pitch BGA)



1. Non solder mask defined (NSMD) pads are recommended
2. 4 to 6 mils solder paste screen printing process

Figure 54. LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package outline⁽¹⁾

Figure 55. Recommended footprint⁽¹⁾⁽²⁾



1. Drawing is not to scale.
2. Dimensions are in millimeters.

Table 58. LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package mechanical data

| Symbol | millimeters | | | inches ⁽¹⁾ | | |
|--------|-------------|-------|-------|-----------------------|--------|--------|
| | Min | Typ | Max | Min | Typ | Max |
| A | | | 1.600 | | | 0.0630 |
| A1 | 0.050 | | 0.150 | 0.0020 | | 0.0059 |
| A2 | 1.350 | 1.400 | 1.450 | 0.0531 | 0.0551 | 0.0571 |
| b | 0.170 | 0.220 | 0.270 | 0.0067 | 0.0087 | 0.0106 |
| c | 0.090 | | 0.200 | 0.0035 | | 0.0079 |
| D | 8.800 | 9.000 | 9.200 | 0.3465 | 0.3543 | 0.3622 |
| D1 | 6.800 | 7.000 | 7.200 | 0.2677 | 0.2756 | 0.2835 |
| D3 | | 5.500 | | | 0.2165 | |
| E | 8.800 | 9.000 | 9.200 | 0.3465 | 0.3543 | 0.3622 |
| E1 | 6.800 | 7.000 | 7.200 | 0.2677 | 0.2756 | 0.2835 |
| E3 | | 5.500 | | | 0.2165 | |
| e | | 0.500 | | | 0.0197 | |
| L | 0.450 | 0.600 | 0.750 | 0.0177 | 0.0236 | 0.0295 |
| L1 | | 1.000 | | | 0.0394 | |
| k | 0° | 3.5° | 7° | 0° | 3.5° | 7° |
| ccc | 0.080 | | | 0.0031 | | |

1. Values in inches are converted from mm and rounded to 4 decimal digits.

6.2 Thermal characteristics

The maximum chip junction temperature (T_J max) must never exceed the values given in [Table 9: General operating conditions on page 38](#).

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$ max),
- P_{INT} max is the product of I_{DD} and V_{DD} , expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma (V_{DD} - V_{OH}) \times I_{OH},$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 59. Package thermal characteristics

| Symbol | Parameter | Value | Unit |
|---------------|---|-------|------|
| Θ_{JA} | Thermal resistance junction-ambient LFBGA100 - 10 × 10 mm / 0.8 mm pitch | 44 | °C/W |
| | Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch | 46 | |
| | Thermal resistance junction-ambient UFBGA100 - 7 × 7 mm / 0.5 mm pitch | 59 | |
| | Thermal resistance junction-ambient LQFP64 - 10 × 10 mm / 0.5 mm pitch | 45 | |
| | Thermal resistance junction-ambient TFBGA64 - 5 × 5 mm / 0.5 mm pitch | 65 | |
| | Thermal resistance junction-ambient LQFP48 - 7 × 7 mm / 0.5 mm pitch | 55 | |
| | Thermal resistance junction-ambient UFQFPN 48 - 7 × 7 mm / 0.5 mm pitch | 32 | |
| | Thermal resistance junction-ambient VFQFPN 36 - 6 × 6 mm / 0.5 mm pitch | 18 | |

6.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

6.2.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in [Table 60: Ordering information scheme](#).

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32F103xx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature $T_{Amax} = 82\text{ °C}$ (measured according to JESD51-2),
 $I_{DDmax} = 50\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 20 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$ and maximum 8 I/Os used at the same time in output at low level with $I_{OL} = 20\text{ mA}$, $V_{OL} = 1.3\text{ V}$

$$P_{INTmax} = 50\text{ mA} \times 3.5\text{ V} = 175\text{ mW}$$

$$P_{IOmax} = 20 \times 8\text{ mA} \times 0.4\text{ V} + 8 \times 20\text{ mA} \times 1.3\text{ V} = 272\text{ mW}$$

This gives: $P_{INTmax} = 175\text{ mW}$ and $P_{IOmax} = 272\text{ mW}$:

$$P_{Dmax} = 175 + 272 = 447\text{ mW}$$

Thus: $P_{Dmax} = 447\text{ mW}$

Using the values obtained in [Table 59](#) T_{Jmax} is calculated as follows:

– For LQFP100, 46 °C/W

$$T_{Jmax} = 82\text{ °C} + (46\text{ °C/W} \times 447\text{ mW}) = 82\text{ °C} + 20.6\text{ °C} = 102.6\text{ °C}$$

This is within the range of the suffix 6 version parts ($-40 < T_J < 105\text{ °C}$).

In this case, parts must be ordered at least with the temperature range suffix 6 (see [Table 60: Ordering information scheme](#)).

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature $T_{Amax} = 115\text{ °C}$ (measured according to JESD51-2),
 $I_{DDmax} = 20\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 20 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$

$$P_{INTmax} = 20\text{ mA} \times 3.5\text{ V} = 70\text{ mW}$$

$$P_{IOmax} = 20 \times 8\text{ mA} \times 0.4\text{ V} = 64\text{ mW}$$

This gives: $P_{INTmax} = 70\text{ mW}$ and $P_{IOmax} = 64\text{ mW}$:

$$P_{Dmax} = 70 + 64 = 134\text{ mW}$$

Thus: $P_{Dmax} = 134\text{ mW}$

Using the values obtained in [Table 59](#) T_{Jmax} is calculated as follows:

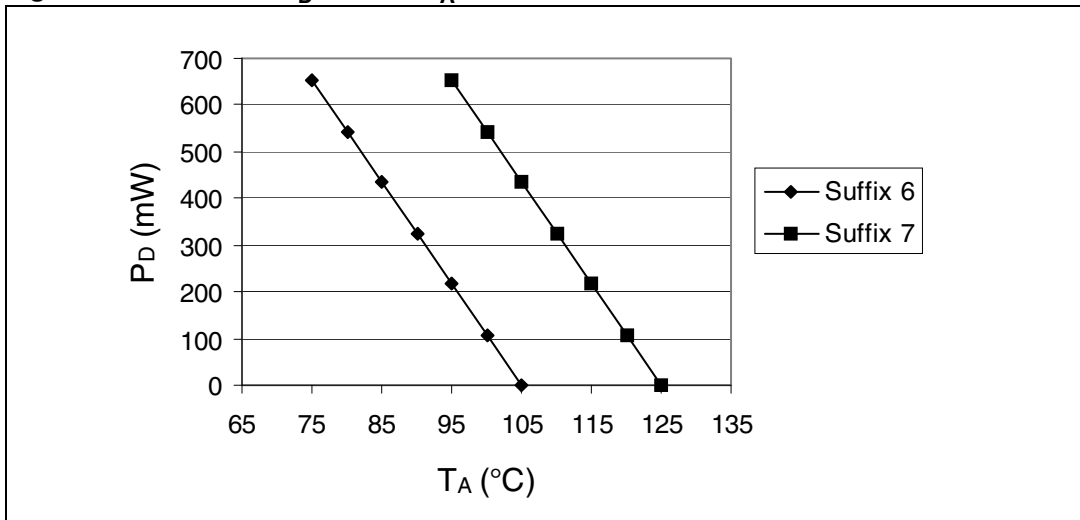
– For LQFP100, 46 °C/W

$$T_{Jmax} = 115\text{ °C} + (46\text{ °C/W} \times 134\text{ mW}) = 115\text{ °C} + 6.2\text{ °C} = 121.2\text{ °C}$$

This is within the range of the suffix 7 version parts ($-40 < T_J < 125\text{ °C}$).

In this case, parts must be ordered at least with the temperature range suffix 7 (see [Table 60: Ordering information scheme](#)).

Figure 56. LQFP100 P_D max vs. T_A



7 Ordering information scheme

Table 60. Ordering information scheme

| | | | | | | | | |
|---|-------|---|-----|---|---|---|---|-----|
| Example: | STM32 | F | 103 | C | 8 | T | 7 | xxx |
| Device family STM32 = ARM-based 32-bit microcontroller | | | | | | | | |
| Product type F = general-purpose | | | | | | | | |
| Device subfamily 103 = performance line | | | | | | | | |
| Pin count T = 36 pins C = 48 pins R = 64 pins V = 100 pins | | | | | | | | |
| Flash memory size⁽¹⁾ 8 = 64 Kbytes of Flash memory B = 128 Kbytes of Flash memory | | | | | | | | |
| Package H = BGA I = UFBGA T = LQFP U = VFQFPN or UFQFPN | | | | | | | | |
| Temperature range 6 = Industrial temperature range, -40 to 85 °C. 7 = Industrial temperature range, -40 to 105 °C. | | | | | | | | |
| Options xxx = programmed parts TR = tape and real | | | | | | | | |

1. Although STM32F103x6 devices are not described in this datasheet, orderable part numbers that do not show the A internal code after temperature range code 6 or 7 should be referred to this datasheet for the electrical characteristics. The low-density datasheet only covers STM32F103x6 devices that feature the A code.

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

8 Revision history

Table 61. Document revision history

| Date | Revision | Changes |
|-------------|----------|---|
| 01-jun-2007 | 1 | Initial release. |
| 20-Jul-2007 | 2 | <p>Flash memory size modified in Note 9, Note 5, Note 7, Note 7 and BGA100 pins added to Table 5: Medium-density STM32F103xx pin definitions. Figure 3: STM32F103xx performance line LFBGA100 ballout added.</p> <p>T_{HSE} changed to T_{LSE} in Figure 23: Low-speed external clock source AC timing diagram. V_{BAT} ranged modified in Power supply schemes.</p> <p>$t_{SU(LSE)}$ changed to $t_{SU(HSE)}$ in Table 22: HSE 4-16 MHz oscillator characteristics. $I_{DD(HSI)}$ max value added to Table 24: HSI oscillator characteristics.</p> <p>Sample size modified and machine model removed in Electrostatic discharge (ESD).</p> <p>Number of parts modified and standard reference updated in Static latch-up. 25 °C and 85 °C conditions removed and class name modified in Table 33: Electrical sensitivities. R_{PU} and R_{PD} min and max values added to Table 35: I/O static characteristics. R_{PU} min and max values added to Table 38: NRST pin characteristics.</p> <p>Figure 32: I2C bus AC waveforms and measurement circuit and Figure 31: Recommended NRST pin protection corrected.</p> <p>Notes removed below Table 9, Table 38, Table 44.</p> <p>I_{DD} typical values changed in Table 11: Maximum current consumption in Run and Sleep modes. Table 39: TIMx characteristics modified.</p> <p>t_{STAB}, V_{REF+} value, t_{lat} and f_{TRIG} added to Table 46: ADC characteristics. In Table 29: Flash memory endurance and data retention, typical endurance and data retention for $T_A = 85\text{ °C}$ added, data retention for $T_A = 25\text{ °C}$ removed.</p> <p>V_{BG} changed to V_{REFINT} in Table 12: Embedded internal reference voltage. Document title changed. Controller area network (CAN) section modified.</p> <p>Figure 14: Power supply scheme modified.</p> <p>Features on page 1 list optimized. Small text changes.</p> |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|--|
| 18-Oct-2007 | 3 | <p>STM32F103CBT6, STM32F103T6 and STM32F103T8 root part numbers added (see Table 2: STM32F103xx medium-density device features and peripheral counts)</p> <p>VFQFPN36 package added (see Section 6: Package characteristics). All packages are ECOPACK® compliant. Package mechanical data inch values are calculated from mm and rounded to 4 decimal digits (see Section 6: Package characteristics).</p> <p>Table 5: Medium-density STM32F103xx pin definitions updated and clarified.</p> <p>Table 26: Low-power mode wakeup timings updated.</p> <p>T_A min corrected in Table 12: Embedded internal reference voltage.</p> <p>Note 2 added below Table 22: HSE 4-16 MHz oscillator characteristics.</p> <p>$V_{ESD(CDM)}$ value added to Table 32: ESD absolute maximum ratings.</p> <p>Note 4 added and V_{OH} parameter description modified in Table 36: Output voltage characteristics.</p> <p>Note 1 modified under Table 37: I/O AC characteristics.</p> <p>Equation 1 and Table 47: RAIN max for fADC = 14 MHz added to Section 5.3.18: 12-bit ADC characteristics.</p> <p>V_{AIN}, t_S max, t_{CONV}, V_{REF+} min and t_{lat} max modified, notes modified and t_{latr} added in Table 46: ADC characteristics.</p> <p>Figure 37: ADC accuracy characteristics updated. Note 1 modified below Figure 38: Typical connection diagram using the ADC.</p> <p>Electrostatic discharge (ESD) on page 60 modified.</p> <p>Number of TIM4 channels modified in Figure 1: STM32F103xx performance line block diagram.</p> <p>Maximum current consumption Table 13, Table 14 and Table 15 updated. V_{hys} modified in Table 35: I/O static characteristics.</p> <p>Table 49: ADC accuracy updated. t_{VDD} modified in Table 10: Operating conditions at power-up / power-down. V_{FESD} value added in Table 30: EMS characteristics.</p> <p>Values corrected, note 2 modified and note 3 removed in Table 26: Low-power mode wakeup timings.</p> <p>Table 16: Typical and maximum current consumptions in Stop and Standby modes: Typical values added for $V_{DD}/V_{BAT} = 2.4$ V, Note 2 modified, Note 2 added.</p> <p>Table 21: Typical current consumption in Standby mode added. On-chip peripheral current consumption on page 50 added.</p> <p>ACC_{HSI} values updated in Table 24: HSI oscillator characteristics.</p> <p>V_{prog} added to Table 28: Flash memory characteristics.</p> <p>Upper option byte address modified in Figure 11: Memory map.</p> <p>Typical f_{LSI} value added in Table 25: LSI oscillator characteristics and internal RC value corrected from 32 to 40 kHz in entire document.</p> <p>T_{S_temp} added to Table 50: TS characteristics. N_{END} modified in Table 29: Flash memory endurance and data retention.</p> <p>$T_{S_vrefint}$ added to Table 12: Embedded internal reference voltage.</p> <p>Handling of unused pins specified in General input/output characteristics on page 62. All I/Os are CMOS and TTL compliant. Figure 39: Power supply and reference decoupling (VREF+ not connected to VDDA) modified.</p> <p>t_{JITTER} and f_{VCO} removed from Table 27: PLL characteristics.</p> <p>Appendix A: Important notes on page 81 added.</p> <p>Added Figure 16, Figure 17, Figure 19 and Figure 21.</p> |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|---|
| 22-Nov-2007 | 4 | <p>Document status promoted from preliminary data to datasheet. The STM32F103xx is USB certified. Small text changes.</p> <p><i>Power supply schemes on page 15</i> modified. Number of communication peripherals corrected for STM32F103Tx and number of GPIOs corrected for LQFP package in <i>Table 2: STM32F103xx medium-density device features and peripheral counts</i>.</p> <p>Main function and default alternate function modified for PC14 and PC15 in, <i>Note 6</i> added and Remap column added in <i>Table 5: Medium-density STM32F103xx pin definitions</i>.</p> <p>V_{DD}-V_{SS} ratings and <i>Note 1</i> modified in <i>Table 6: Voltage characteristics</i>, <i>Note 1</i> modified in <i>Table 7: Current characteristics</i>.</p> <p><i>Note 1</i> and <i>Note 2</i> added in <i>Table 11: Embedded reset and power control block characteristics</i>.</p> <p>I_{DD} value at 72 MHz with peripherals enabled modified in <i>Table 14: Maximum current consumption in Run mode, code with data processing running from RAM</i>.</p> <p>I_{DD} value at 72 MHz with peripherals enabled modified in <i>Table 15: Maximum current consumption in Sleep mode, code running from Flash or RAM on page 44</i>.</p> <p>I_{DD_VBAT} typical value at 2.4 V modified and I_{DD_VBAT} maximum values added in <i>Table 16: Typical and maximum current consumptions in Stop and Standby modes</i>. Note added in <i>Table 17 on page 48</i> and <i>Table 18 on page 49</i>. ADC1 and ADC2 consumption and notes modified in <i>Table 19: Peripheral current consumption</i>.</p> <p>t_{SU(HSE)} and t_{SU(LSE)} conditions modified in <i>Table 22</i> and <i>Table 23</i>, respectively.</p> <p>Maximum values removed from <i>Table 26: Low-power mode wakeup timings</i>. t_{RET} conditions modified in <i>Table 29: Flash memory endurance and data retention</i>. <i>Figure 14: Power supply scheme</i> corrected. <i>Figure 20: Typical current consumption in Stop mode with regulator in Low-power mode versus temperature at VDD = 3.3 V and 3.6 V</i> added. Note removed below <i>Figure 33: SPI timing diagram - slave mode and CPHA = 0</i>. Note added below <i>Figure 34: SPI timing diagram - slave mode and CPHA = 1(1)</i>.</p> <p>Details on unused pins removed from <i>General input/output characteristics on page 62</i>.</p> <p><i>Table 42: SPI characteristics</i> updated. <i>Table 43: USB startup time</i> added. V_{AIN}, t_{lat} and t_{latr} modified, note added and I_{IKG} removed in <i>Table 46: ADC characteristics</i>. Test conditions modified and note added in <i>Table 49: ADC accuracy</i>. Note added below <i>Table 47</i> and <i>Table 50</i>.</p> <p>Inch values corrected in <i>Table 54: LQPF100, 14 x 14 mm 100-pin low-profile quad flat package mechanical data</i>, <i>Table 56: LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package mechanical data</i> and <i>Table 58: LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package mechanical data</i>.</p> <p>Θ_{JA} value for VFQFPN36 package added in <i>Table 59: Package thermal characteristics</i>.</p> <p>Order codes replaced by <i>Section 7: Ordering information scheme</i>.</p> <p>MCU 's operating conditions modified in <i>Typical current consumption on page 47</i>. Avg_Slope and V₂₅ modified in <i>Table 50: TS characteristics</i>.</p> <p><i>I2C interface characteristics on page 70</i> modified.</p> <p>Impedance size specified in <i>A.4: Voltage glitch on ADC input 0 on page 81</i>.</p> |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|---|
| 14-Mar-2008 | 5 | <p>Figure 2: Clock tree on page 12 added.</p> <p>Maximum T_J value given in Table 8: Thermal characteristics on page 38.</p> <p>CRC feature added (see CRC (cyclic redundancy check) calculation unit on page 9 and Figure 11: Memory map on page 34 for address).</p> <p>I_{DD} modified in Table 16: Typical and maximum current consumptions in Stop and Standby modes.</p> <p>ACC_{HSI} modified in Table 24: HSI oscillator characteristics on page 55, note 2 removed.</p> <p>P_D, T_A and T_J added, t_{prog} values modified and t_{prog} description clarified in Table 28: Flash memory characteristics on page 57.</p> <p>t_{RET} modified in Table 29: Flash memory endurance and data retention.</p> <p>$V_{NF(NRST)}$ unit corrected in Table 38: NRST pin characteristics on page 68.</p> <p>Table 42: SPI characteristics on page 72 modified.</p> <p>I_{VREF} added to Table 46: ADC characteristics on page 76.</p> <p>Table 48: ADC accuracy - limited test conditions added. Table 49: ADC accuracy modified.</p> <p>LQFP100 package specifications updated (see Section 6: Package characteristics on page 81).</p> <p>Recommended LQFP100, LQFP 64, LQFP48 and VFQFPN36 footprints added (see Figure 48, Figure 51, Figure 55 and Figure 42).</p> <p>Section 6.2: Thermal characteristics on page 93 modified, Section 6.2.1 and Section 6.2.2 added.</p> <p>Appendix A: Important notes on page 81 removed.</p> |
| 21-Mar-2008 | 6 | <p>Small text changes. Figure 11: Memory map clarified.</p> <p>In Table 29: Flash memory endurance and data retention:</p> <ul style="list-style-type: none"> – N_{END} tested over the whole temperature range – cycling conditions specified for t_{RET} – t_{RET} min modified at $T_A = 55\text{ °C}$ <p>V_{25}, Avg_Slope and T_L modified in Table 50: TS characteristics.</p> <p>CRC feature removed.</p> |
| 22-May-2008 | 7 | <p>CRC feature added back. Small text changes. Section 1: Introduction modified. Section 2.2: Full compatibility throughout the family added.</p> <p>I_{DD} at T_A max = 105 °C added to Table 16: Typical and maximum current consumptions in Stop and Standby modes on page 45.</p> <p>I_{DD_VBAT} removed from Table 21: Typical current consumption in Standby mode on page 47.</p> <p>Values added to Table 41: SCL frequency (fPCLK1= 36 MHz., VDD_I2C = 3.3 V) on page 71.</p> <p>Figure 33: SPI timing diagram - slave mode and CPHA = 0 on page 73 modified. Equation 1 corrected.</p> <p>t_{RET} at $T_A = 105\text{ °C}$ modified in Table 29: Flash memory endurance and data retention on page 58.</p> <p>V_{USB} added to Table 44: USB DC electrical characteristics on page 75.</p> <p>Figure 56: LQFP100 PD max vs. TA on page 95 modified.</p> <p>Axx option added to Table 60: Ordering information scheme on page 96.</p> |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|---|
| 21-Jul-2008 | 8 | <p><i>Power supply supervisor</i> updated and V_{DDA} added to Table 9: General operating conditions.</p> <p>Capacitance modified in Figure 14: Power supply scheme on page 36.</p> <p>Table notes revised in Section 5: Electrical characteristics.</p> <p>Table 16: Typical and maximum current consumptions in Stop and Standby modes modified.</p> <p>Data added to Table 16: Typical and maximum current consumptions in Stop and Standby modes and Table 21: Typical current consumption in Standby mode removed.</p> <p>f_{HSE_ext} modified in Table 20: High-speed external user clock characteristics on page 51. f_{PLL_IN} modified in Table 27: PLL characteristics on page 57.</p> <p>Minimum SDA and SCL fall time value for Fast mode removed from Table 40: I2C characteristics on page 70, note 1 modified.</p> <p>$t_{h(NSS)}$ modified in Table 42: SPI characteristics on page 72 and Figure 33: SPI timing diagram - slave mode and CPHA = 0 on page 73.</p> <p>C_{ADC} modified in Table 46: ADC characteristics on page 76 and Figure 38: Typical connection diagram using the ADC modified.</p> <p>Typical T_{S_temp} value removed from Table 50: TS characteristics on page 80.</p> <p>LQFP48 package specifications updated (see Table 58 and Table 55), Section 6: Package characteristics revised.</p> <p>Axx option removed from Table 60: Ordering information scheme on page 96.</p> <p>Small text changes.</p> |
| 22-Sep-2008 | 9 | <p>STM32F103x6 part numbers removed (see Table 60: Ordering information scheme). Small text changes.</p> <p>General-purpose timers (TIMx) and Advanced-control timer (TIM1) on page 18 updated.</p> <p>Notes updated in Table 5: Medium-density STM32F103xx pin definitions on page 28.</p> <p>Note 2 modified below Table 6: Voltage characteristics on page 37, $\Delta V_{DDx} _{min}$ and $\Delta V_{DDx} _{min}$ removed.</p> <p>Measurement conditions specified in Section 5.3.5: Supply current characteristics on page 41.</p> <p>I_{DD} in standby mode at 85 °C modified in Table 16: Typical and maximum current consumptions in Stop and Standby modes on page 45.</p> <p>General input/output characteristics on page 62 modified.</p> <p>f_{HCLK} conditions modified in Table 30: EMS characteristics on page 59.</p> <p>Θ_{JA} and pitch value modified for LFBGA100 package in Table 59: Package thermal characteristics. Small text changes.</p> |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|--|
| 23-Apr-2009 | 10 | <p>I/O information clarified <i>on page 1</i>.</p> <p><i>Figure 3: STM32F103xx performance line LFBGA100 ballout</i> modified.</p> <p><i>Figure 11: Memory map</i> modified. <i>Table 4: Timer feature comparison</i> added.</p> <p>PB4, PB13, PB14, PB15, PB3/TRACESWO moved from Default column to Remap column in <i>Table 5: Medium-density STM32F103xx pin definitions</i>.</p> <p>P_D for LFBGA100 corrected in <i>Table 9: General operating conditions</i>.</p> <p>Note modified in <i>Table 13: Maximum current consumption in Run mode, code with data processing running from Flash</i> and <i>Table 15: Maximum current consumption in Sleep mode, code running from Flash or RAM</i>.</p> <p><i>Table 20: High-speed external user clock characteristics</i> and <i>Table 21: Low-speed external user clock characteristics</i> modified.</p> <p><i>Figure 20</i> shows a typical curve (title modified). ACC_{HSI} max values modified in <i>Table 24: HSI oscillator characteristics</i>.</p> <p>TFBGA64 package added (see <i>Table 57</i> and <i>Table 52</i>). Small text changes.</p> |
| 22-Sep-2009 | 11 | <p><i>Note 5</i> updated and <i>Note 4</i> added in <i>Table 5: Medium-density STM32F103xx pin definitions</i>.</p> <p>V_{REINT} and $T_{C_{eff}}$ added to <i>Table 12: Embedded internal reference voltage</i>. I_{DD_VBAT} value added to <i>Table 16: Typical and maximum current consumptions in Stop and Standby modes</i>. <i>Figure 18: Typical current consumption on VBAT with RTC on versus temperature at different VBAT values</i> added.</p> <p>f_{HSE_ext} min modified in <i>Table 20: High-speed external user clock characteristics</i>.</p> <p>C_{L1} and C_{L2} replaced by C in <i>Table 22: HSE 4-16 MHz oscillator characteristics</i> and <i>Table 23: LSE oscillator characteristics (fLSE = 32.768 kHz)</i>, notes modified and moved below the tables. <i>Table 24: HSI oscillator characteristics</i> modified. Conditions removed from <i>Table 26: Low-power mode wakeup timings</i>.</p> <p><i>Note 1</i> modified below <i>Figure 24: Typical application with an 8 MHz crystal</i>.</p> <p>IEC 1000 standard updated to IEC 61000 and SAE J1752/3 updated to IEC 61967-2 in <i>Section 5.3.10: EMC characteristics on page 58</i>.</p> <p>Jitter added to <i>Table 27: PLL characteristics</i>.</p> <p><i>Table 42: SPI characteristics</i> modified.</p> <p>C_{ADC} and R_{AIN} parameters modified in <i>Table 46: ADC characteristics</i>. R_{AIN} max values modified in <i>Table 47: RAIN max for fADC = 14 MHz</i>.</p> <p><i>Figure 45: LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline</i> updated.</p> |
| 03-Jun-2010 | 12 | <p>Added STM32F103TB devices.</p> <p>Added VFQFPN48 package.</p> <p>Updated note 2 below <i>Table 40: I2C characteristics</i></p> <p>Updated <i>Figure 32: I2C bus AC waveforms and measurement circuit</i></p> <p>Updated <i>Figure 31: Recommended NRST pin protection</i></p> <p>Updated <i>Section 5.3.12: I/O current injection characteristics</i></p> |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|--|
| 19-Apr-2011 | 13 | Updated footnotes below Table 6: Voltage characteristics on page 37 and Table 7: Current characteristics on page 38 Updated $t_{w \min}$ in Table 20: High-speed external user clock characteristics on page 51 Updated startup time in Table 23: LSE oscillator characteristics (fLSE = 32.768 kHz) on page 54 Added Section 5.3.12: I/O current injection characteristics Updated Section 5.3.13: I/O port characteristics |
| 07-Dec-2012 | 14 | Added UFBGA100 7 x 7 mm. Updated Figure 50: LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline to add pin 1 identification. |

Table 61. Document revision history (continued)

| Date | Revision | Changes |
|-------------|----------|--|
| 14-May-2013 | 15 | <p>Replaced VQFN48 package with UQFN48 in cover page packages, Table 2: STM32F103xx medium-density device features and peripheral counts, Figure 9: STM32F103xx performance line UFQFPN48 pinout, Table 2: STM32F103xx medium-density device features and peripheral counts, Table 55: UFBGA100 - ultra fine pitch ball grid array, 7 x 7 mm, 0.50 mm pitch, package mechanical data, Table 60: Ordering information scheme and updated Table 59: Package thermal characteristics</p> <p>Added footnote for TFBGA ADC channels in Table 2: STM32F103xx medium-density device features and peripheral counts</p> <p>Updated 'All GPIOs are high current...' in Section 2.3.21: GPIOs (general-purpose inputs/outputs)</p> <p>Updated Table 5: Medium-density STM32F103xx pin definitions</p> <p>Corrected Sigma letter in Section 5.1.1: Minimum and maximum values</p> <p>Removed the first sentence in Section 5.3.16: Communications interfaces</p> <p>Added 'V_{IN}' in Table 9: General operating conditions</p> <p>Updated first sentence in Output driving current</p> <p>Added note 5. in Table 24: HSI oscillator characteristics</p> <p>Updated 'V_{IL}' and 'V_{IH}' in Table 35: I/O static characteristics</p> <p>Added notes to Figure 26: Standard I/O input characteristics - CMOS port, Figure 27: Standard I/O input characteristics - TTL port, Figure 28: 5 V tolerant I/O input characteristics - CMOS port and Figure 29: 5 V tolerant I/O input characteristics - TTL port</p> <p>Updated Figure 32: I2C bus AC waveforms and measurement circuit</p> <p>Updated note 2. and 3., removed note "the device must internally..." in Table 40: I2C characteristics</p> <p>Updated title of Table 41: SCL frequency (fPCLK1= 36 MHz., VDD_I2C = 3.3 V)</p> <p>Updated note 2. in Table 49: ADC accuracy</p> <p>Updated Figure 49: UFBGA100 - ultra fine pitch ball grid array, 7 x 7 mm, 0.50 mm pitch, package outline and Table 55: UFBGA100 - ultra fine pitch ball grid array, 7 x 7 mm, 0.50 mm pitch, package mechanical data</p> <p>Updated Figure 45: LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package outline and Table 53: LFBGA100 - 10 x 10 mm low profile fine pitch ball grid array package mechanical data</p> <p>Updated Figure 52: TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package outline and Table 57: TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package mechanical data</p> |

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